Past and Future Trends 0f Integrated Circuit Technology

@Prithvi Narayan Campus, Trivhuvan Univ., Pokhara, Nepal

October 25, 2010

Tokyo Institute of Technology

Frontier Research Center

Hiroshi Iwai,

Tokyo Institute of Technology

Founded in 1881, Promoted to Univ. 1929

Institute Overview

Einstein Visit

Established in 1881→ 130th anniversary in 2011

3 undergraduate schools

School of Science, School of Engineering, School of Bioscience and Biotechnology

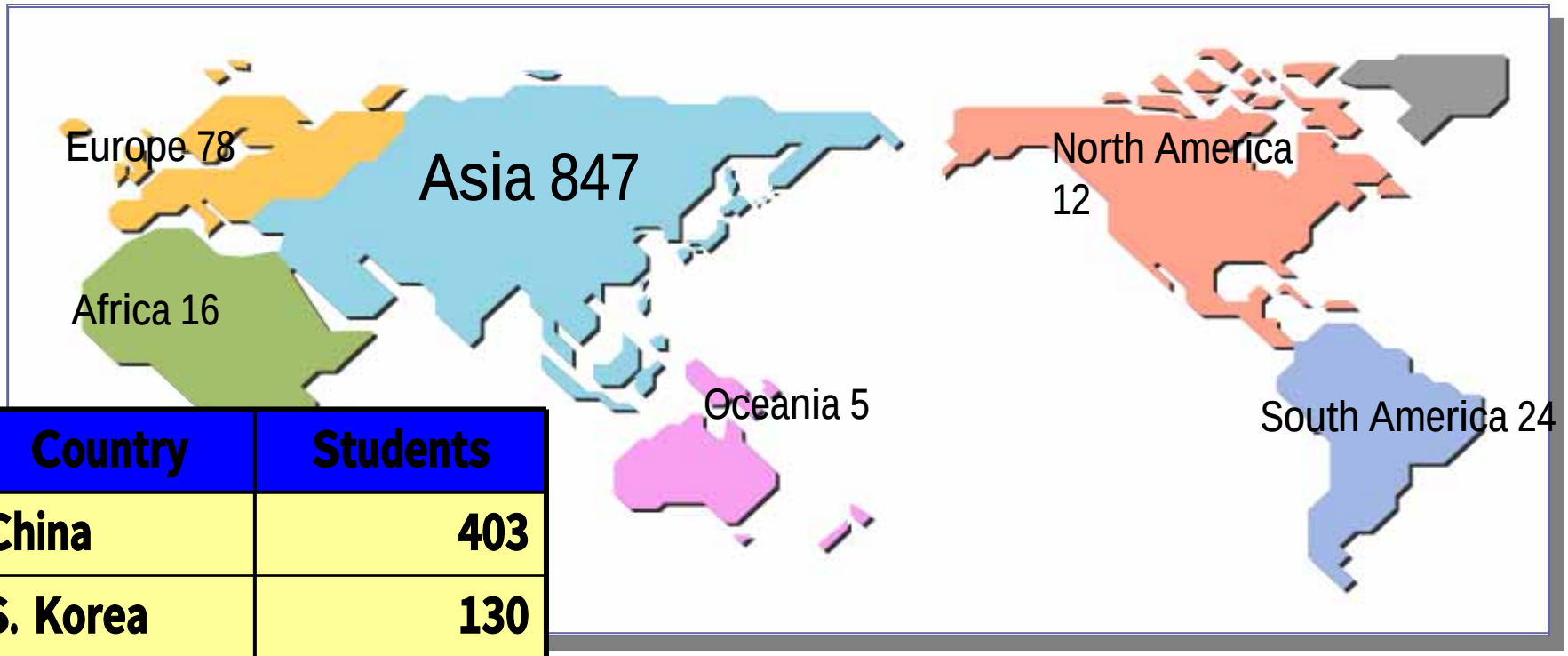
7 graduate schools

Science and Engineering Science, Science and Engineering Technology,
Bioscience and Biotechnology, Interdisciplinary Graduate School of Science and Engineering,
Information Science and Engineering, Decision Science and Technology, Innovation Management

Total Number of Students

	Undergraduate	Graduate	Master's	Doctoral	Teaching Staff	Student/Instructor	Staff
Tokyo Inst.	5,000	5,000	3,500	1,500	1,200	8.3	550
Per Year	1,200		1,800	500			

International Students



Country	Students
China	403
S. Korea	130
Indonesia	64
Thailand	55
Vietnam	60
Malaysia	28

Total 982

(As of May. 1, 2005)

Importance of Electronics

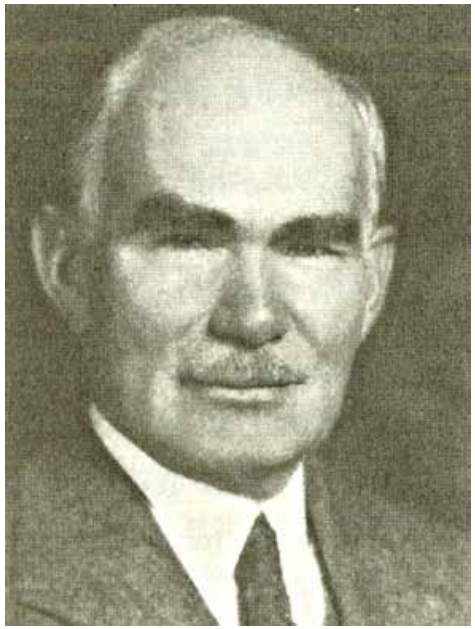
- There were many inventions in the 20th century:

  Airplane, Nuclear Power generation, Computer,

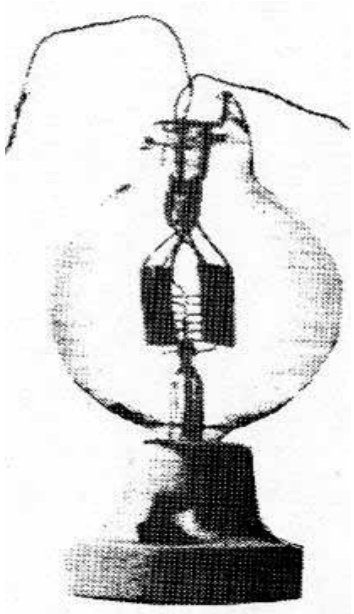
  Space aircraft, etc
- However, everything has to be controlled by electronics
- Electronics

  Most important invention in the 20th century
- What is Electronics: To use electrons,

  Electronic Circuits

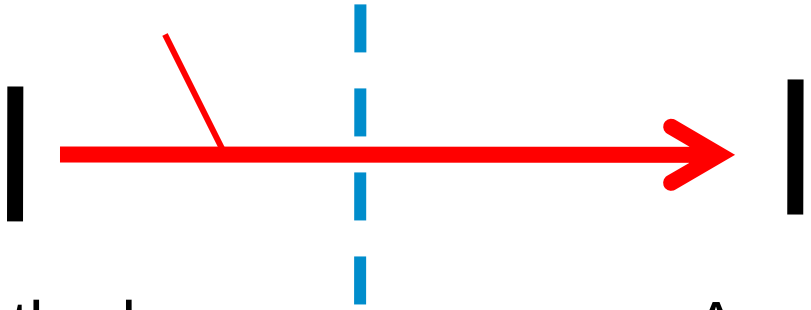


Lee De Forest



Electronic Circuits started by the invention of vacuum tube (Triode) in 1906

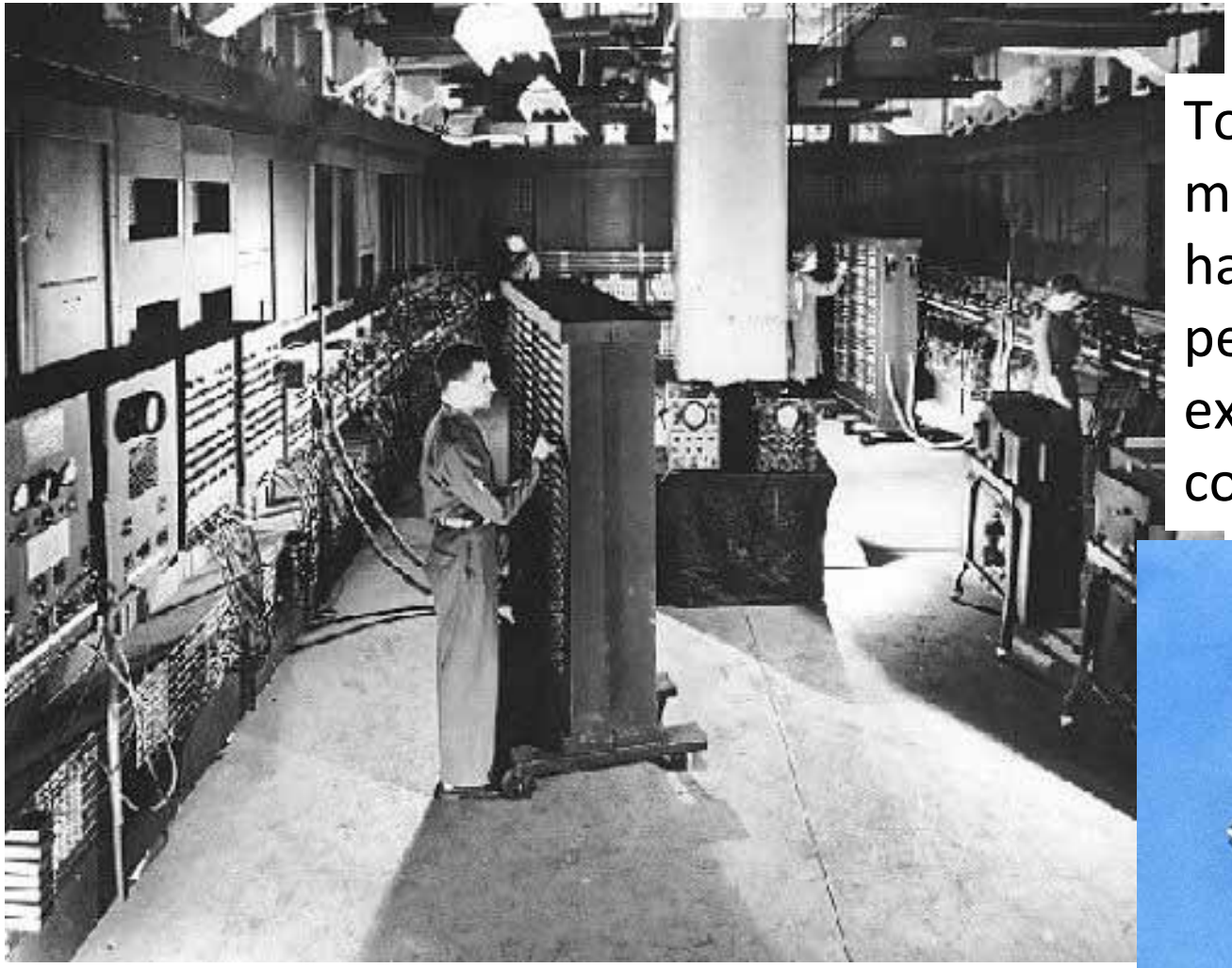
Thermal electrons from cathode controlled by grid bias



Same mechanism as that of transistor

First Computer Eniac: made of huge number of vacuum tubes 1946
Big size, huge power, short life time filament

→ dreamed of replacing vacuum tube with solid-state device

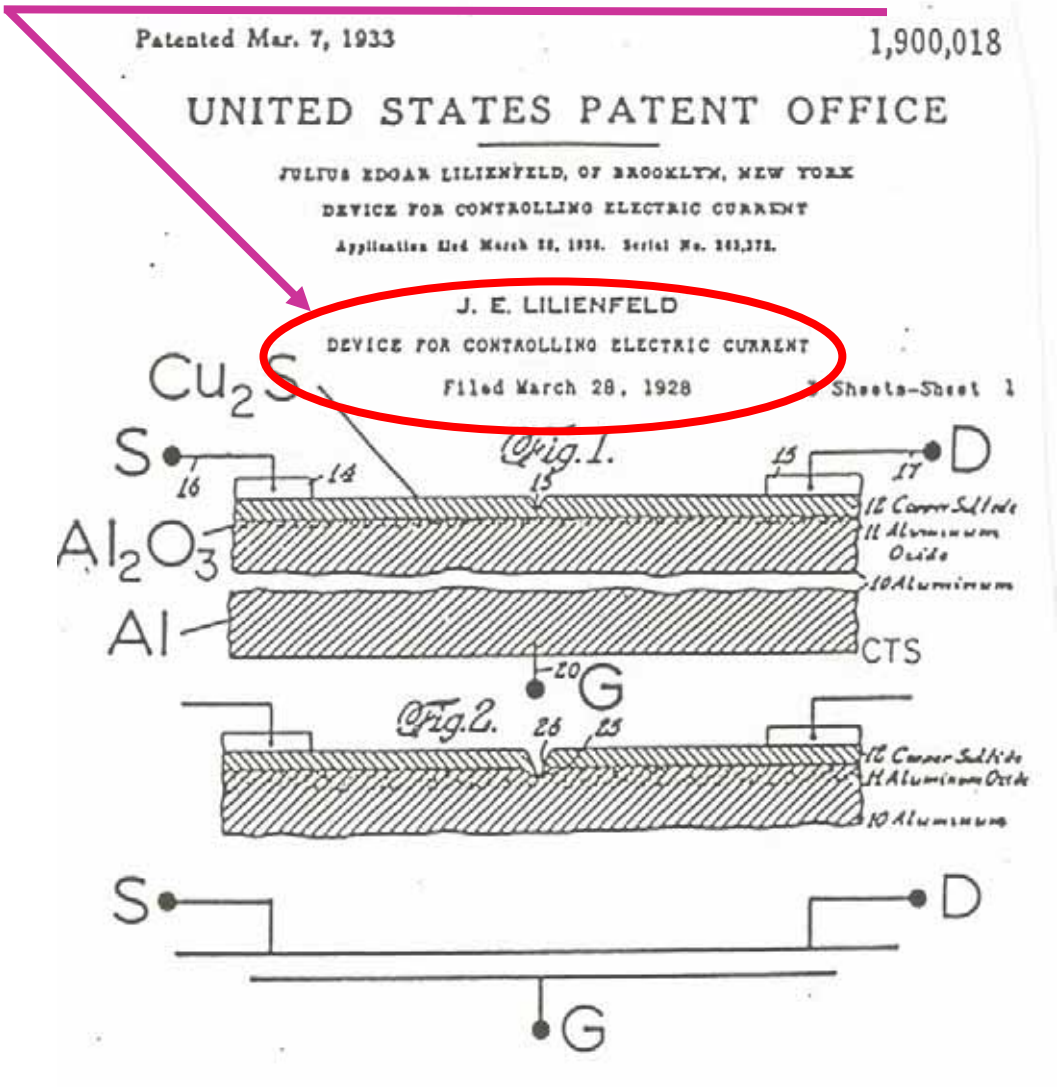


Today's pocket PC made of semiconductor has much higher performance with extremely low power consumption

J. E. LILIENFELD

DEVICES FOR CONTROLLED ELECTRIC CURRENT

Filed March 28, 1928



Patented Mar. 7, 1933 1,900,018

UNITED STATES PATENT OFFICE

JULIUS EDGAR LILIENFELD, OF BROOKLYN, NEW YORK

DEVICE FOR CONTROLLING ELECTRIC CURRENT

Application filed March 28, 1928. Serial No. 263,372.

J. E. LILIENFELD

DEVICE FOR CONTROLLING ELECTRIC CURRENT

Filed March 28, 1928 2 Sheets-Sheet 1

Cu_2S

S

D

Al_2O_3

Al

CTS

G

Fig. 1.

Fig. 2.

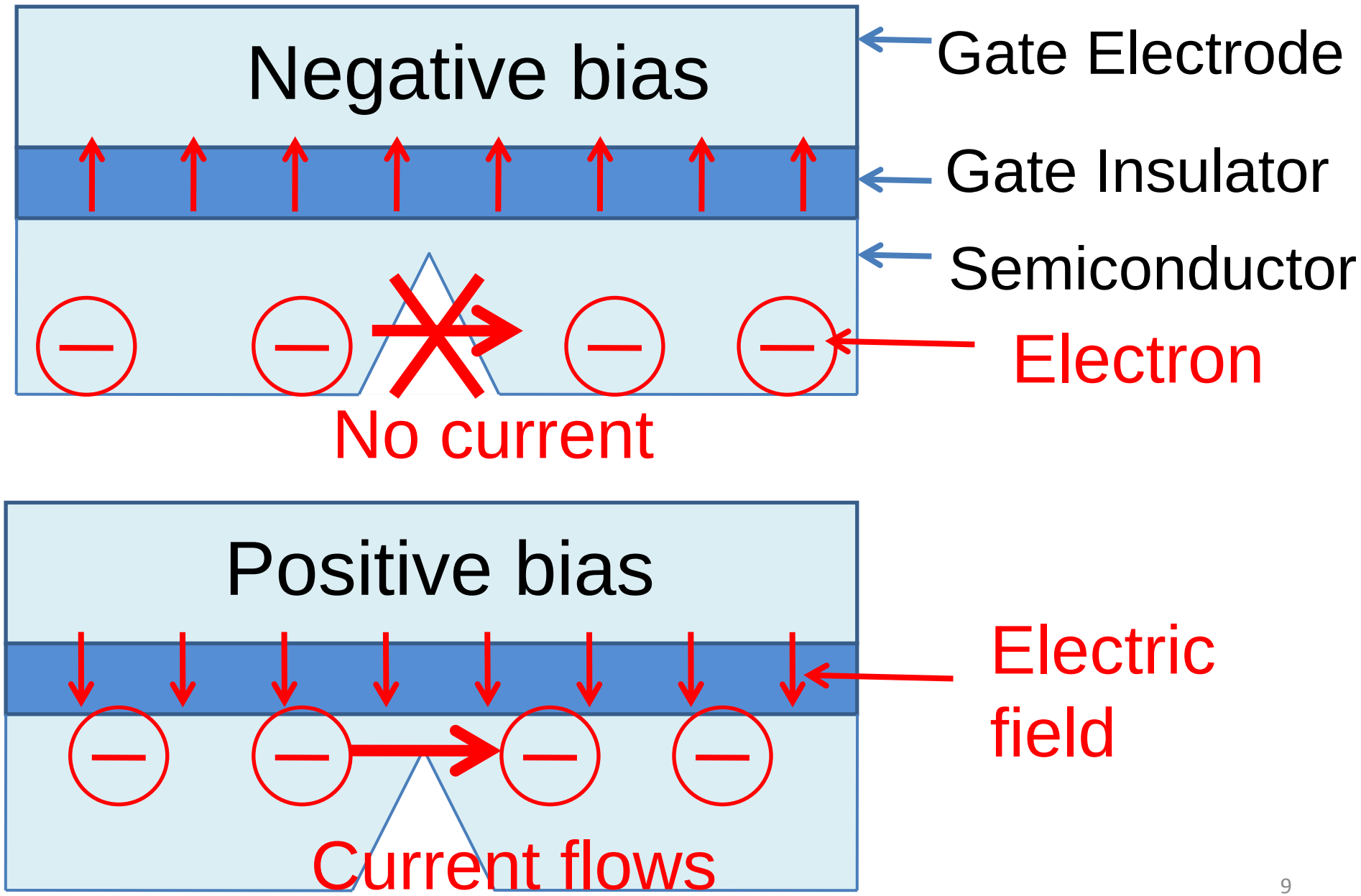
S

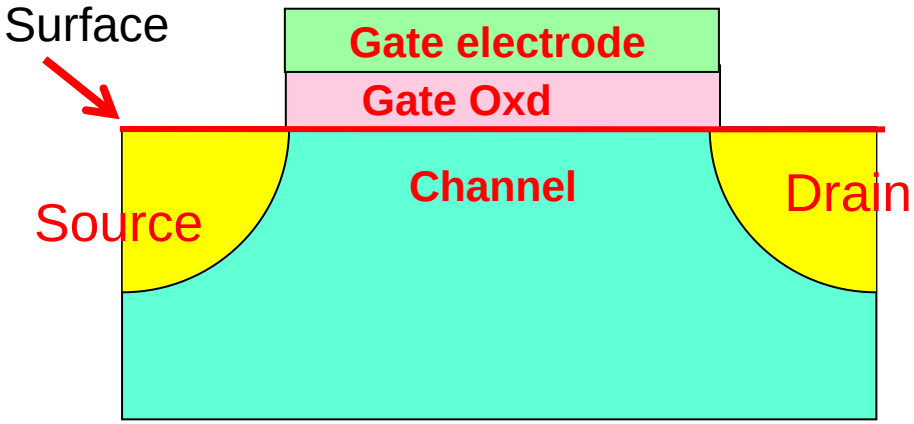
D

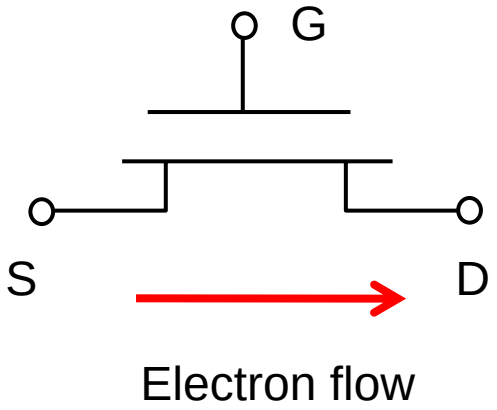
G

J.E.LILIENFELD

Capacitor structure with notch

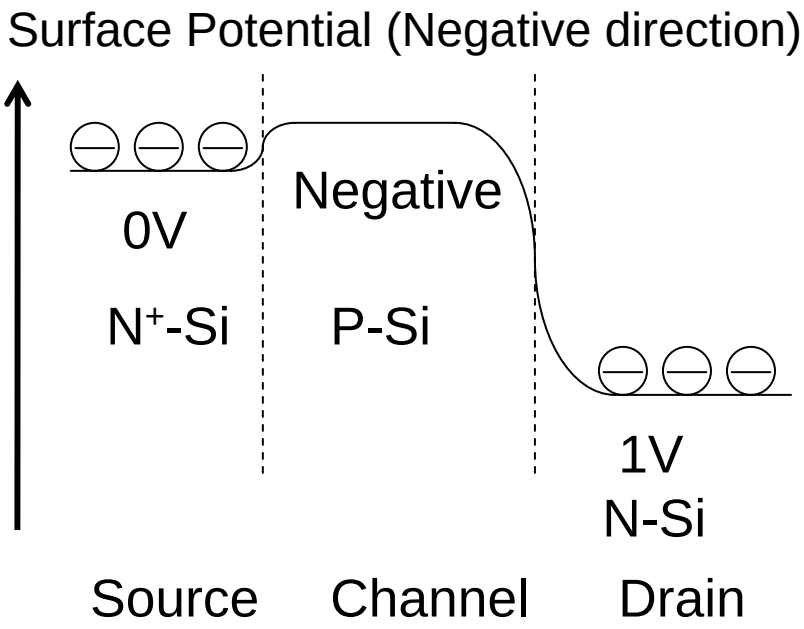


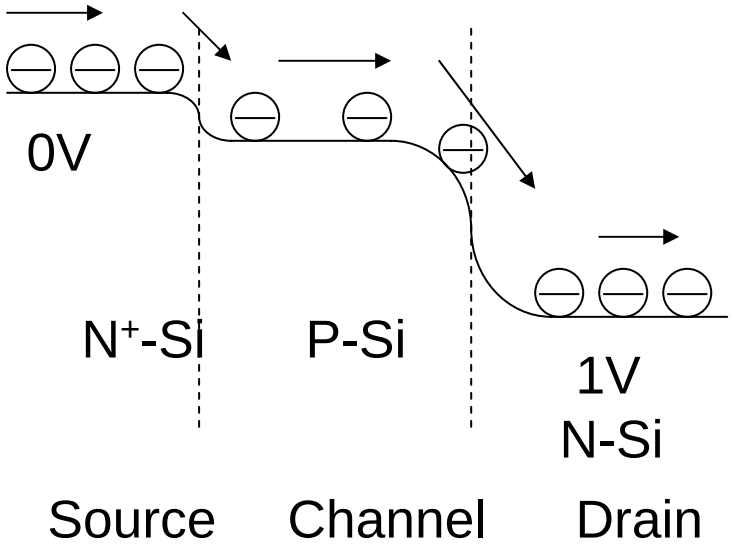




0 bias for gate

Positive bias for gate



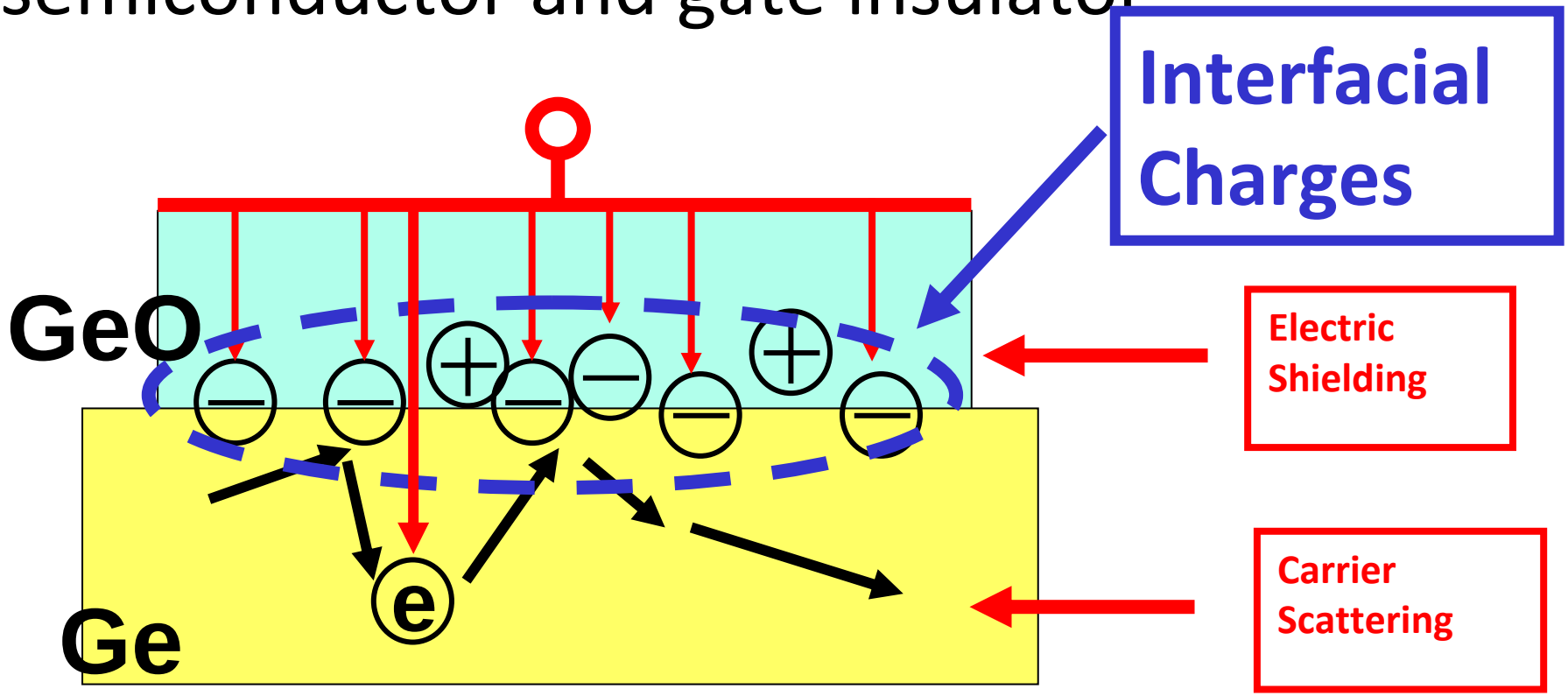


However, no one could realize MOSFET operation for more than 30 years.

Because of very bad interface property between the semiconductor and gate insulator

Even Shockley!

Very bad interface property between the semiconductor and gate insulator

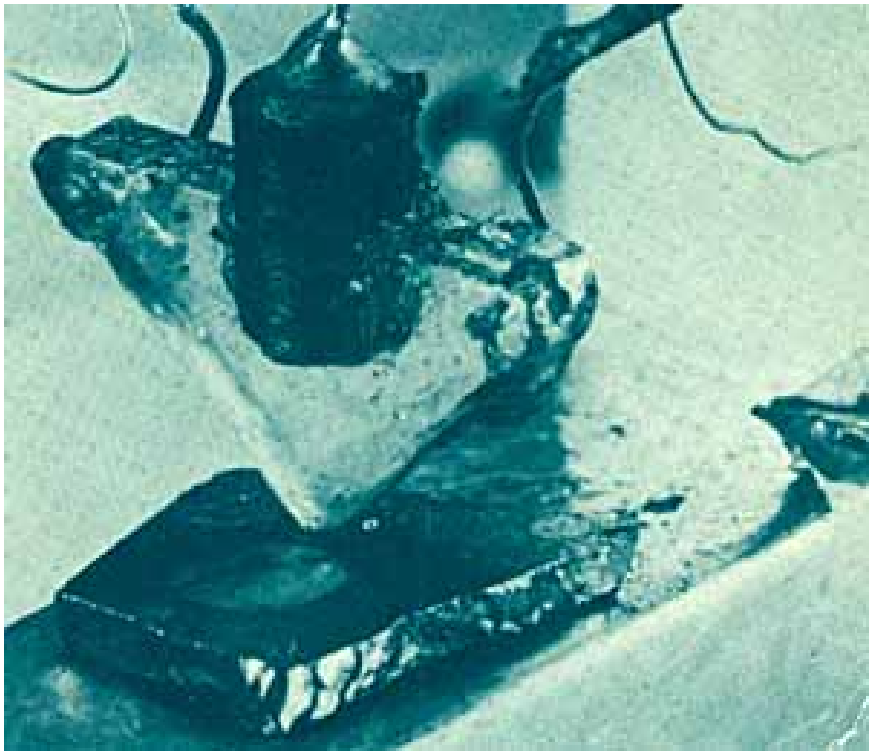


Drain Current was several orders of magnitude smaller than expected

Even Shockley!

However, they found amplification phenomenon when investigating Ge surface when putting needles.
This is the 1st Transistor:
Not Field Effect Transistor,
But Bipolar Transistor (another mechanism)

1947: 1st transistor



Bipolar using Ge

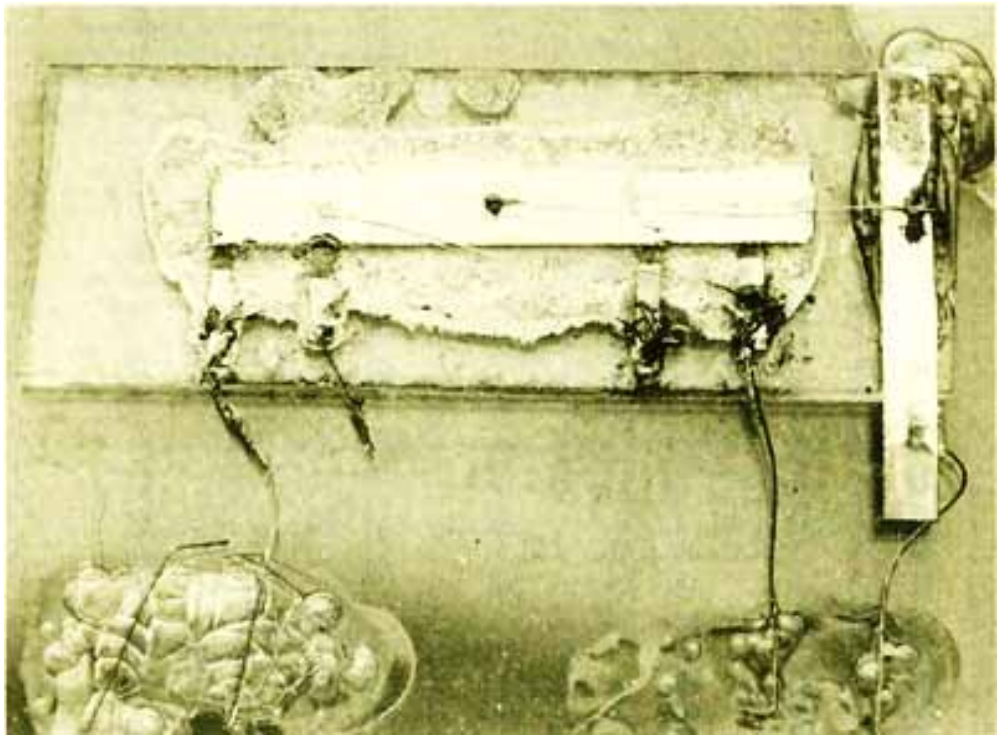
J. Bardeen W. Bratten,

W. Shockley

1958: 1st Integrated Circuit

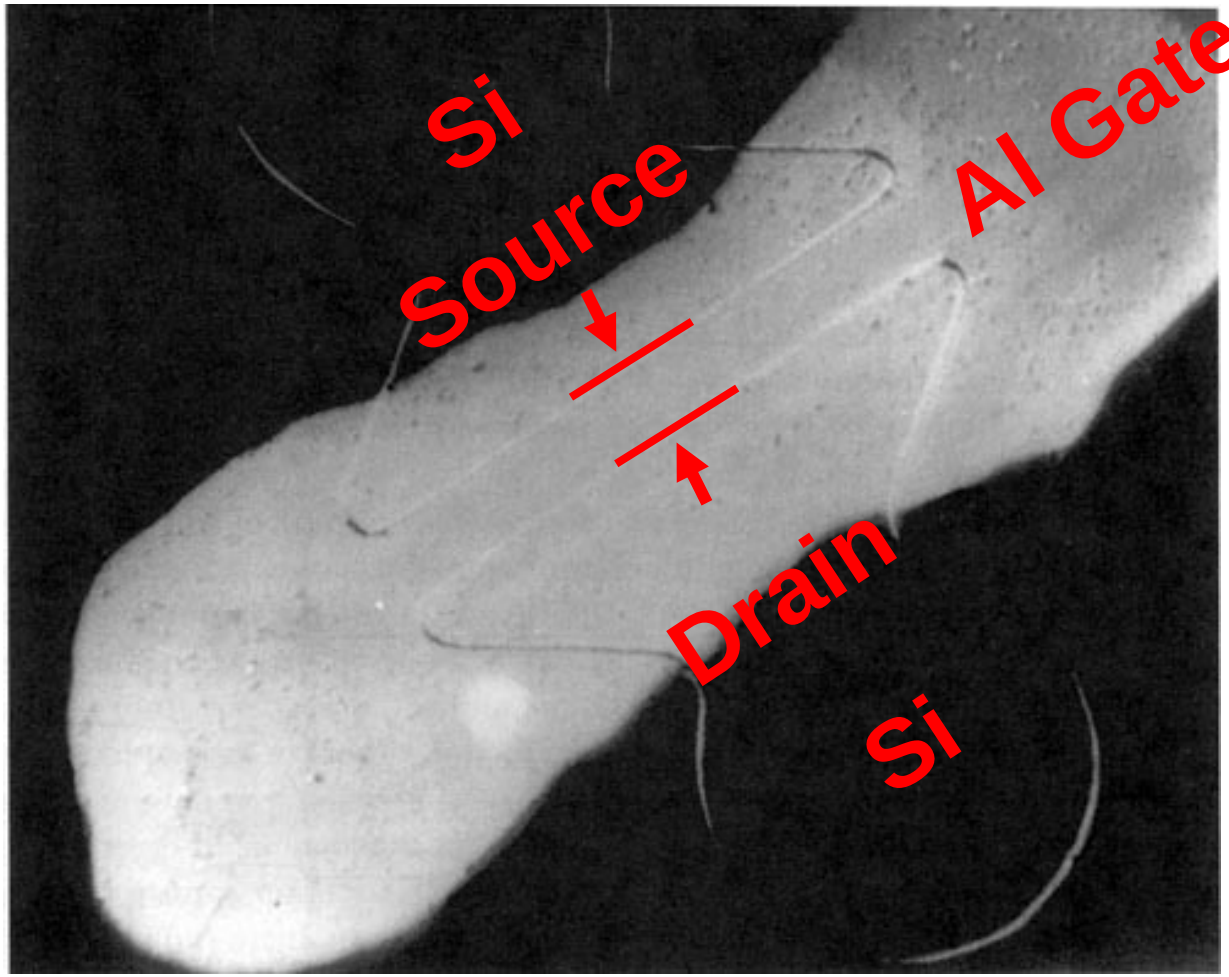
Jack S. Kilby

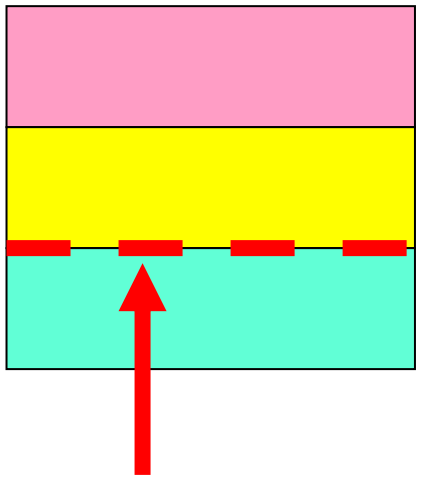
Connect 2 bipolar transistors in the
Same substrate by bonding wire.



1960: First MOSFET
by D. Kahng and M. Atalla

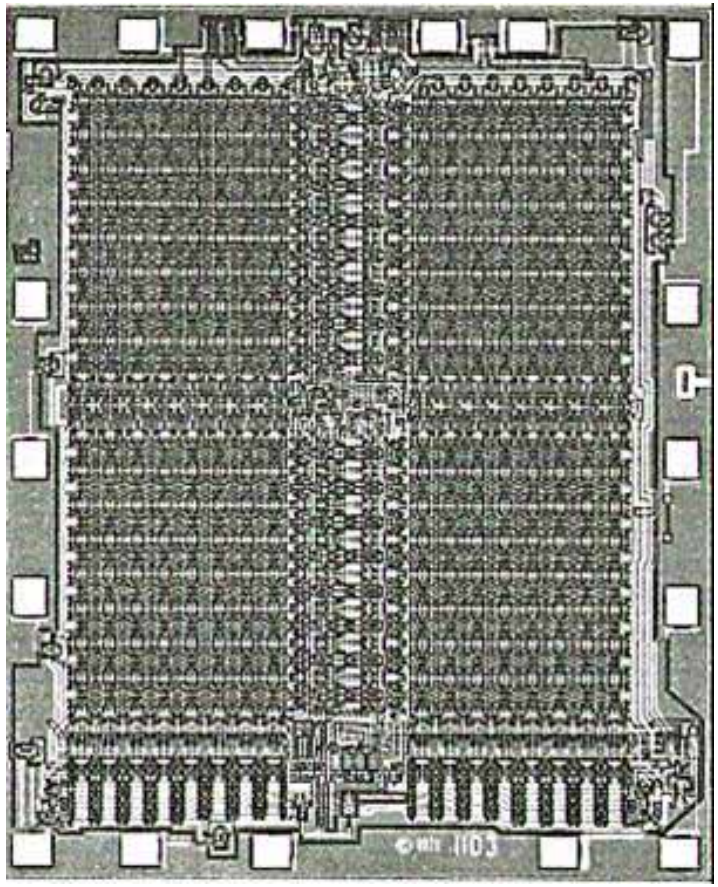
Top View



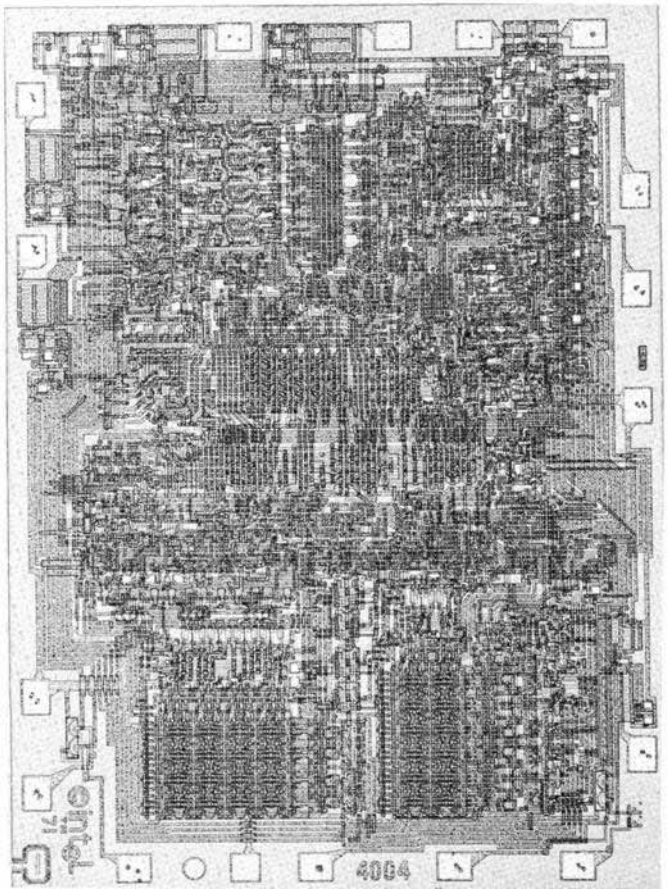


1970,71: 1st generation of LSIs

DRAM Intel 1103

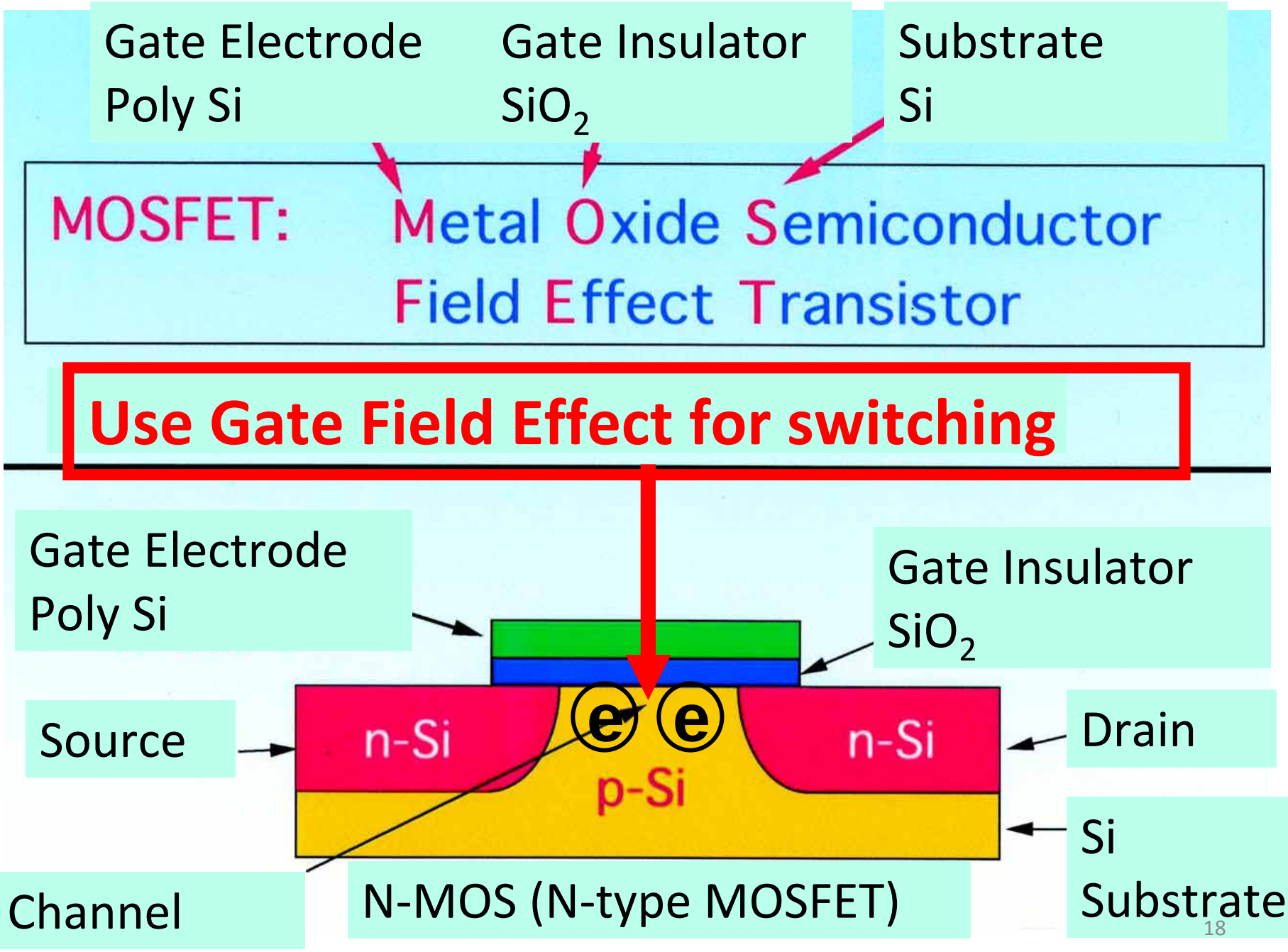


MPU Intel 4004



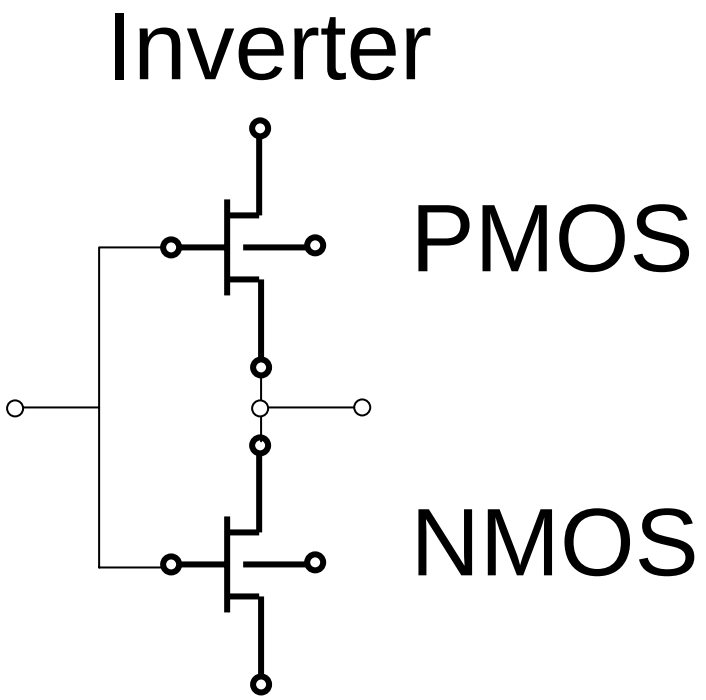
MOS LSI experienced continuous progress for many years

	Name of Integrated Circuits	Number of Transistors
1960s	IC (Integrated Circuits)	~ 10
1970s	LSI (Large Scale Integrated Circuit)	~1,000
1980s	VLSI (Very Large Scale IC)	~10,000
1990s	ULSI (Ultra Large Scale IC)	~1,000,000
2000s	?LSI (? Large Scale IC)	~1000,000,000


Gate Electrode
Poly Si
Gate Insulator
SiO2
Substrate
Si
MOSFET: Metal Oxide Semiconductor
Field Effect Transistor
Use Gate Field Effect for switching
Gate Electrode
Poly Si
Gate Insulator
SiO2
Source
n-Si
e
e
n-Si
Drain
p-Si
Si
Substrate
Channel
N-MOS (N-type MOSFET)

CMOS

Complimentary MOS



When NMOS is ON, PMOS is OFF

When PMOS is ON, NMOS is OFF

Needless to say, but….

CMOS Technology:

Indispensible for our human society

Al the human activities are controlled by CMOS

living, production, financing, telecommunication, transportation, medical care, education, entertainment, etc.

Without CMOS:

There is no computer in banks, and

world economical activities immediately stop.

Cellarer phone dose not exists

Downsizing of the components has been the driving force for circuit evolution

1900	1950	1960	1970	2000
Vacuum Tube	Transistor	IC	LSI	ULSI
10 cm	cm	mm	10 μm	100 nm
10^{-1}m	10^{-2}m	10^{-3}m	10^{-5}m	10^{-7}m

In 100 years, the size reduced by one million times.
There have been many devices from stone age.
We have never experienced such a tremendous reduction of devices in human history.

Downsizing

1. **Reduce Capacitance**

→ **Reduce switching time of MOSFETs**

→ **Increase clock frequency**

→ **Increase circuit operation speed**

2. **Increase number of Transistors**

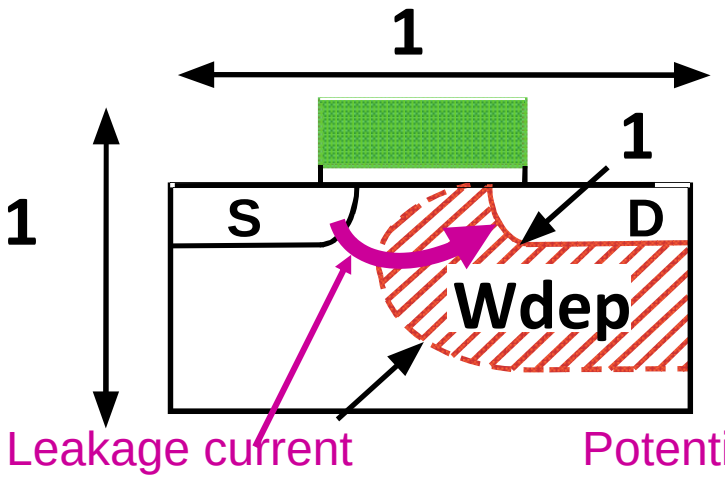
→ **Parallel processing**

→ **Increase circuit operation speed**

Downsizing contribute to the performance increase in double ways

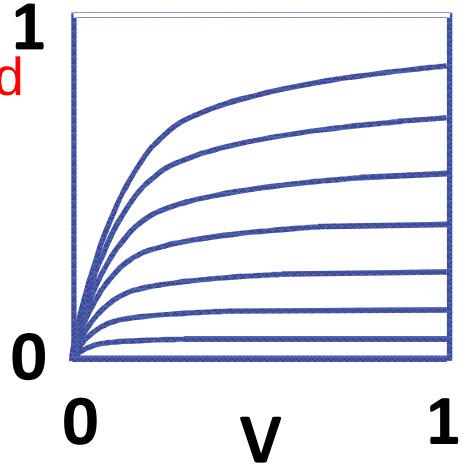
Thus, downsizing of Si devices is the most important and critical issue.

Scaling Method: by R. Dennard in 1974



Wdep: Space Charge Region (or Depletion Region) Width

Wdep has to be suppressed
Otherwise, large leakage between S and D



Leakage current

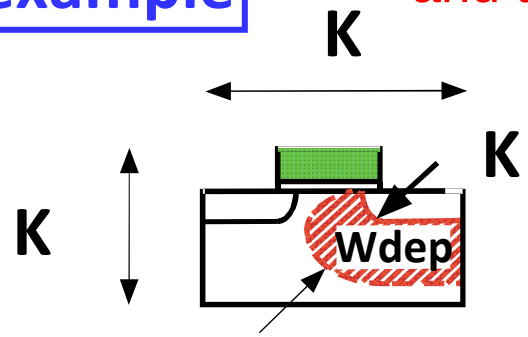
Potential in space charge region is high, and thus, electrons in source are attracted to the space charge region.

K=0.7 for example

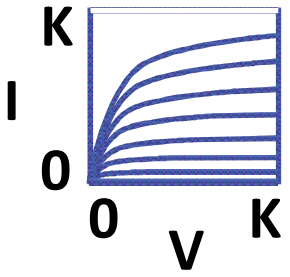
X , Y , Z : K, V : K, Na : 1/K

By the scaling, Wdep is suppressed in proportion, and thus, leakage can be suppressed.

→ Good scaled I-V characteristics



$$Wdep \propto \sqrt{V/Na}$$
$$: K$$



I : K

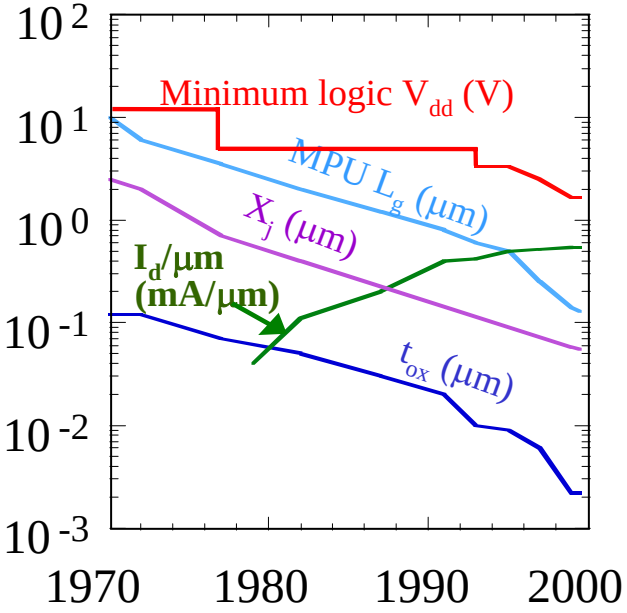
23

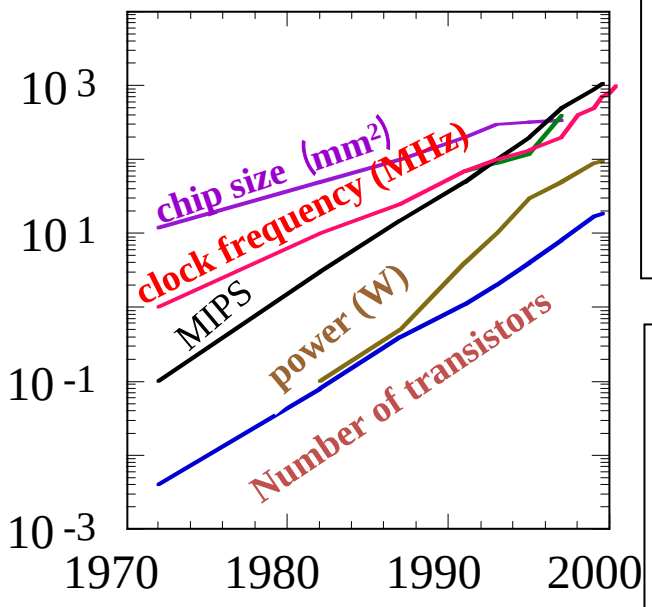
Downscaling merit: Beautiful!

Geometry & Supply voltage	L_g, W_g T_{ox}, V_{dd}	K	**Scaling K : K=0.7 for example**
Drive current in saturation	I_d	K	$I_d = v_{sat} W_g C_o (V_g - V_{th})$ C_o: gate C per unit area → $W_g (t_{ox}^{-1})(V_g - V_{th}) = W_g t_{ox}^{-1}(V_g - V_{th}) = KK^{-1}K = K$
I_d per unit W_g	$I_d/\mu m$	1	I_d per unit $W_g = I_d / W_g = 1$
Gate capacitance	C_g	K	$C_g = \varepsilon_o \varepsilon_{ox} L_g W_g / t_{ox}$ → $KK/K = K$
Switching speed	τ	K	$\tau = C_g V_{dd} / I_d$ → $KK/K = K$
Clock frequency	f	1/K	$f = 1/\tau = 1/K$
Chip area	A_{chip}	α	α: Scaling factor → **In the past, $\alpha>1$ for most cases**
Integration (# of Tr)	N	α/K^2	N → α/K^2 **$= 1/K^2$, when $\alpha=1$**
Power per chip	P	α	$fNCV^2/2$ → $K^{-1}(\alpha K^{-2})K(K^1)^2 = \alpha$ **$= 1$, when $\alpha=1$**

k= 0.7 and α =1	k= 0.7^2 =0.5 and α =1
Single MOFET Vdd → 0.7 Lg → 0.7 Id → 0.7 Cg → 0.7 P (Power)/Clock → 0.7^3 = 0.34 τ (Switching time) → 0.7	Vdd → 0.5 Lg → 0.5 Id → 0.5 Cg → 0.5 P (Power)/Clock → 0.5^3 = 0.125 τ (Switching time) → 0.5
Chip N (# of Tr) → $1/0.7^2$ = 2 f (Clock) → 1/0.7 = 1.4 P (Power) → 1	N (# of Tr) → $1/0.5^2$ = 4 f (Clock) → 1/0.5 = 2 P (Power) → 1

Actual past downscaling trend until year 2000





Past 30 years scaling

Merit: N, f increase

Demerit: P increase

V_{dd} scaling insufficient

⇩

Additional significant increase in I_d, f, P

Source. Iwai and S. Ohmi, Microelectronics Reliability 42 (2002), pp.1251-1268

Change in 30 years

	Ideal scaling	Real Change		Ideal scaling	Real Change		Ideal scaling	Real Change
L_g	K	10^{-2}	I_d	K (10^{-2})	10^{-1}	f	$1/K(10^{2})$	10^{3}
t_{ox}	$K(10^{-2})$	10^{-2}						
V_{dd}	$K(10^{-2})$	10^{-1}	I_d/μm	1	10^{1}	P	$\alpha(10^{1})$	10^{5}
						$= f\alpha NCV^2$		
A_{chip}	α	10^{1}	N	$\alpha/K^2(10^{5})$	10^{4}			

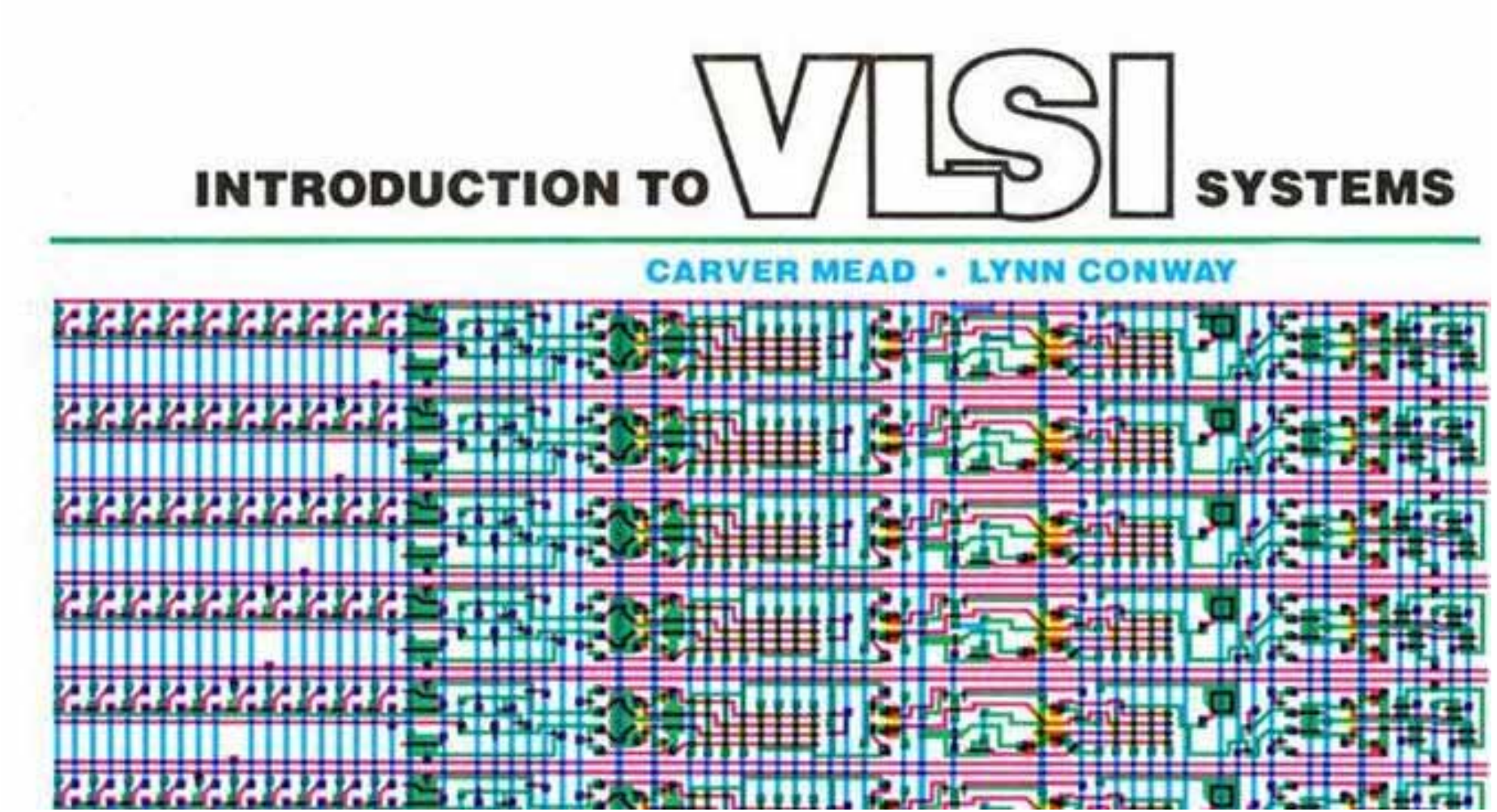
Vd scaling insufficient, α increased → N, Id, f, P increased significantly

Many people wanted to say about the limit. Past predictions were not correct!!

Period	Expected limit(size)	Cause
Late 1970's	1μm:	SCE
Early 1980's	0.5μm:	S/D resistance
Early 1980's	0.25μm:	Direct-tunneling of gate SiO_2
Late 1980's	0.1μm:	'0.1μm brick wall'(various)
2000	50nm:	'Red brick wall' (various)
2000	10nm:	Fundamental?

Historically, many predictions of the limit of downsizing.

VLSI text book written 1979 predict that 0.25 micro-meter would be the limit because of direct-tunneling current through the very thin-gate oxide.

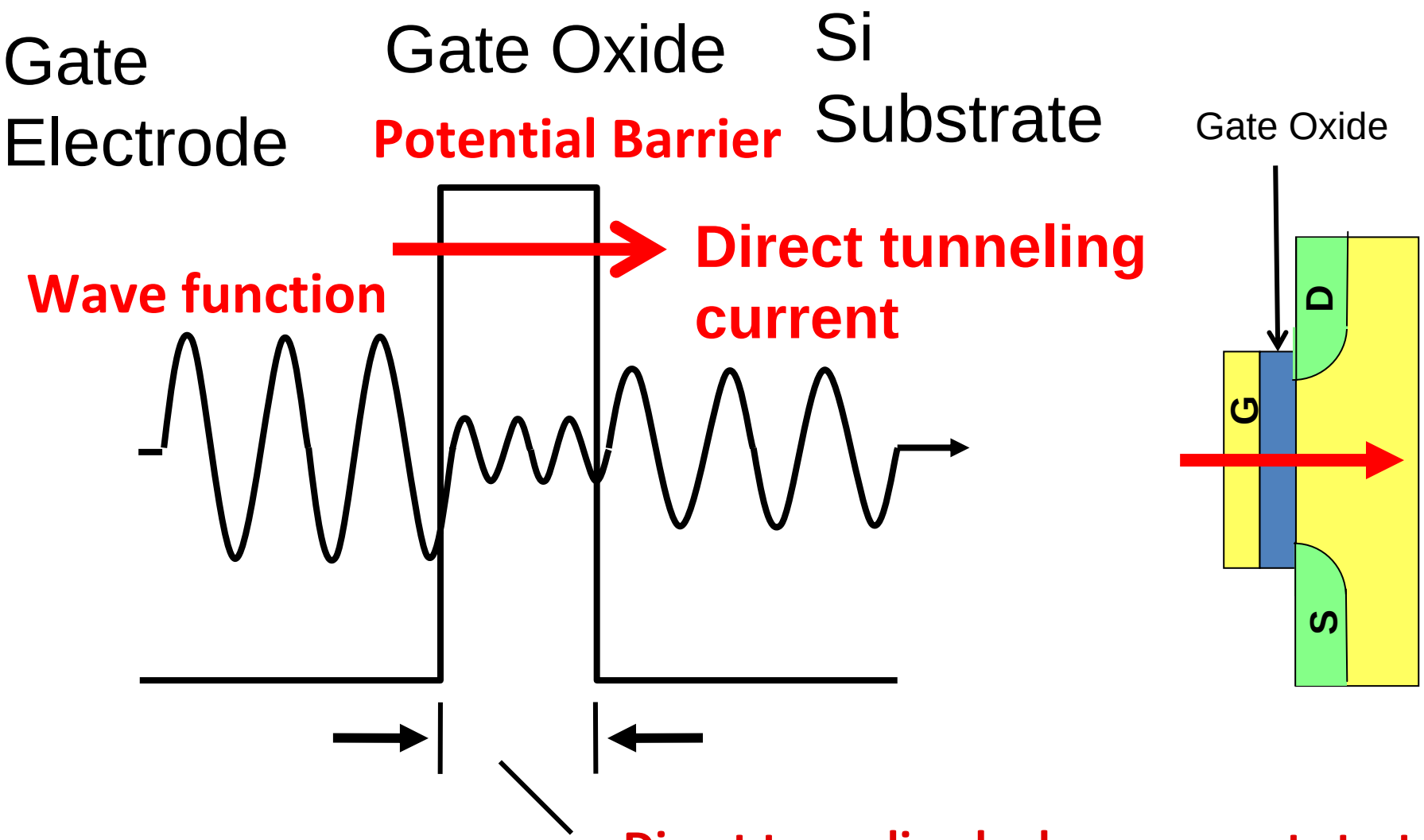


C. Mead L. Conway

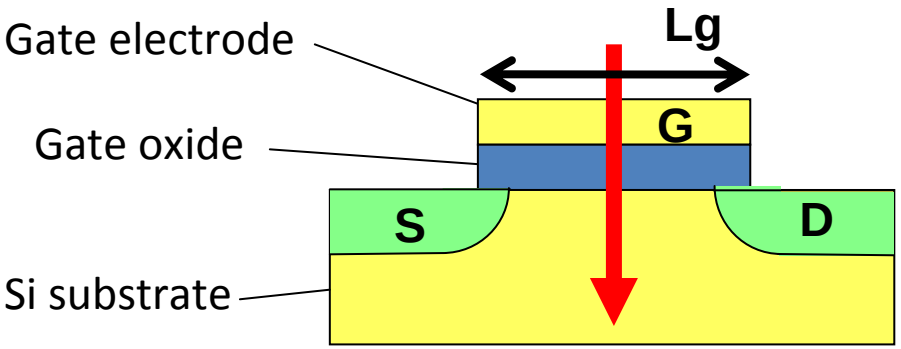
VLSI textbook

Finally, there appears to be a fundamental limit [10] of approximately quarter micron channel length, where certain physical effects such as the tunneling through the gate oxide ..... begin to make the devices of smaller dimension unworkable.

Direct-tunneling effect

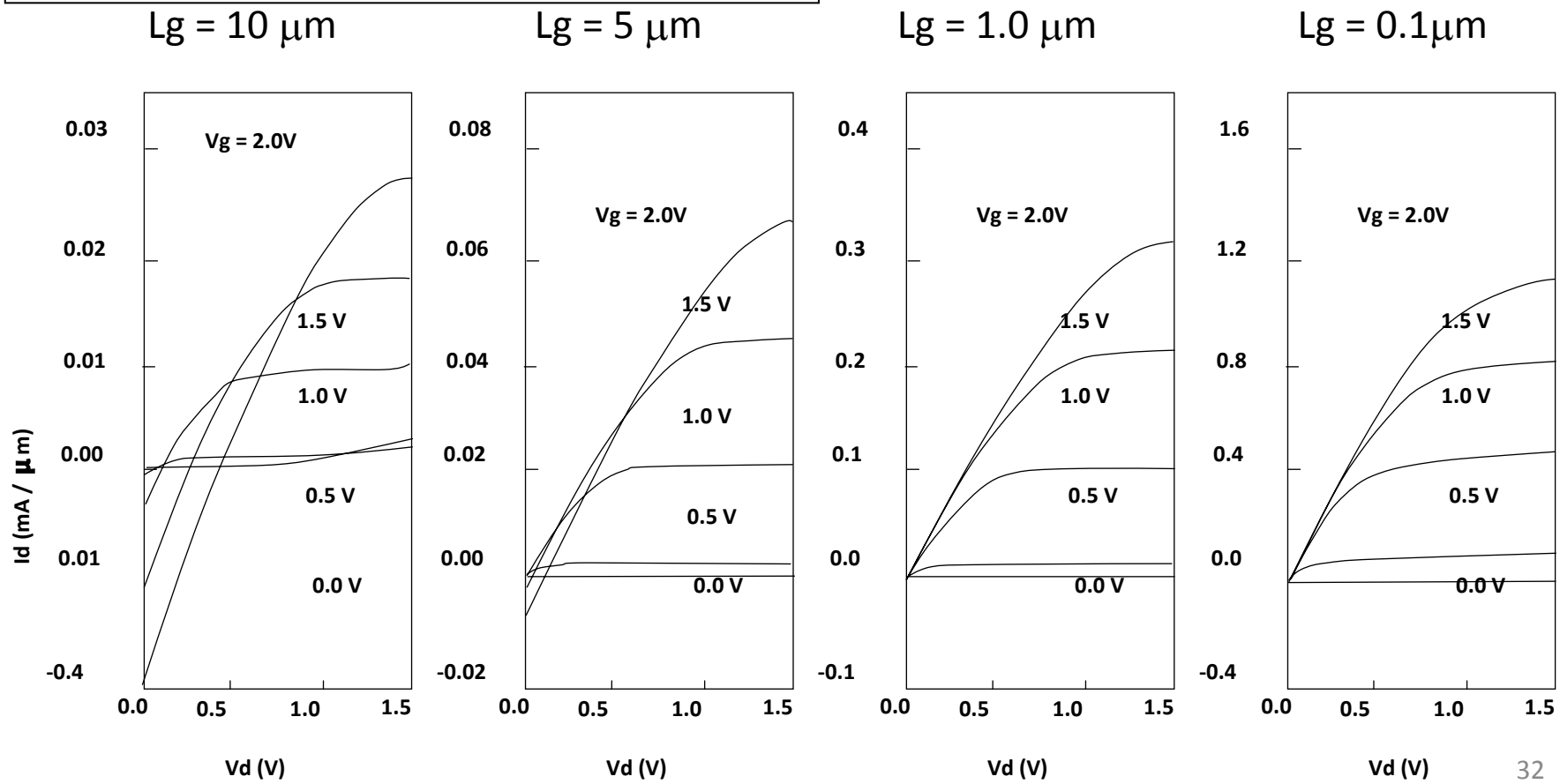


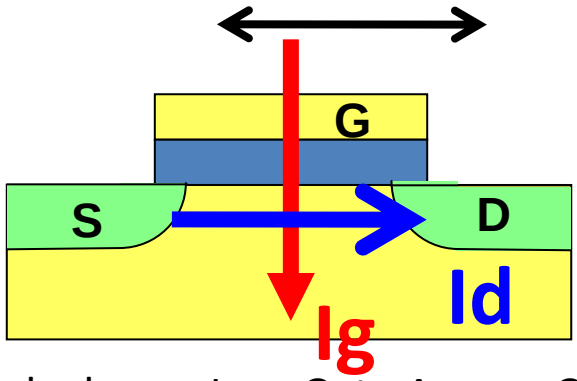
Direct tunneling leakage current start to flow when the thickness is 3 nm.



Direct tunneling leakage was found to be OK! In 1994!

MOSFETs with 1.5 nm gate oxide



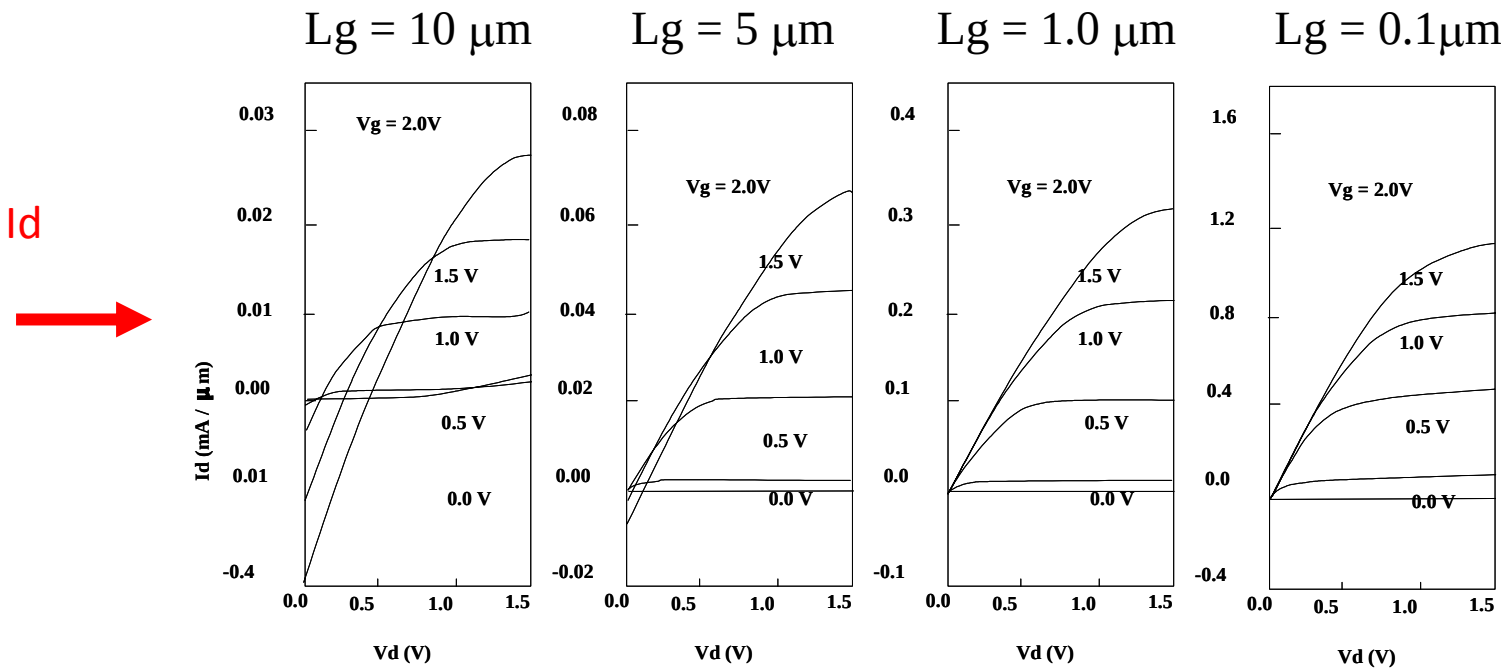


Gate leakage: Ig ∝ Gate Area ∝ Gate length (Lg)

Drain current: Id ∝ 1/Gate length (Lg)

Lg → small,

Then, Ig → small, Id → large, Thus, Ig/Id → very small



Do not believe a text book statement, blindly!

Never Give Up!

No one knows future!

There would be a solution!

Think, Think, and Think!

Or, Wait the time!
Some one will think for you

Transistor Scaling Continues

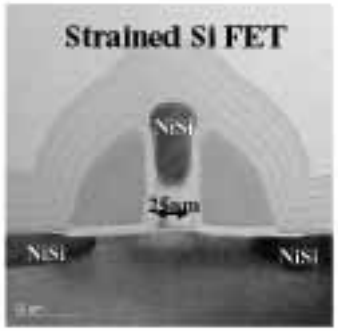
90nm node

Lg=50nm

65nm node

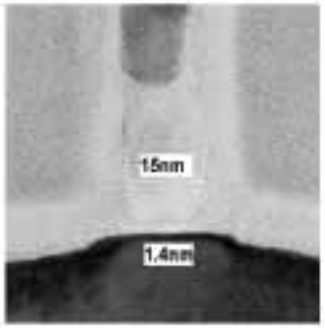
Lg=35nm

45nm node



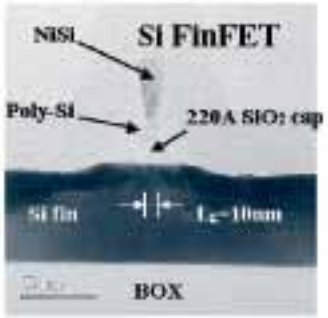
Lg=25nm

32nm node

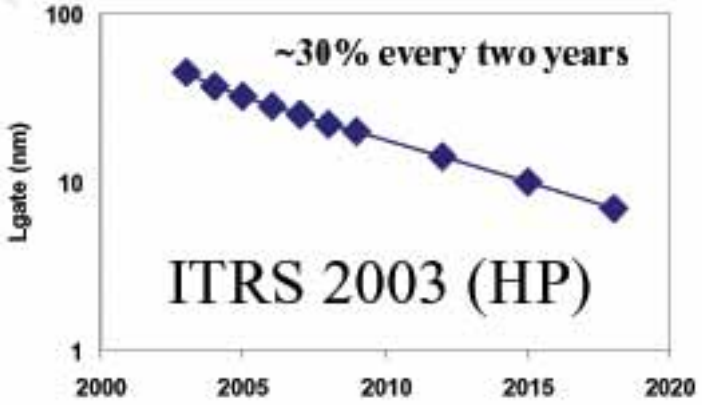


Lg=15nm

22nm node



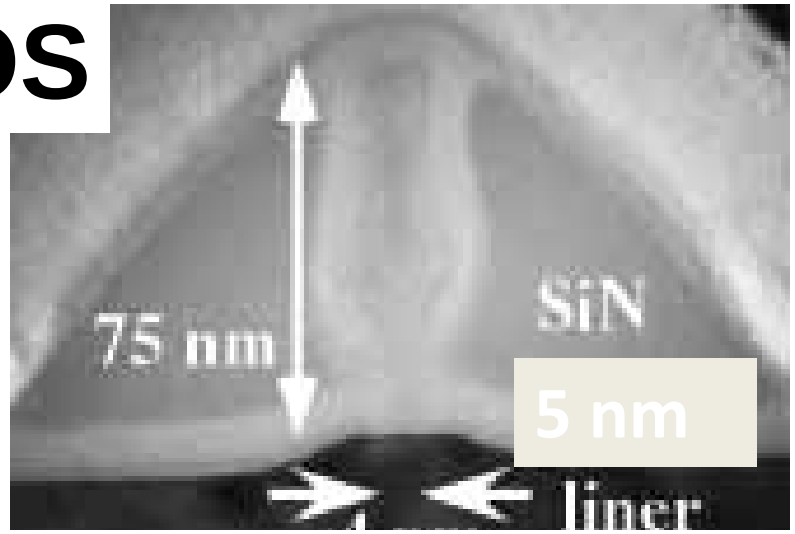
Lg=10nm



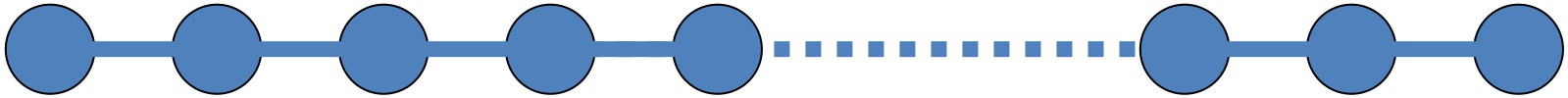
Qi Xinag, ECS 2004, AMD

5 nm gate length CMOS

Is a Real Nano Device!!

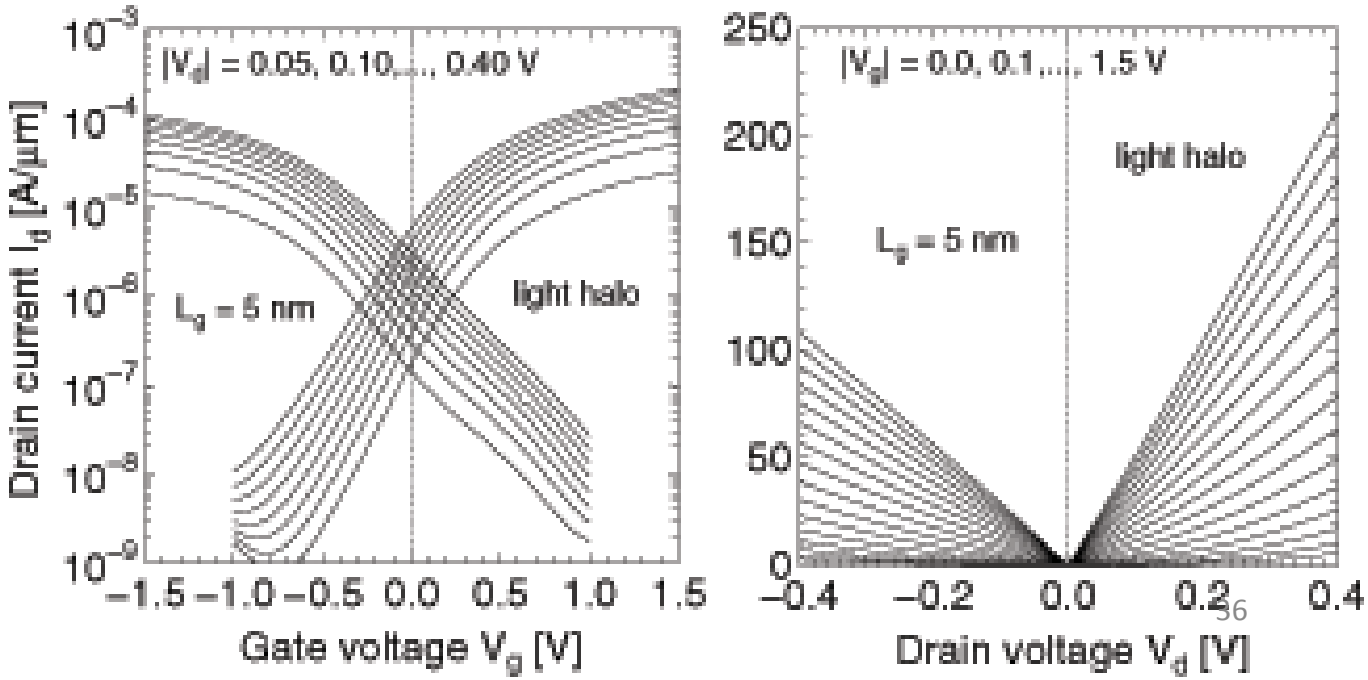


Length of 18 Si atoms



H. Wakabayashi
et.al, NEC

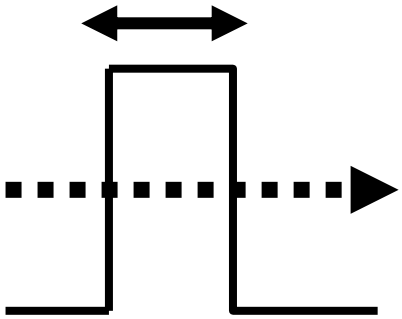
IEDM, 2003



What is the limit prediction now!

Tunneling distance

3 nm

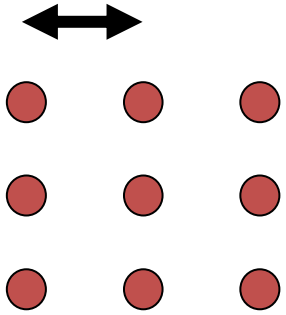


Limit for MOSFET operation

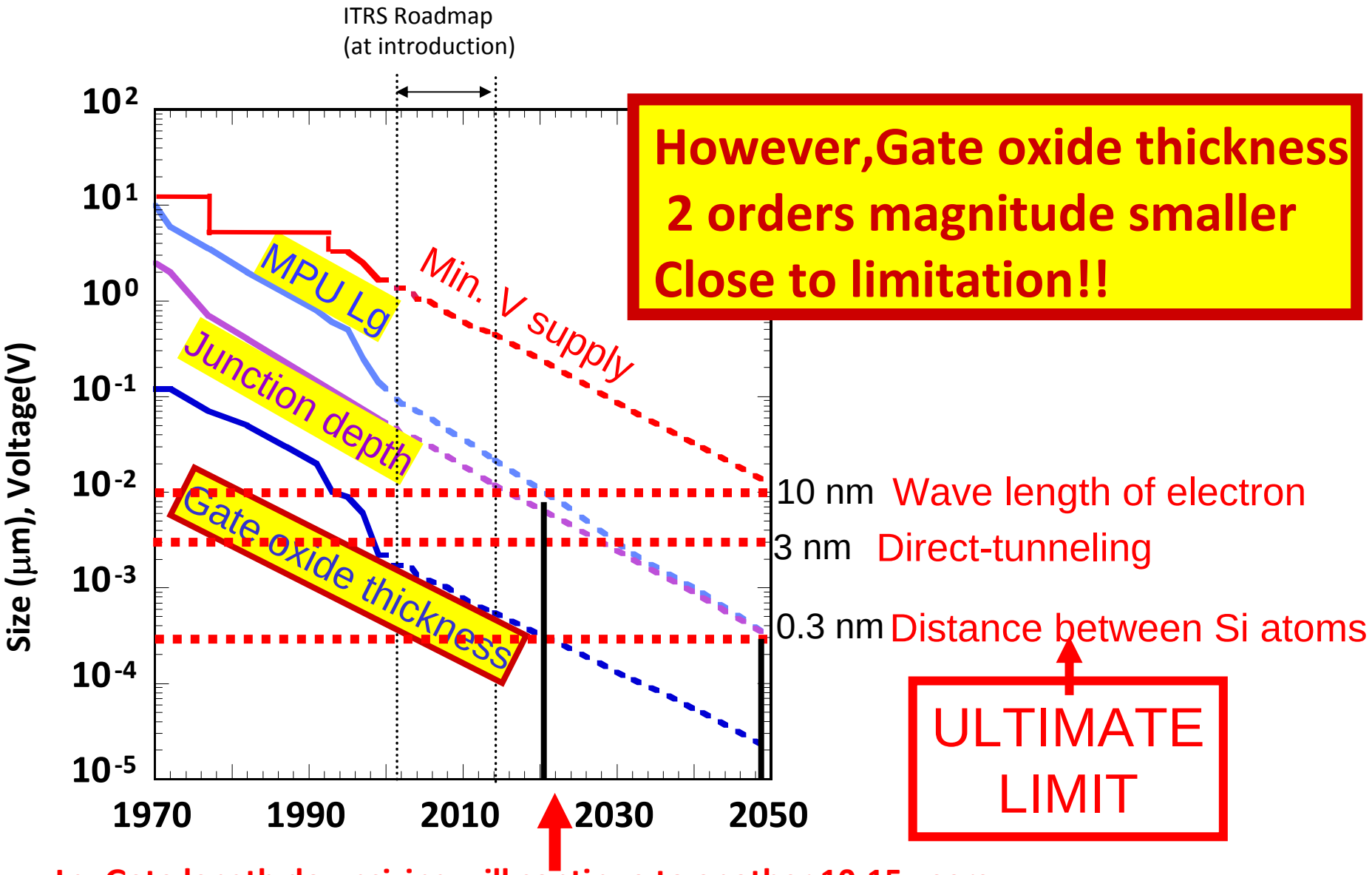
Below this,
no one knows future!

Atomic distance

0.3 nm



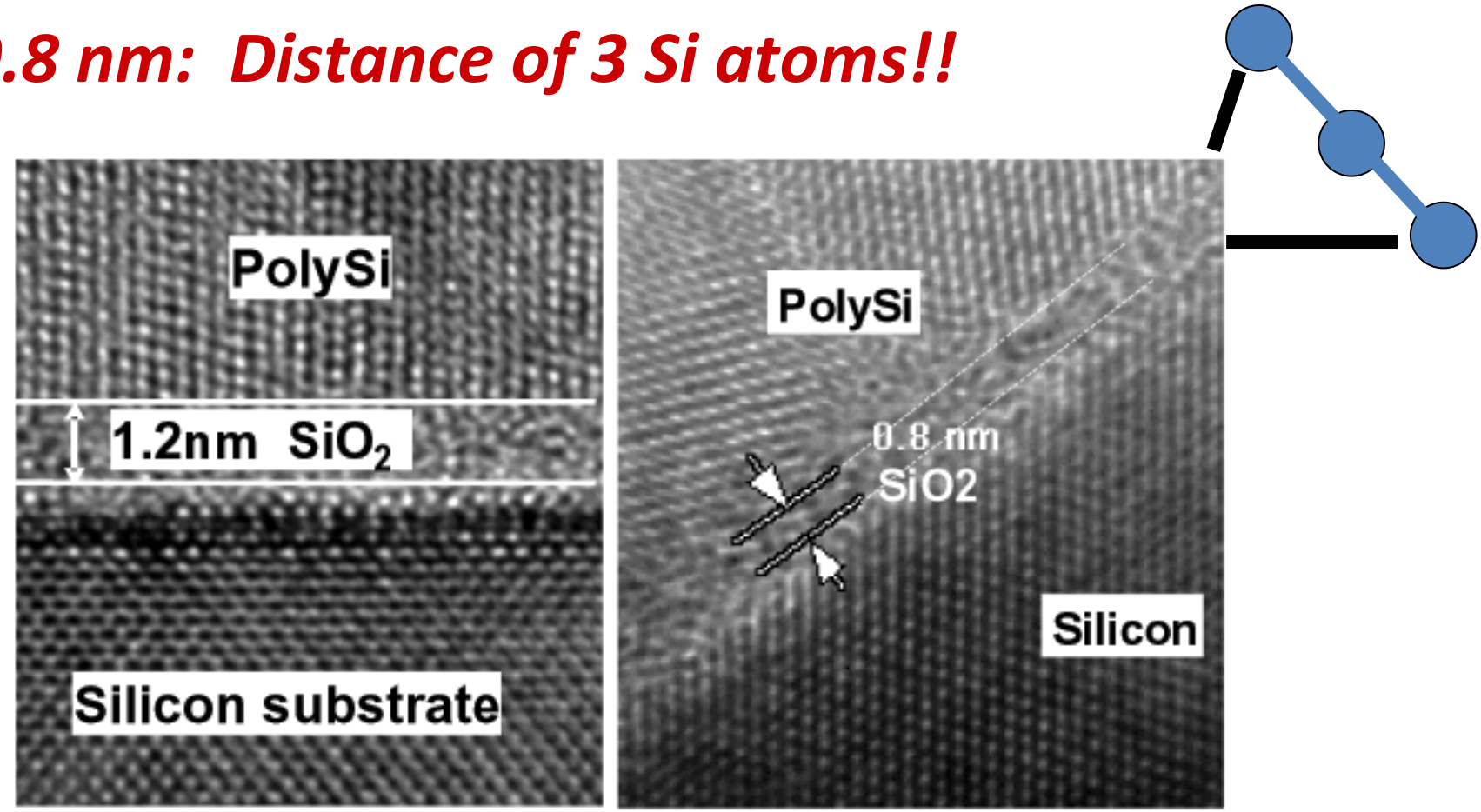
Ultimate limitation



However,Gate oxide thickness 2 orders magnitude smaller Close to limitation!!

0.8 nm Gate Oxide Thickness MOSFETs operates!!

0.8 nm: Distance of 3 Si atoms!!



- 1.2nm physical SiO2 in production (90nm logic node)
- 0.8nm physical SiO2 in research transistors

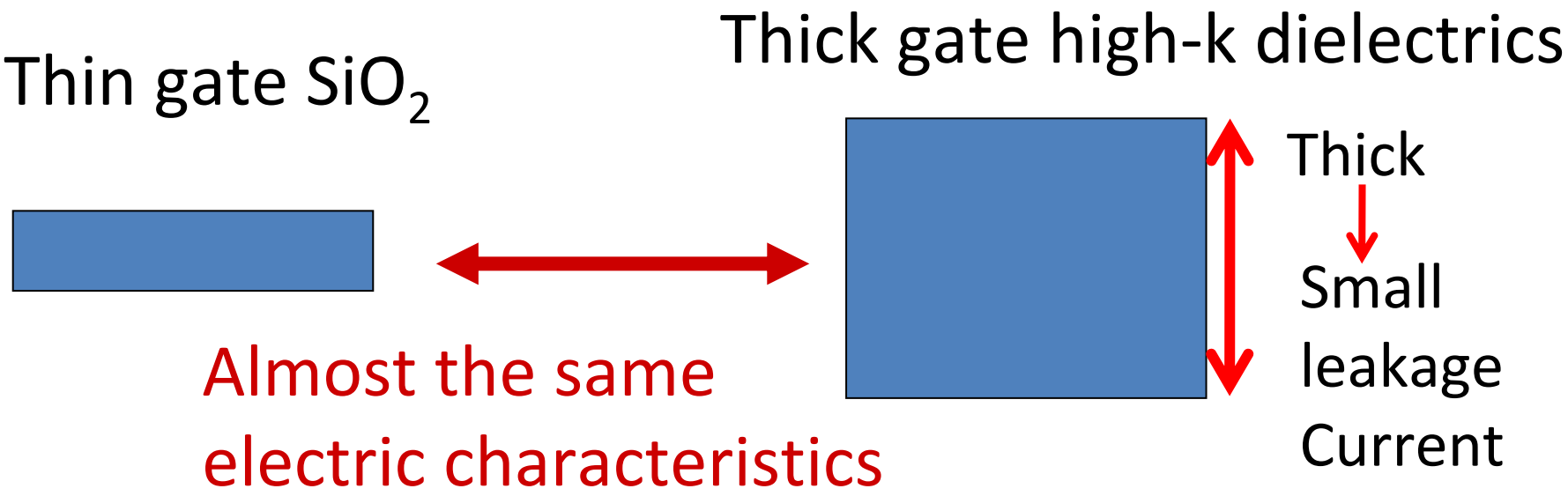
By Robert Chau, IWGI 2003

So, we are now in the limitation of downsizing?

Do you believe this or do not?

There is a solution! K: Dielectric Constant

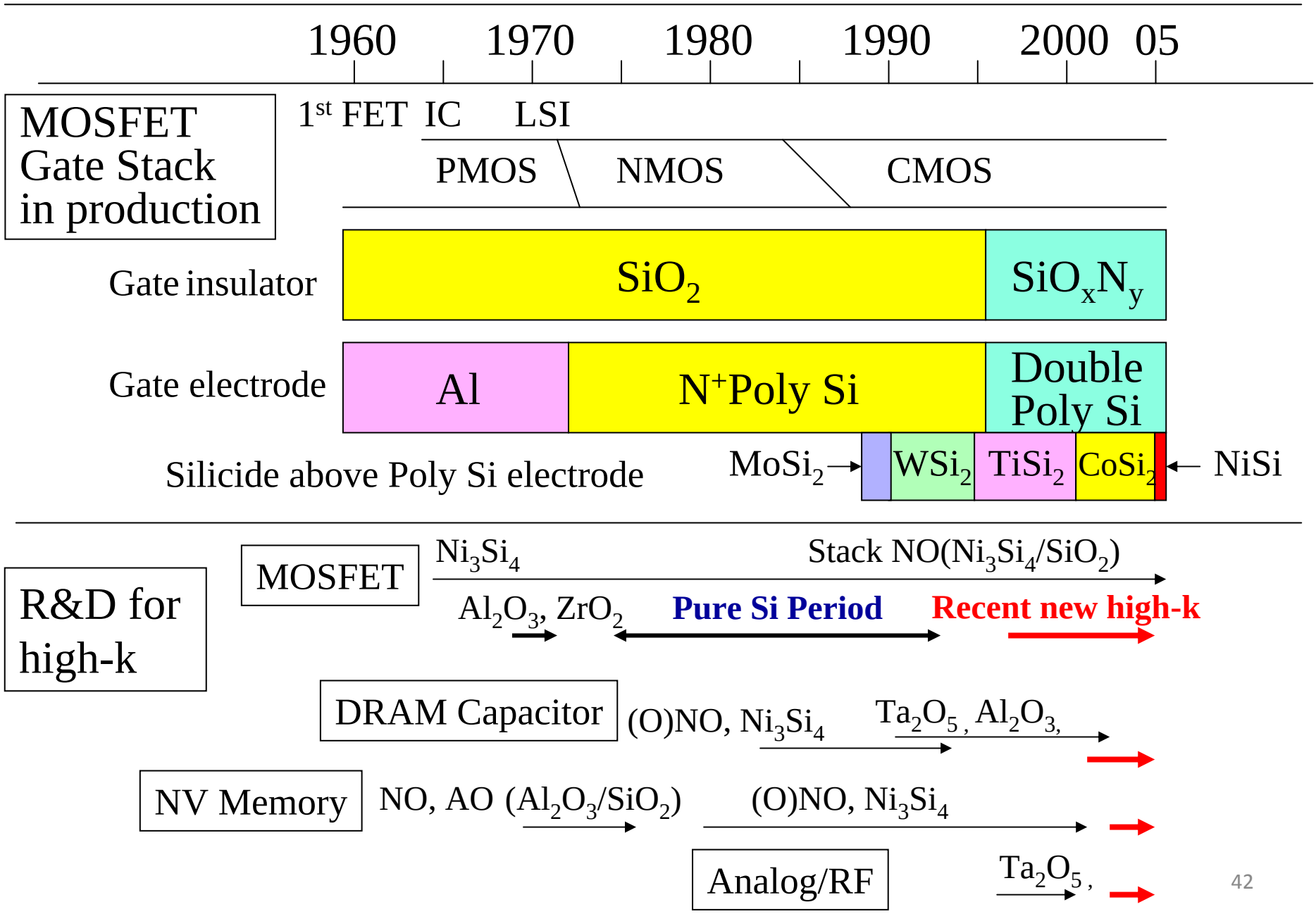
To use high-k dielectrics



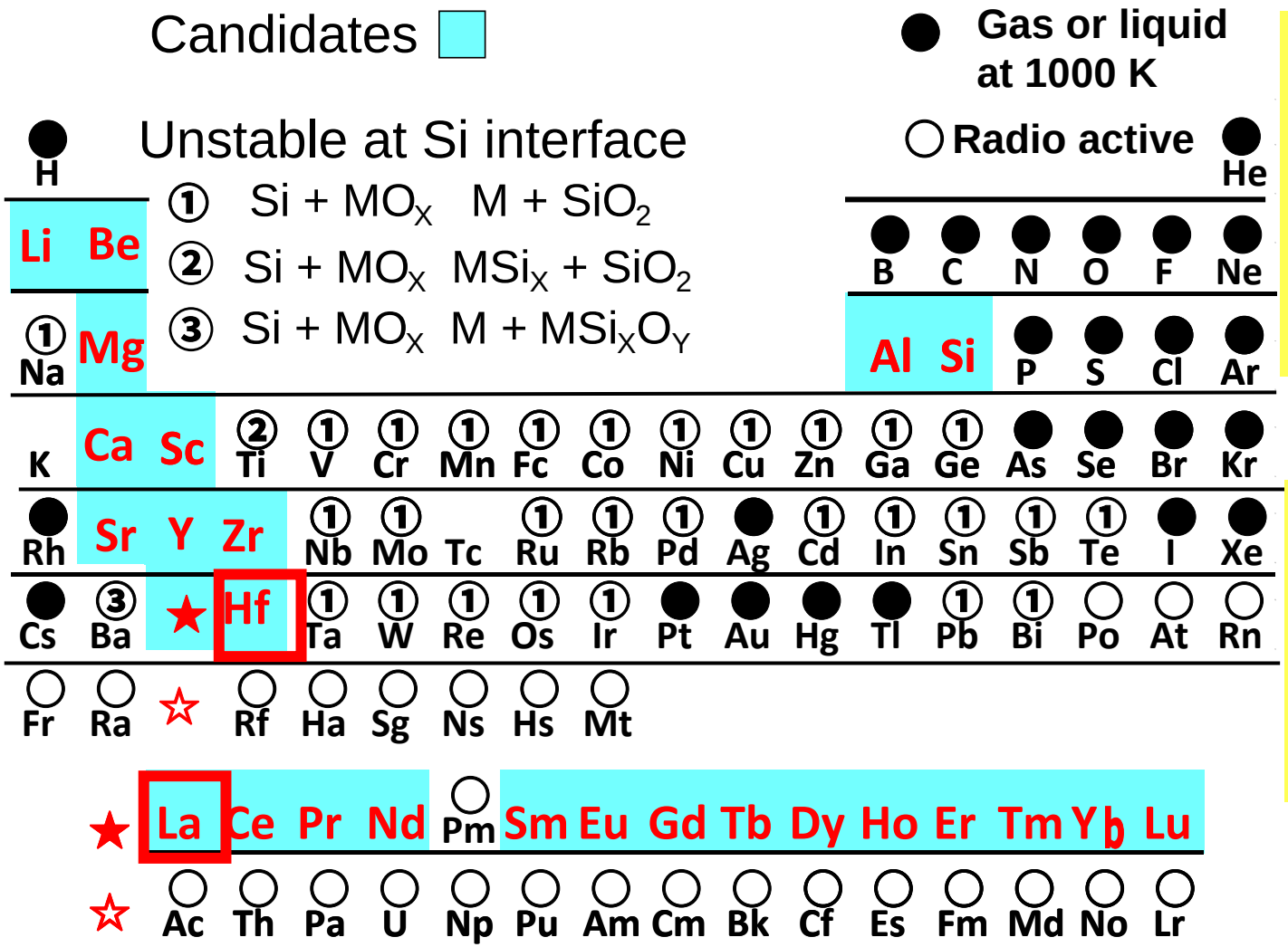
However, very difficult and big challenge!

Remember MOSFET had not been realized without Si/SiO_2!

Historical trend of high-k R& D



Choice of High-k elements for oxide



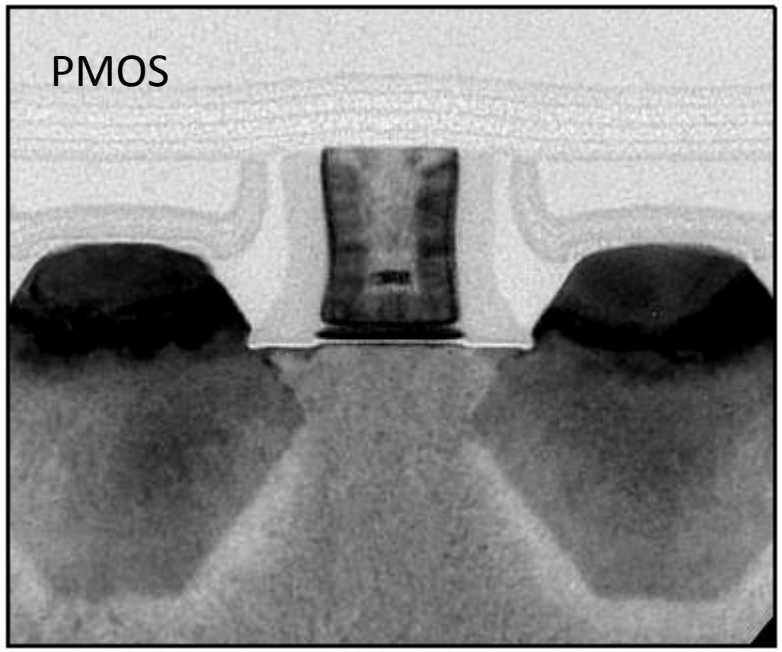
HfO_2 based dielectrics are selected as the first generation materials, because of their merit in
1) band-offset,
2) dielectric constant
3) thermal stability

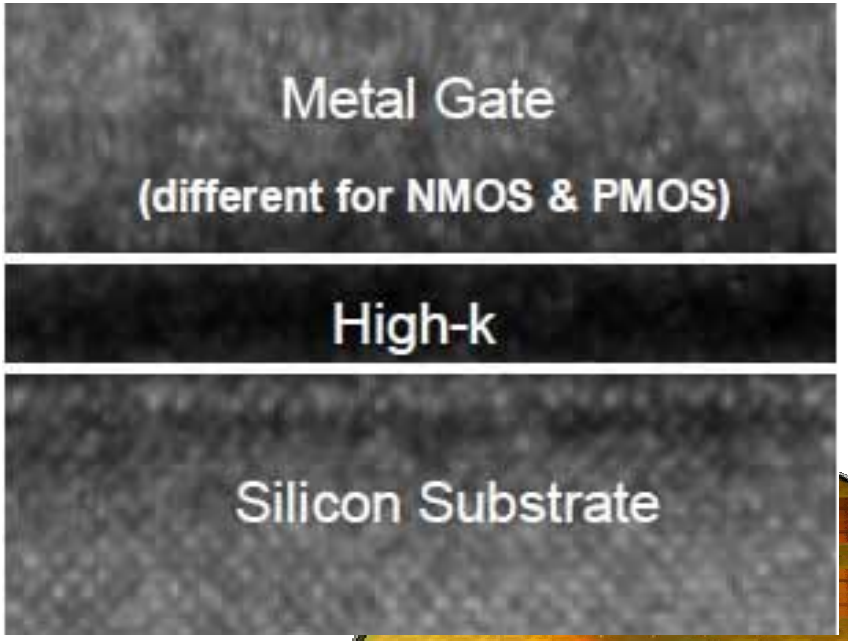
La_2O_3 based dielectrics are thought to be the next generation materials, which may not need a thicker interfacial layer

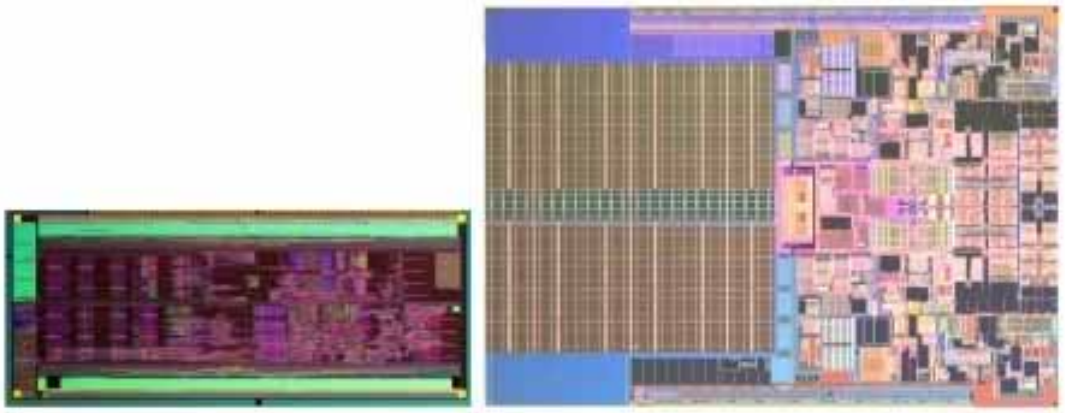
R. Hauser, IEDM Short Course, 1999
Hubbard and Schlom, J Mater Res 11 2757 (1996)

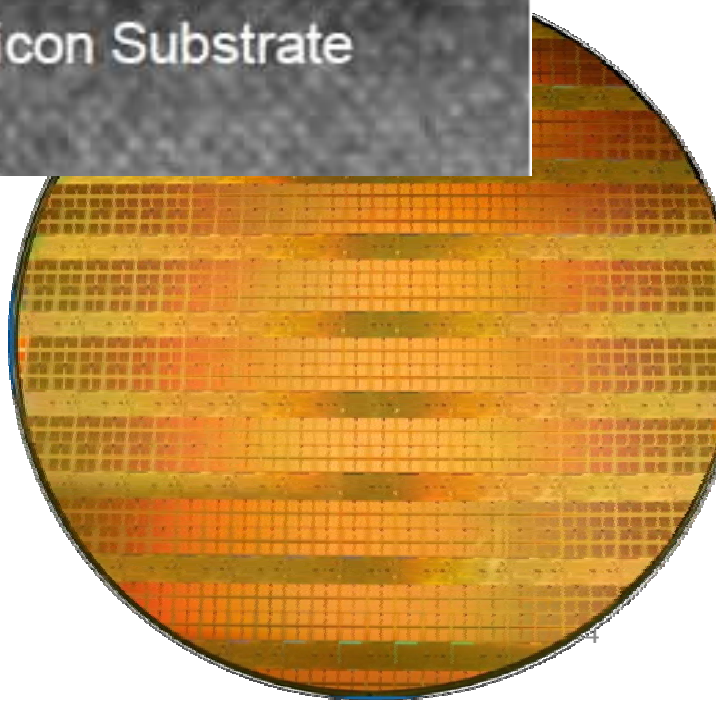
High-k gate insulator MOSFETs for Intel: EOT=1nm

EOT: Equivalent Oxide Thickness

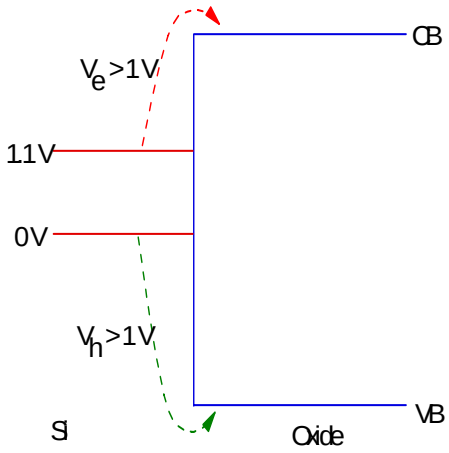




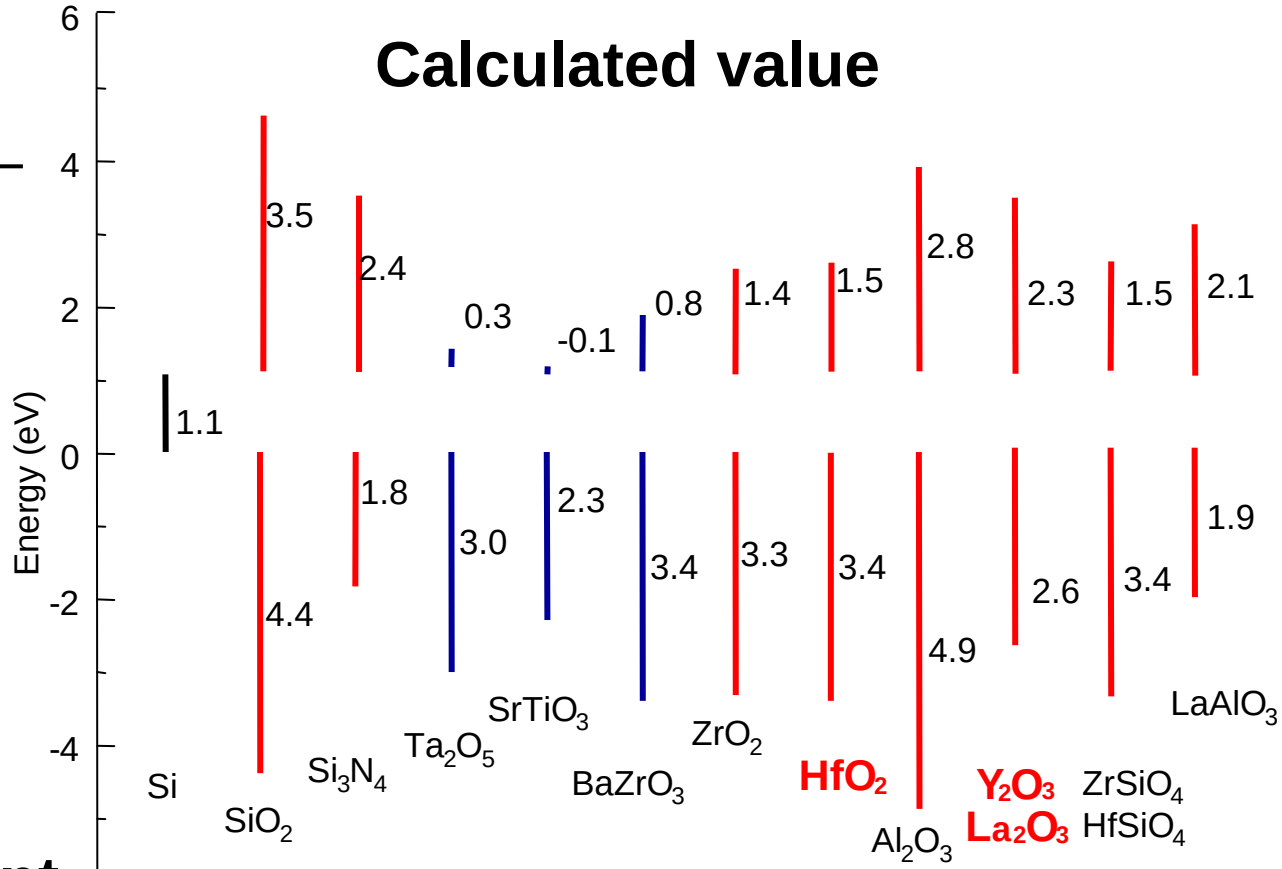




Band Offsets



Dielectric constant



J Robertson, J Vac Sci Technol B **18** 1785 (2000)

SiO2; 4
Si3N4: ~ 7
Al2O3: ~ 9

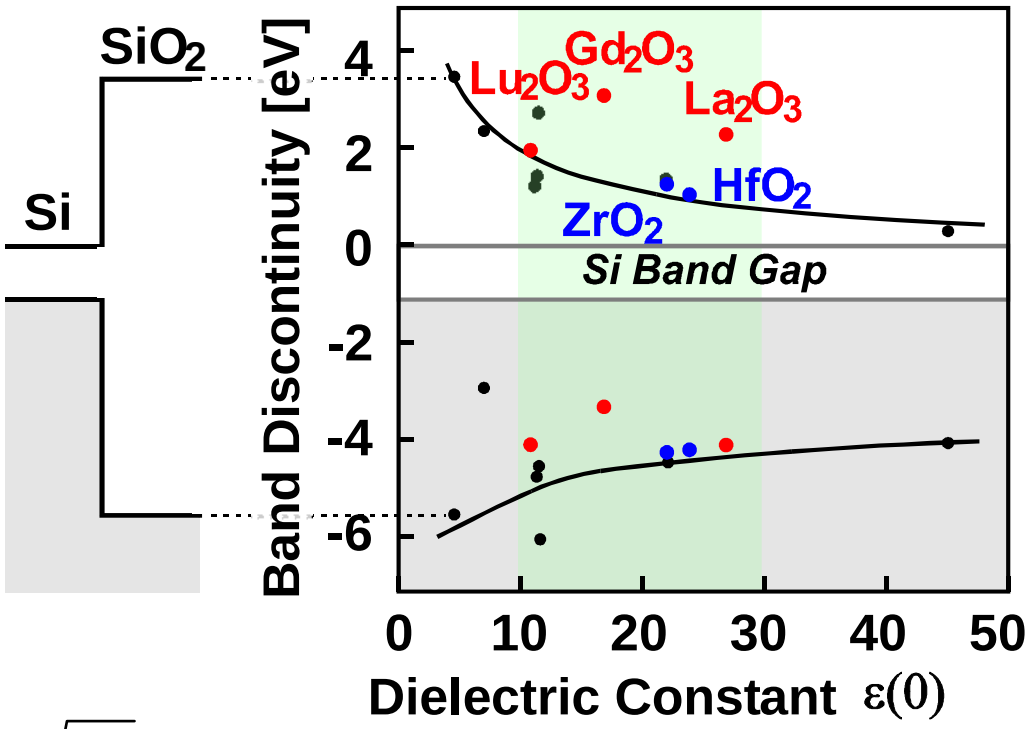
Y2O3; ~10
Gd2O3: ~10

HfO2; ~23
La2O3: ~27

HfO2 was chosen for the 1st generation
La2O3 is more difficult material to treat

Dielectric constant value vs. Band offset (Measured)

SiO_2	3.9	$NdAlO_3$	22.5
Al_xSi_yOz		$PrAlO_3$	25
$(Ba,Sr)TiO_3$	200-300	Si_3N_4	7
$BeAl_2O4$	8.3-9.43	$SmAlO_3$	19
CeO_2	16.6-26	$SrTiO_3$	150-250
$CeHfO_4$	10-20	Ta_2O_5	25-24
$CoTiO_3/Si_3N_4$		Ta_2O_5-TiO_2	
$EuAlO_3$	22.5	TiO_2	86-95
HfO_2	26-30	TiO_2/Si_3N_4	
Hf silicate	11	Y_2O_3	8-11.6
La_2O_3	20.8	$Y_xSi_yO_z$	
$LaScO_3$	30	ZrO_2	22.2-28
La_2SiO_5		Zr-Al-O	
$MgAl_2O_4$		Zr silicate	
		$(Zr,Sn)TiO_4$	40-60

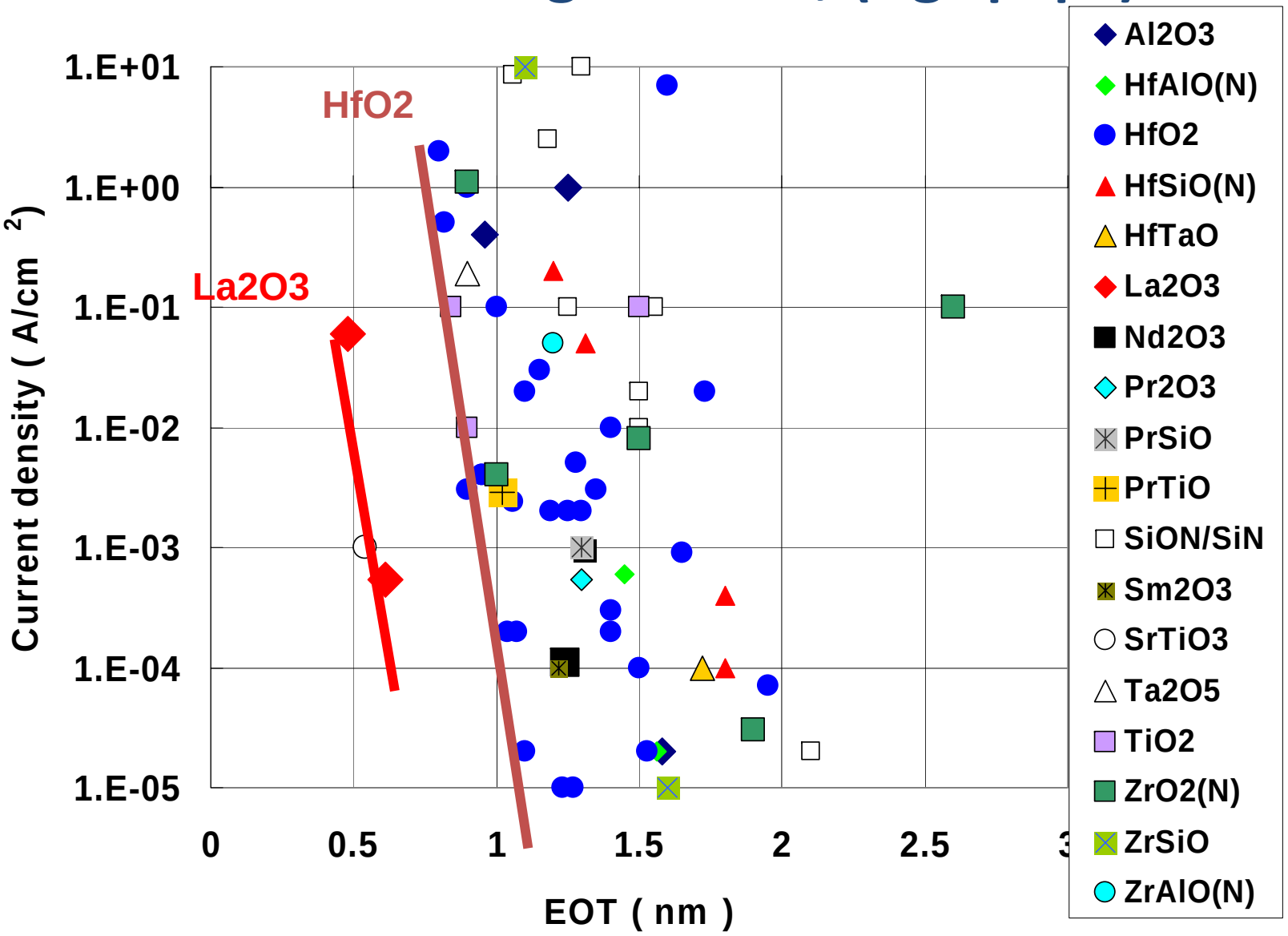


$\sqrt{\phi_B} * k$: Figure of Merit of High-k

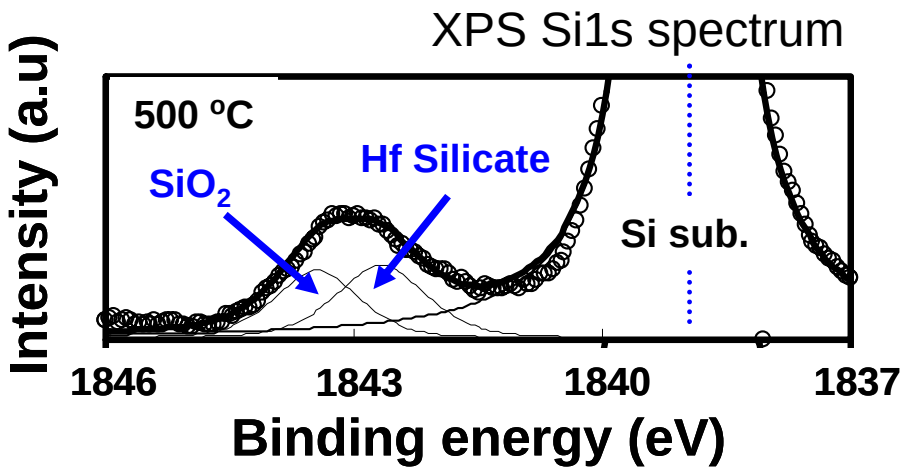
C.A. Billmann et al.,, MRS Spring Symp., 1999,
R.D.Shannon, J. Appl. Phys., 73, 348, 1993
S. De Gebdt, IEDM Short Coyuse, 2004

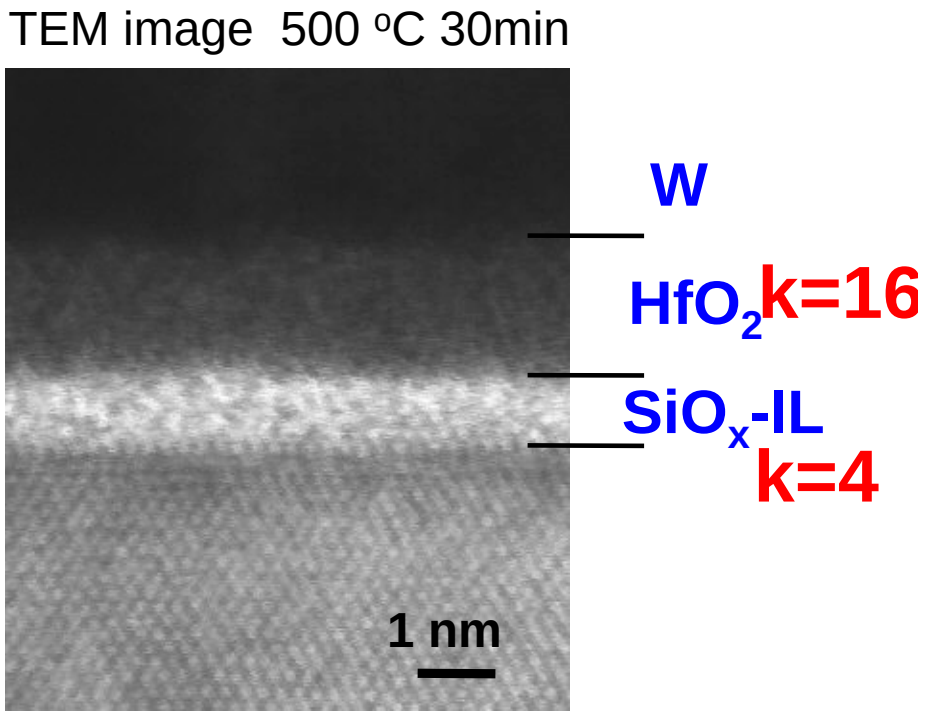
T. Hattori, INFOS , 2003

Gate Leakage vs EOT, (Vg=|1|V)



SiO_x-IL growth at HfO_2/Si Interface





Phase separator

$$HfO_2 + Si + O_2 \rightarrow HfO_2 + Si + 2O^* \rightarrow HfO_2 + SiO_2$$

H. Shimizu, JJAP, 44, pp. 6131

Oxygen supplied from W gate electrode

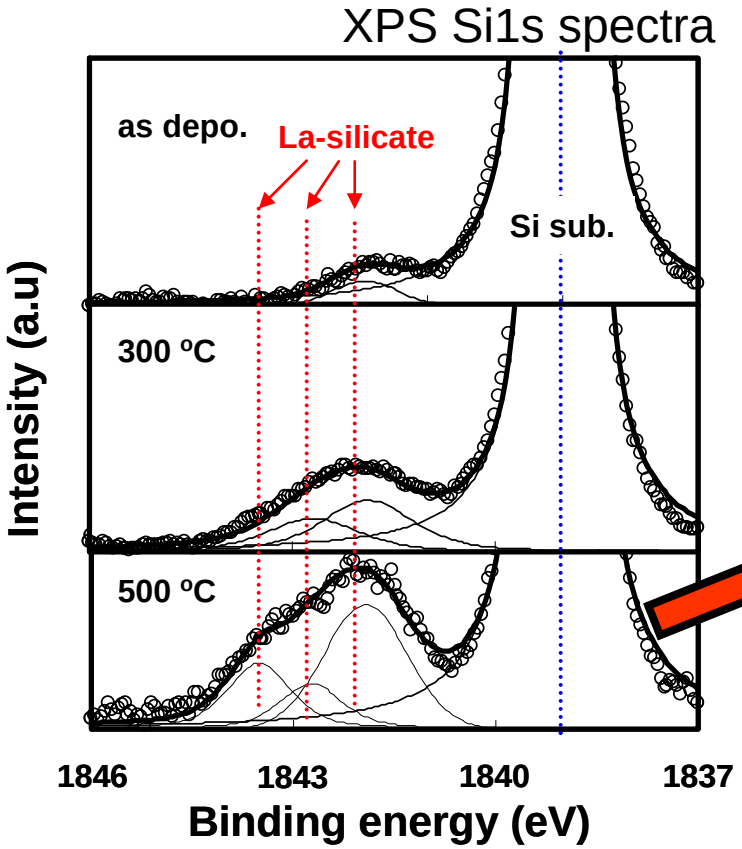
D.J.Lichtenwalner, Tans. ECS 11, 319

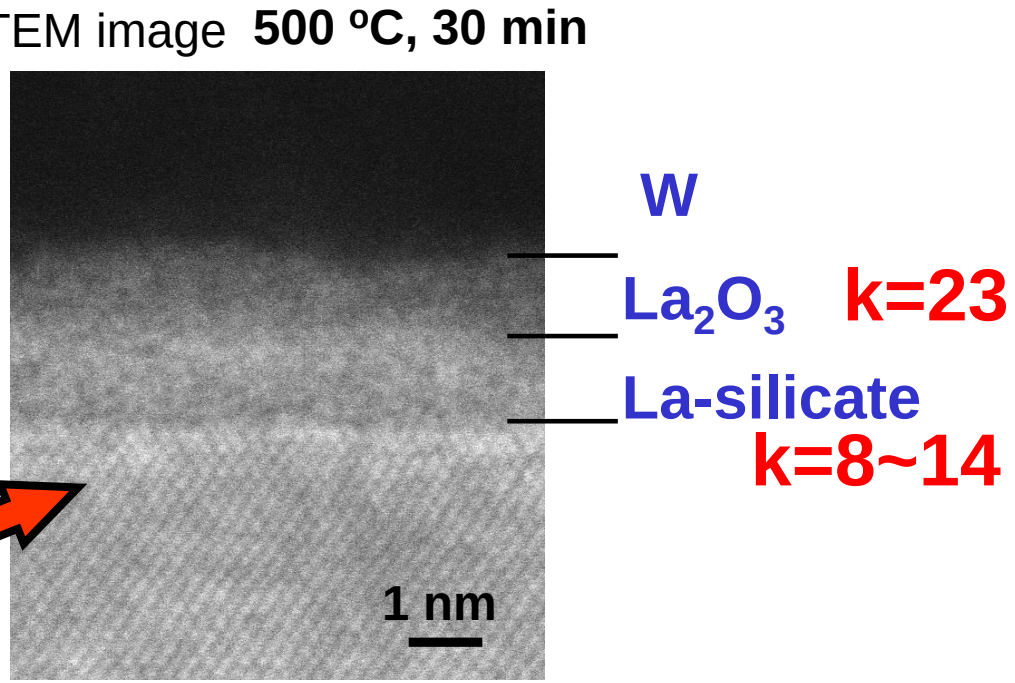
SiO_x-IL is formed after annealing

Oxygen control is required for optimizing the reaction

La-Silicate Reaction at La_2O_3/Si

Direct contact high-k/Si is possible





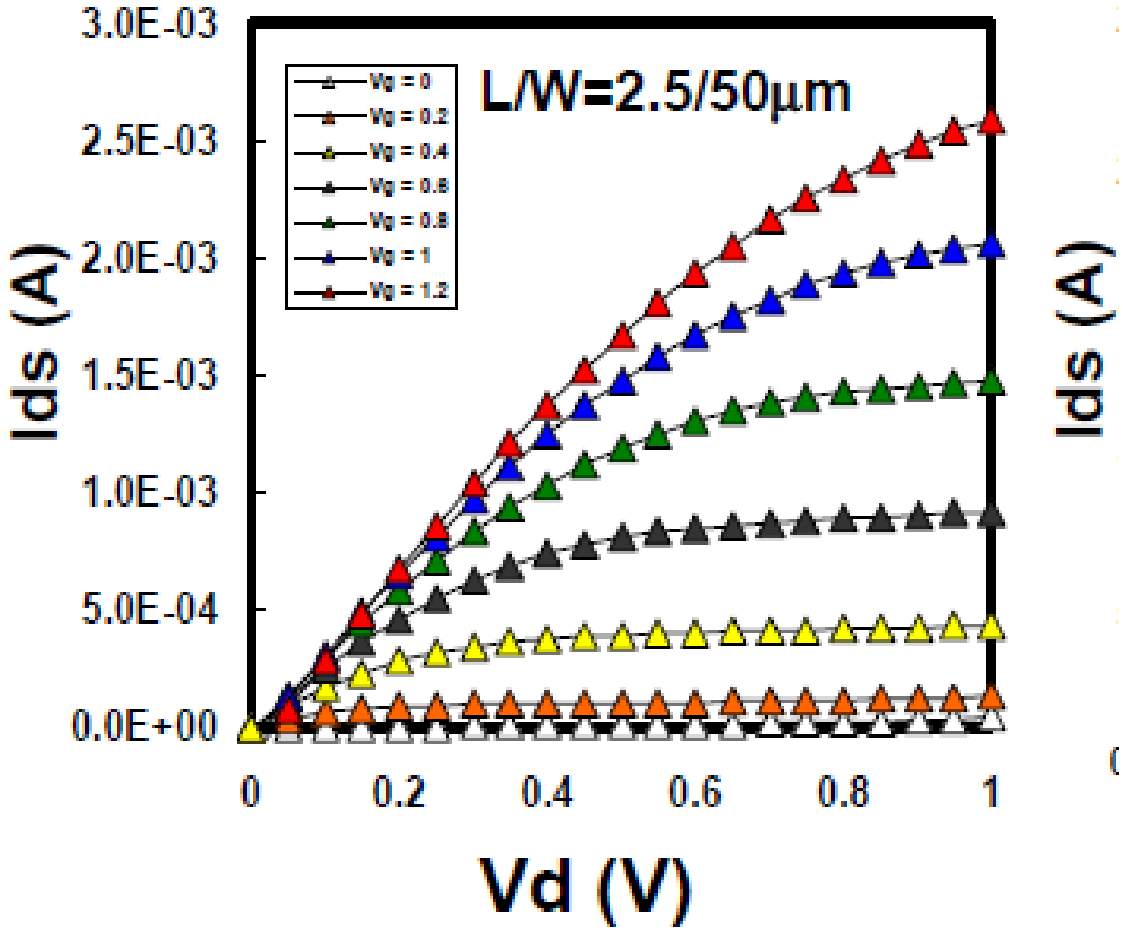
$La_2O_3 + Si + nO_2$
→ La_2SiO_5, $La_2Si_2O_7$,
$La_{9.33}Si_6O_{26}$, $La_{10}(SiO_4)_6O_3$, etc.

La_2O_3 can achieve direct contact of high-k/Si

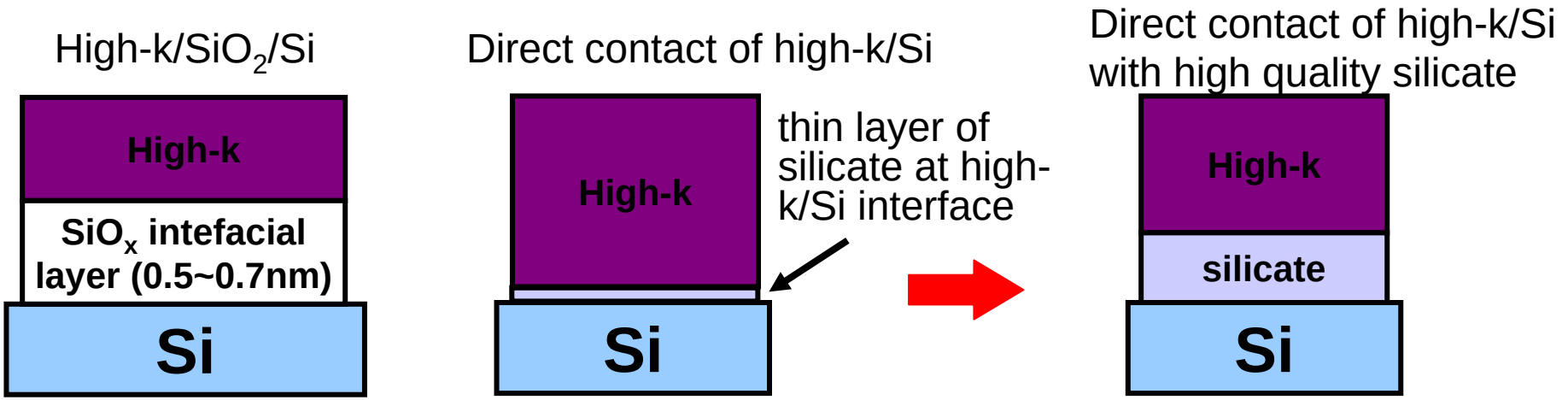
EOT = 0.48 nm

Our results

Transistor with La2O3 gate insulator



Direct contact of high-k/Si with La-silicate foramtion



EOT scaling
→limitted by IL

Issues in Dit, realiability
μ_{eff}, etc.

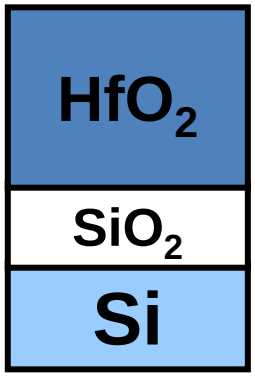
Nice FET operation
→EOT scaling

※EOT:Equivalent oxide thickness

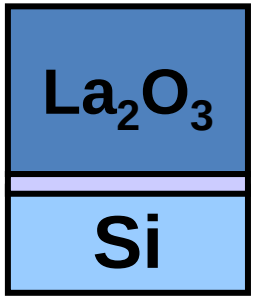
Originality

Foramtion of high-k quality La-silicate using the reaction of La_2O_3 and Si substrate

High quality La-silicate



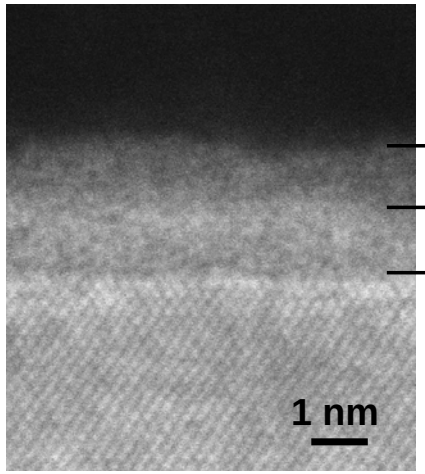
- HfO_2 formes SiO_2 at interface



La-rich silicate La_2SiO_5

- μ_{eff} degradation
- defects in silicate (hysteresis)
- large D_{it} ($10^{13}cm^{-2}/eV$)

La_2O_3/Si after 500 ^oC 30min



$La_2O_3 + Si + nO_2$

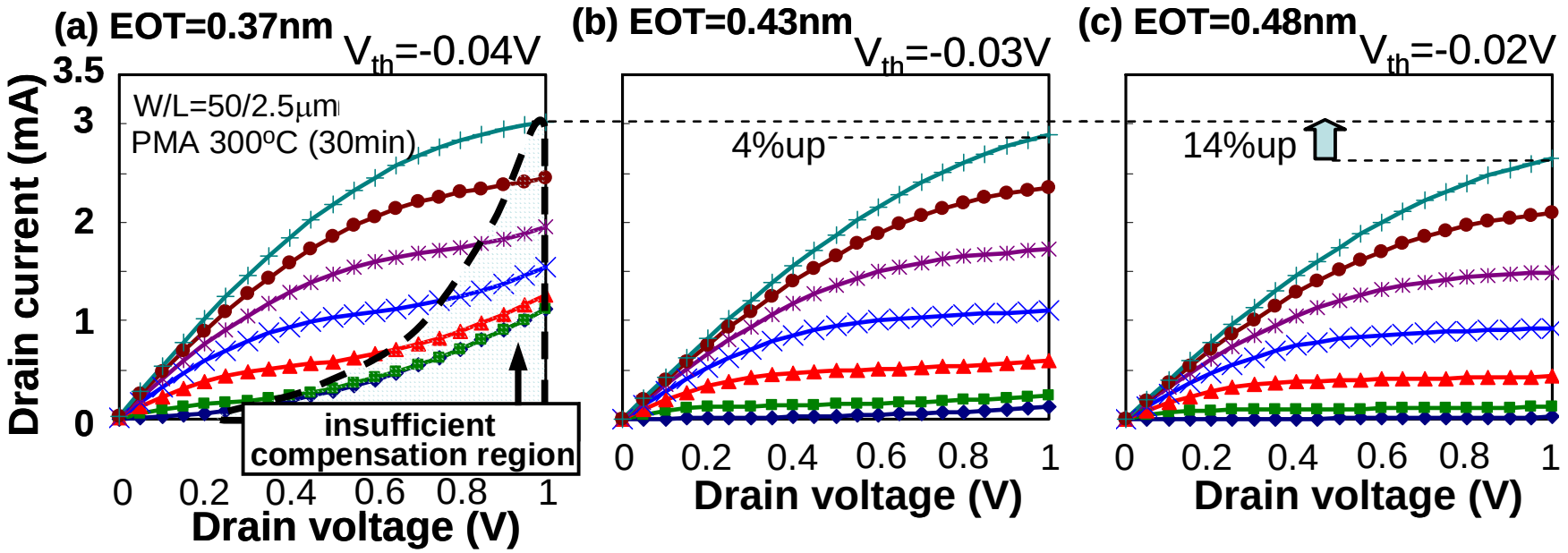
→ La_2SiO_5, $La_{9.33}Si_6O_{26}$, $La_{10}(SiO_4)_6O_3$, $La_2Si_2O_7$, etc.

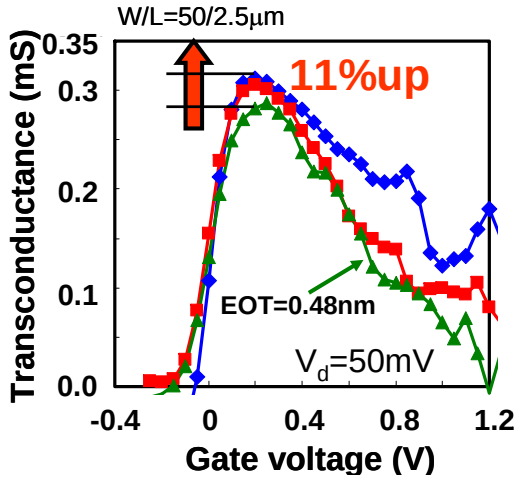
La-rich ⟷ Si-rich

Proper oxygen atom supply to form high quality Si-rich La-silicate

K. Kakushima, et al., ESSDERC '08, Edinburgh

FET operation of EOT=0.37nm





Direct contact of high-k/Si using La_2O_3/silicate

Improvement in both drain current and transconductance

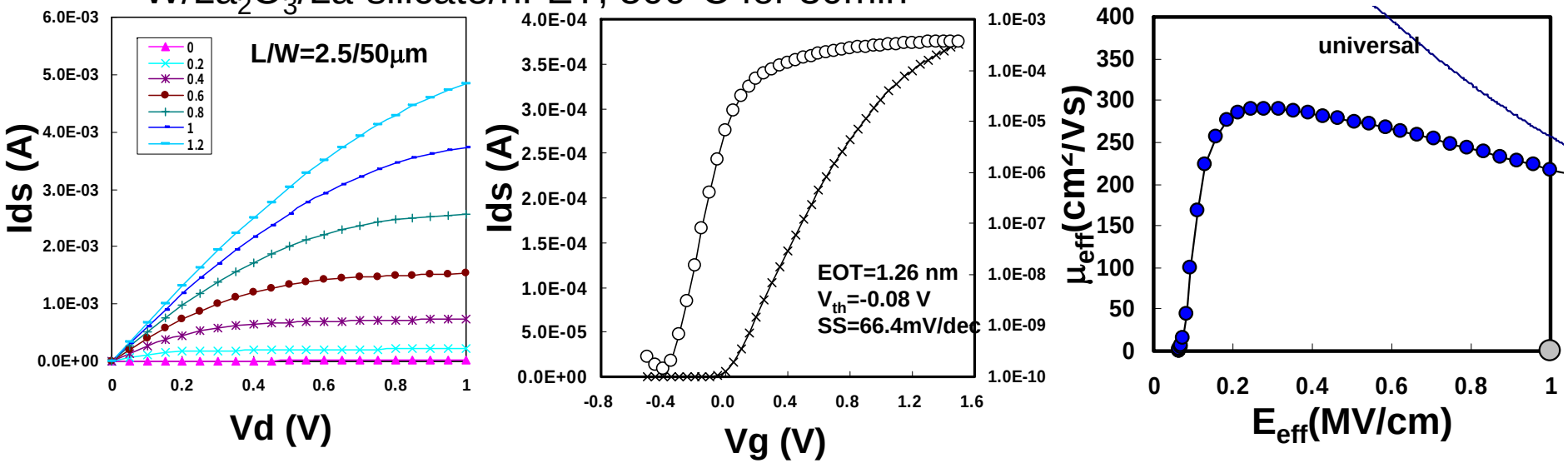
EOT scaling below 0.5nm is still useful

K. Kakushima, et al., Microelectron. Reliab., **50**, 790 (2010)

(2) Direct high-k/Si using La-silicate/Si with high μ_{eff}

EOT=1.26nm

W/La_2O_3/La-silicate/nFET, 500°C for 30min



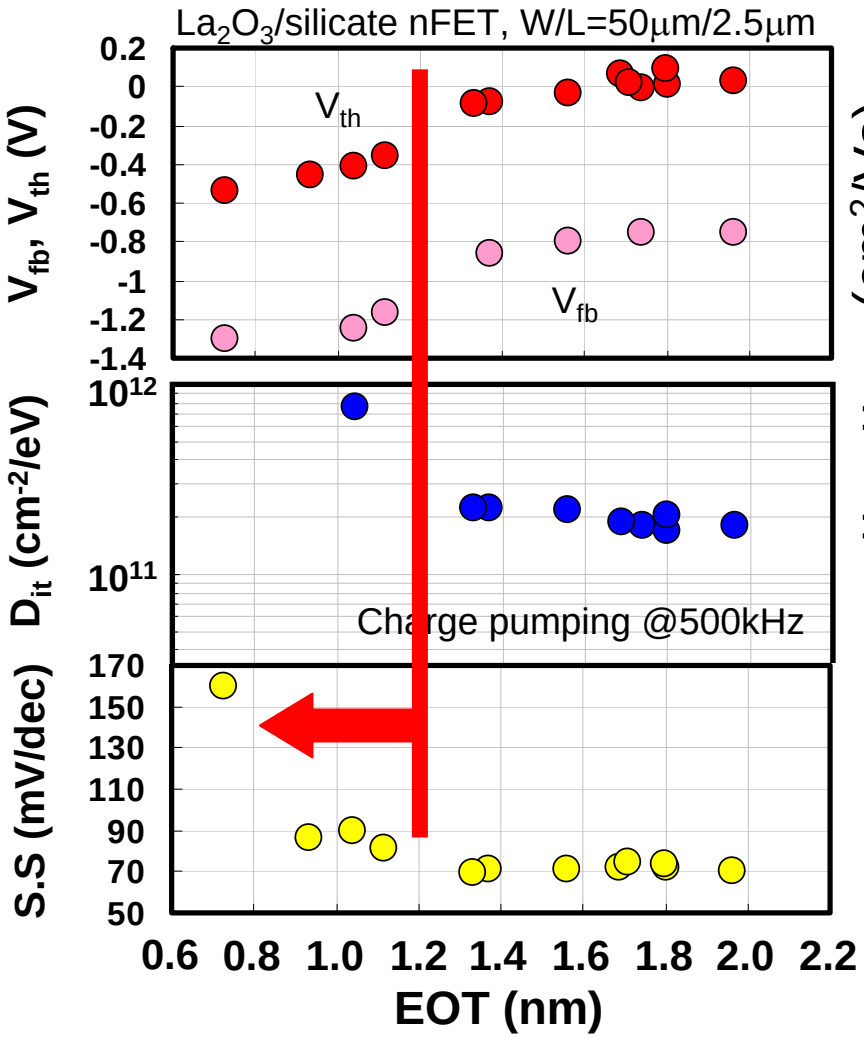
High peak μ_{eff} of 300cm^2/Vs with 500°C annealing

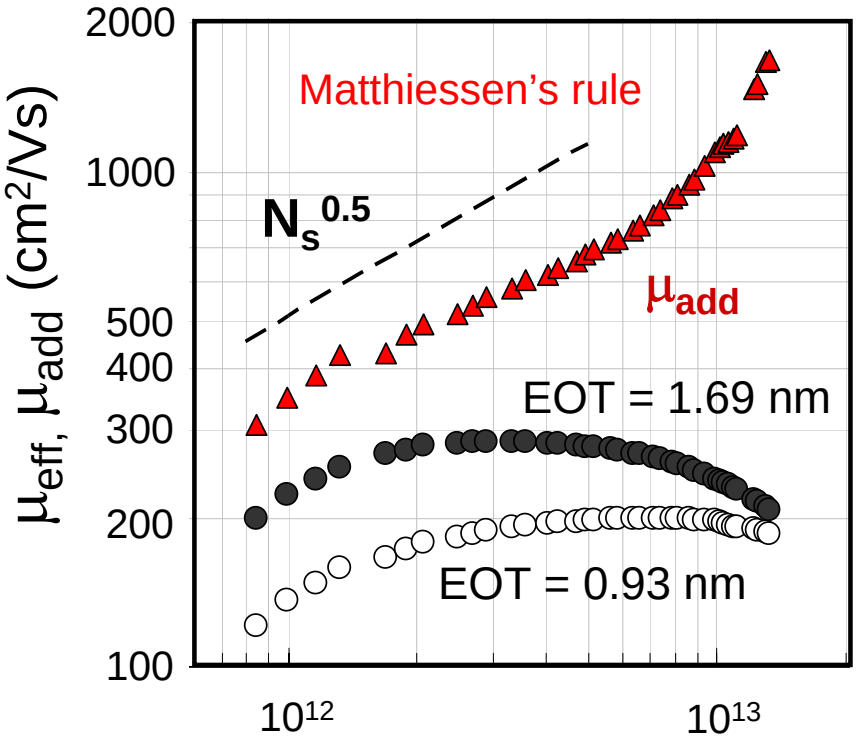
→ nice proerties of Si-rich La-silicate/Si interface

Fairly nice properties can be achieved even with direct high-k/Si interface (EOT~1.2)

K. Kakushima, et al., ESSDERC '08, Edinburgh

(3) Origin of degradations at EOT<1.3nm





Additional scattering of ~$N_s^{0.5}$

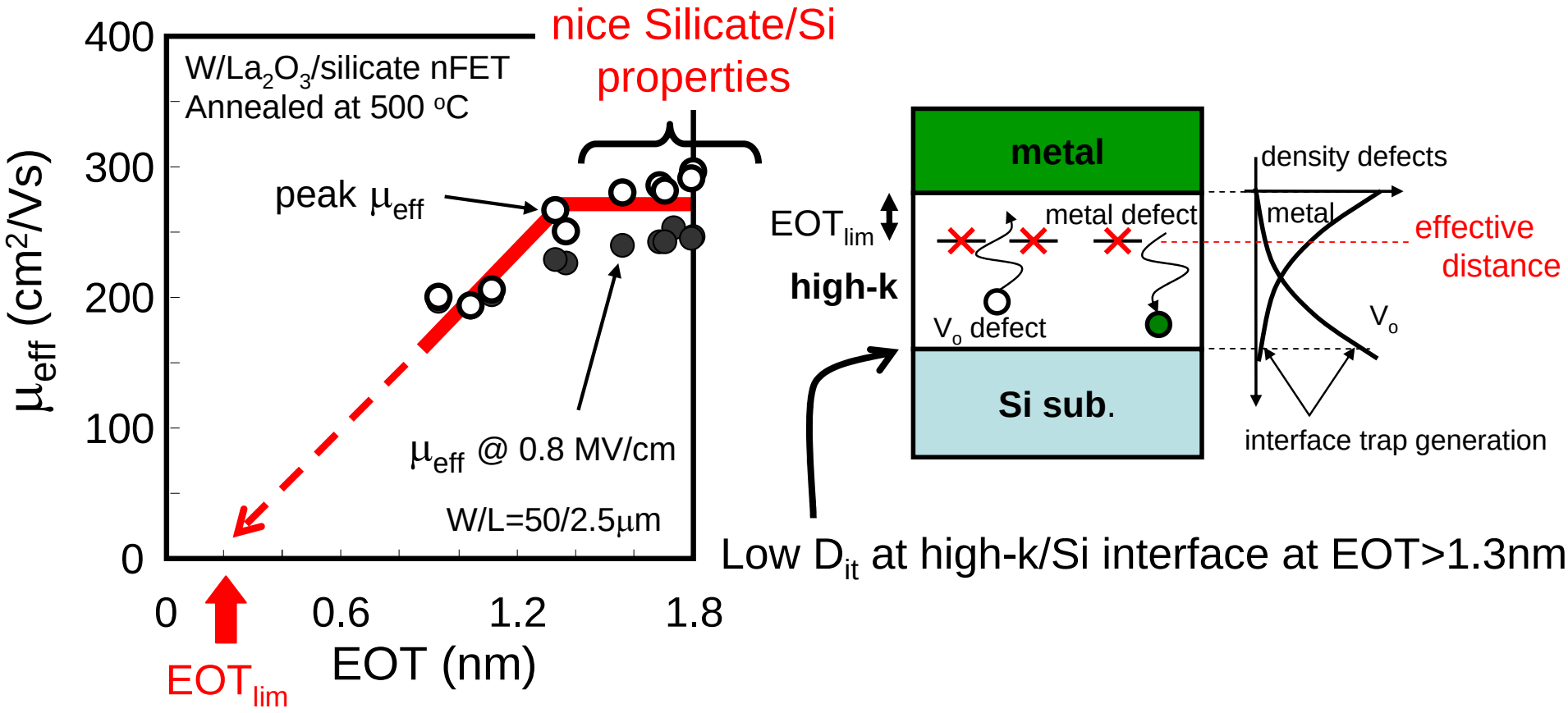
←remote Coulomb scattering

(Coulomb scattering in bulk Si ∝ N_s^{1})

Coulomb scattering from high-k at EOT<1.3nm

K. Kakushima, et al., Solid-State Electron., **54**, 715 (2010)

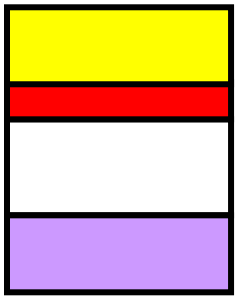
Defects from metal electrode



Metal atom diffusions to degrade the μ_{eff} in EOT<1.3nm

K. Kakushima, et al., Solid-State Electron., **54**, 715 (2010)

Gate Metal Induced Defects Compensation

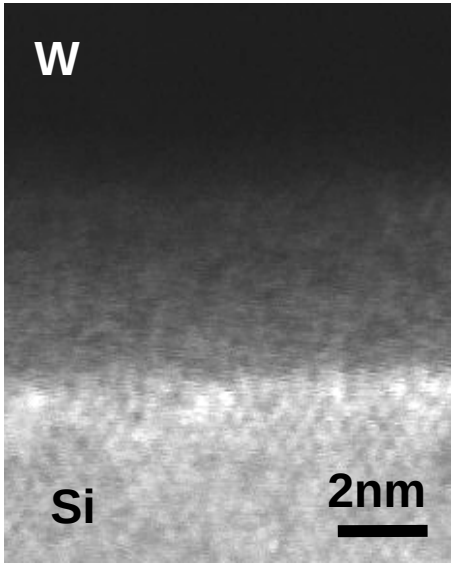


Metal Gate

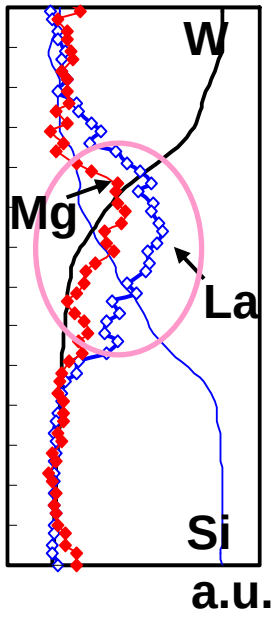
MgO

La2O3

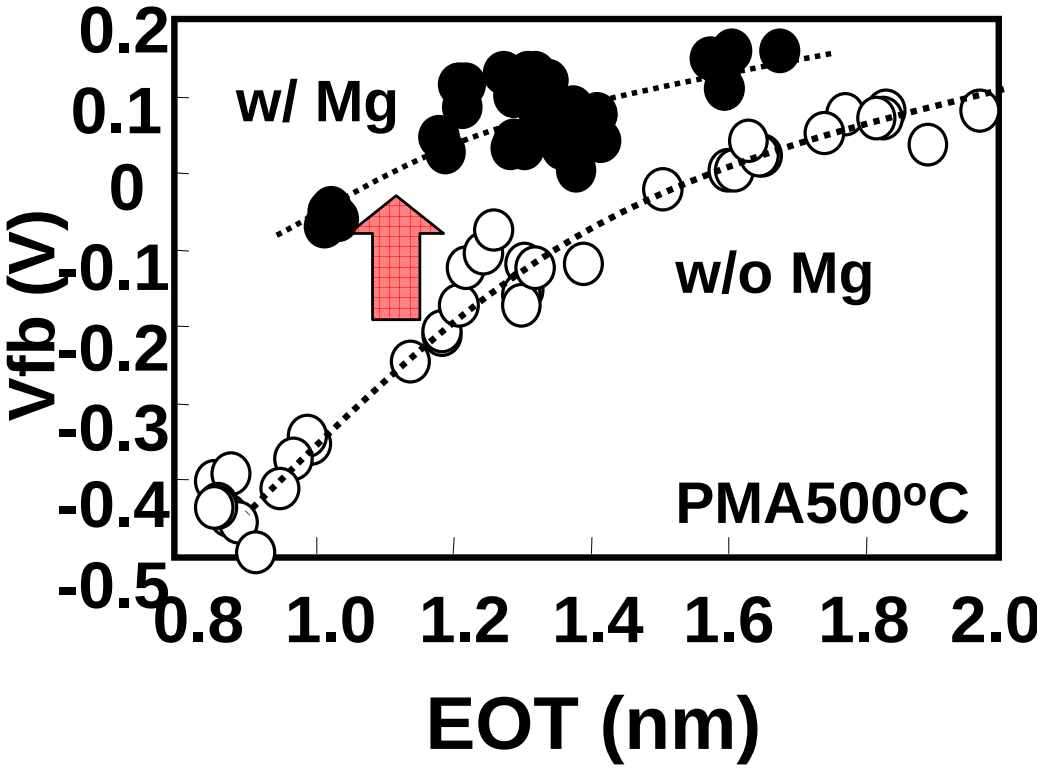
Si



TEM



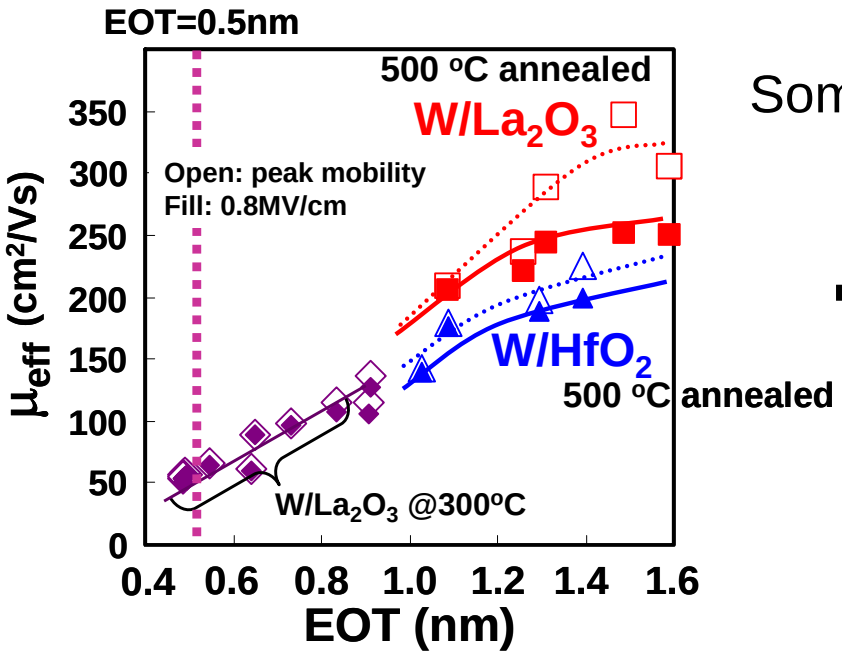
EDX



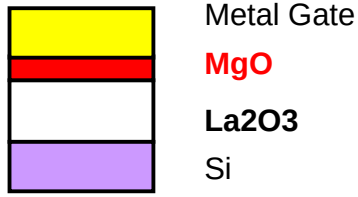
Suppression of aggressive shift in V_{fb}

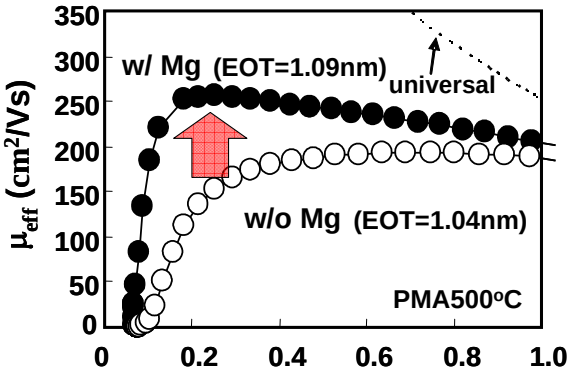
Challenge for thinning High-k

Degradation of mobility



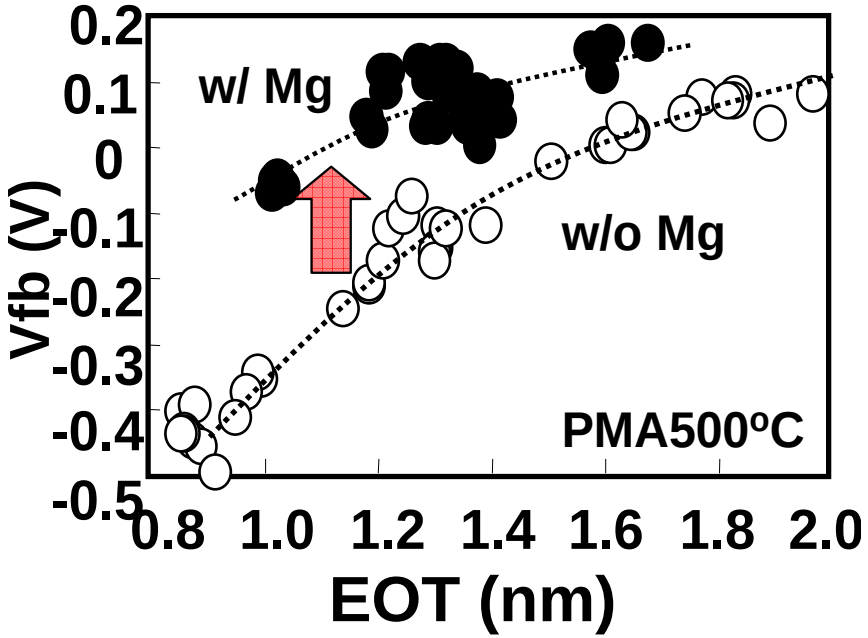
Some solution



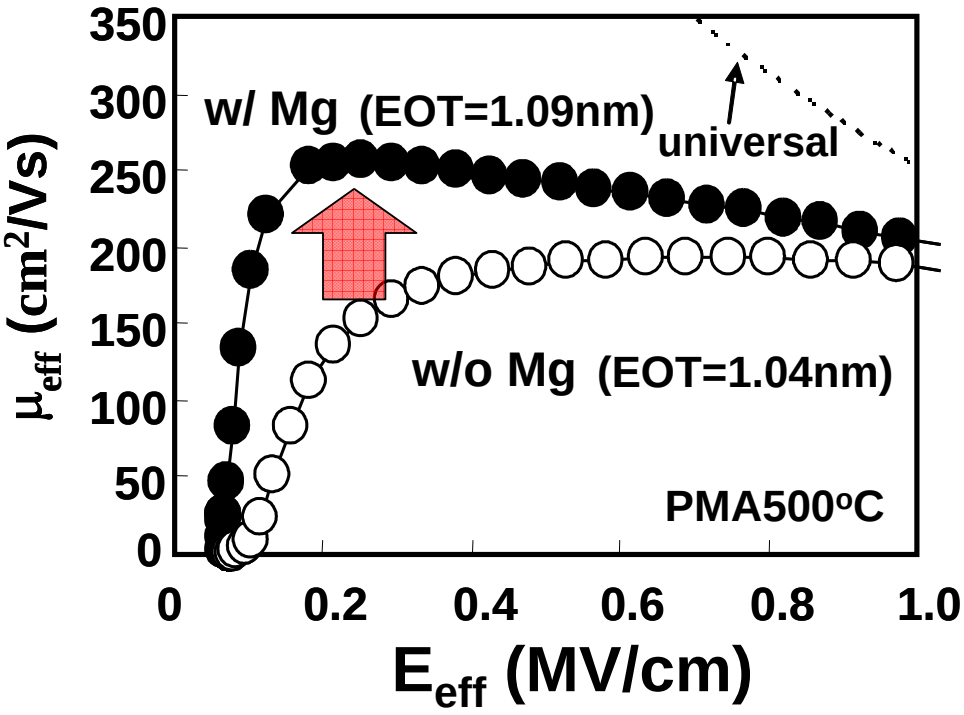


(5) μ_{eff} recovery with Mg incorportation

Mg incorporation into
La-silicate



Suppression of V_{fb} shift
at small EOT

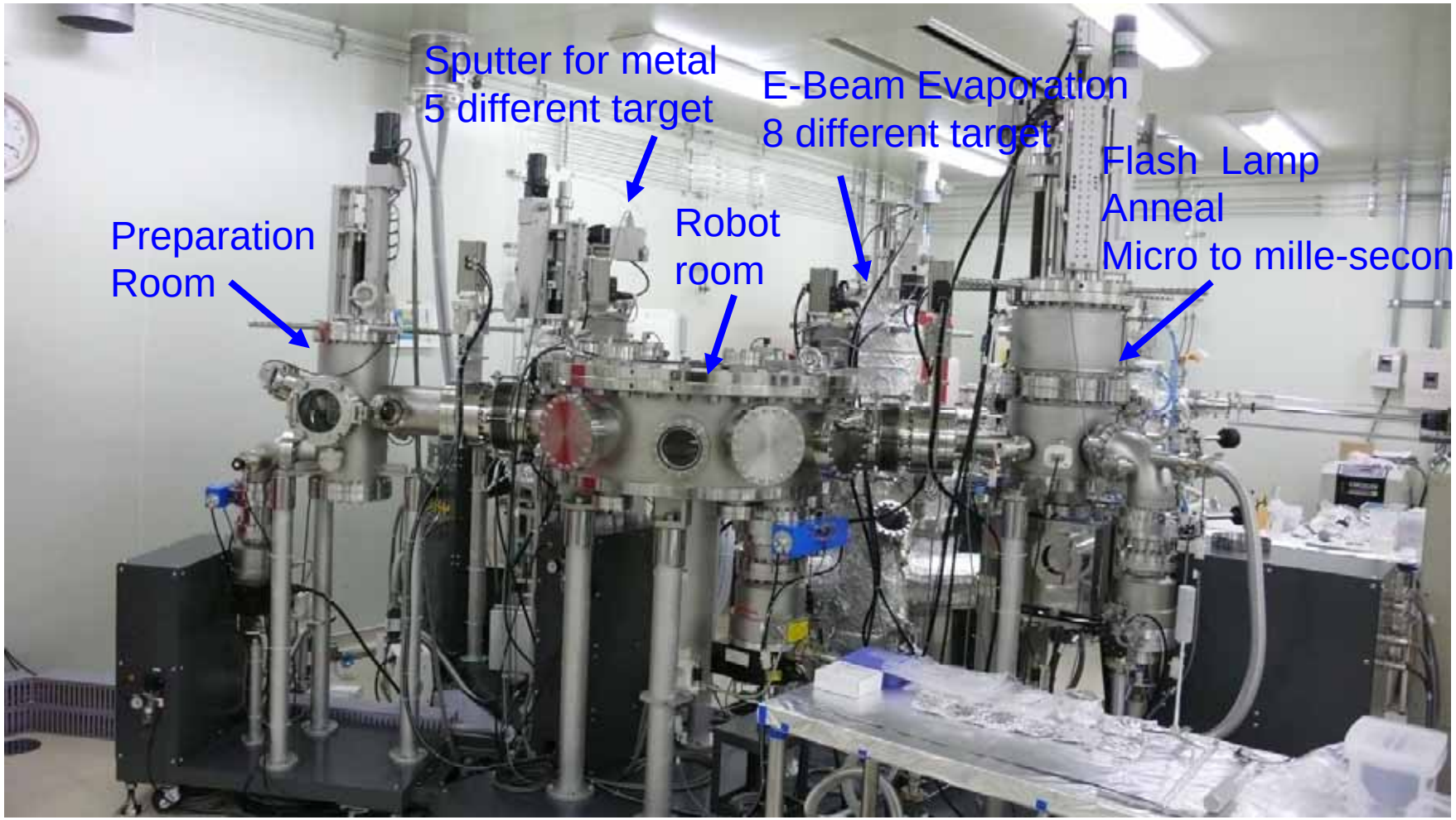


μ_{eff} recovery

Incorprotation of Mg into La-silicate can recover the μ_{eff}

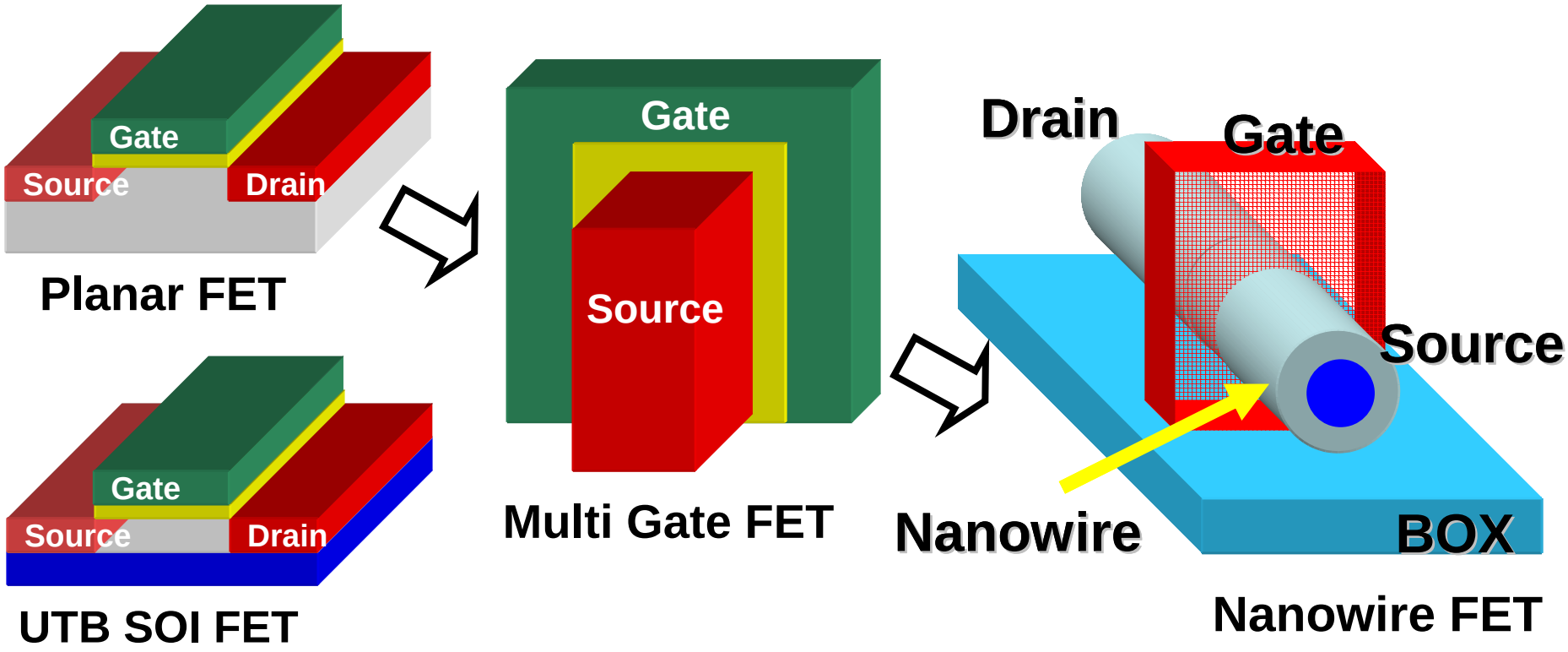
T. Koyanagi, K. Tachi, K. Okamoto, K. Kakushima, et al, Jpn. J. Appl. Phys., **48**, 05DC02 (2009)

Cluster tool for high-k thin film deposition



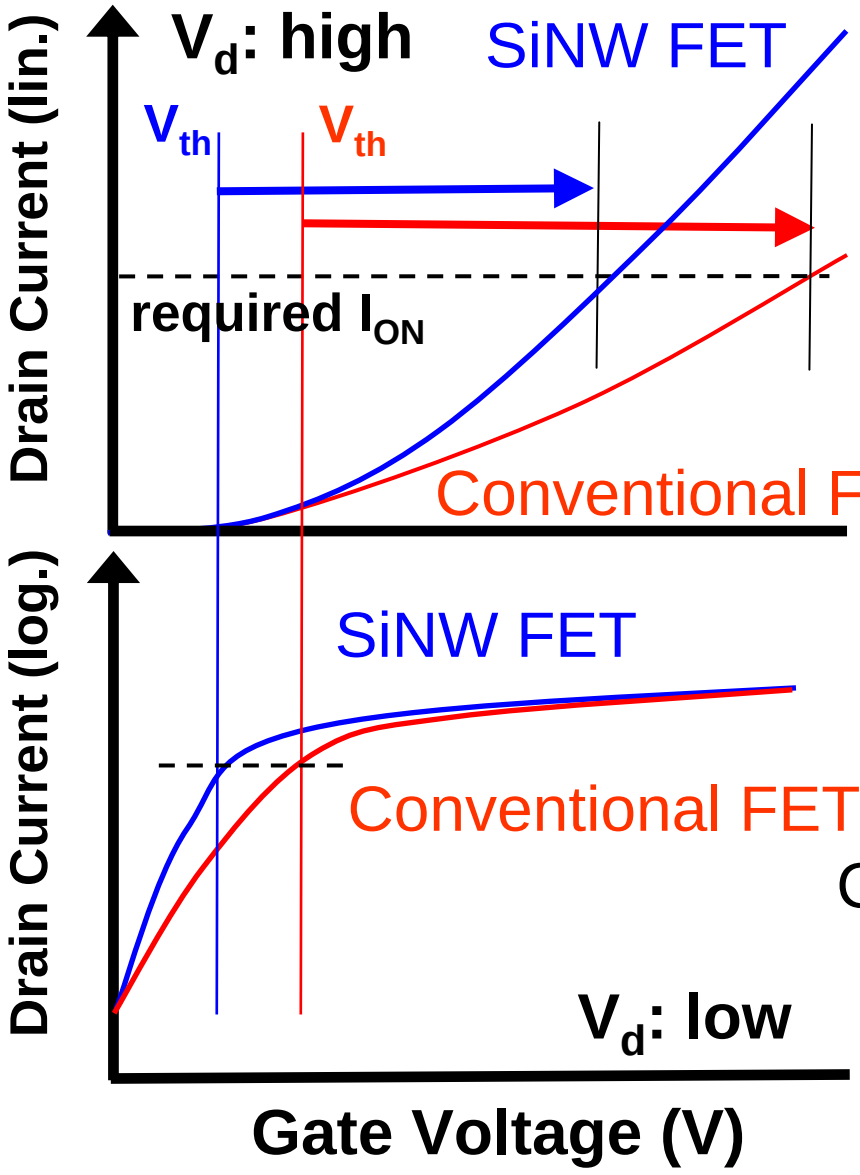
Si Nanowire FET

Introduction of SiNW FETs



- ✓Effective electrostatic control of 1-D channel due to the gate all-around structure.
- ✓Low I_{off} can be achieved.

Toward a Reduction of Power Supply Voltage



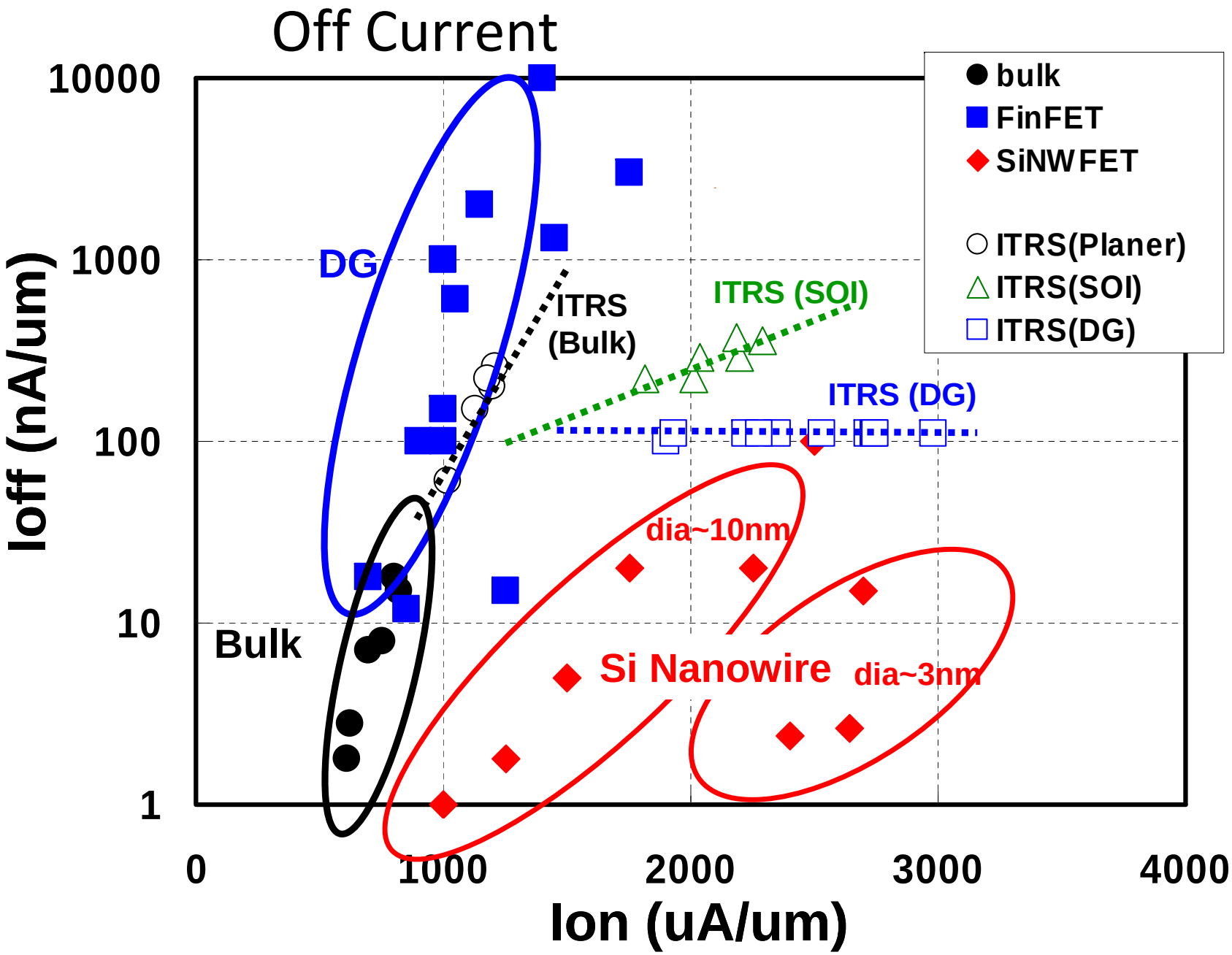
Higher drivability

Required I_{ON} can be achieved with lower overdrive voltage.

Reduction of V_{DD} and low power consumption

Capacity for reduction of V_{th}

Lower I_{OFF}


Off Current
10000
1000
100
10
1
Ioff (nA/um)
0
1000
2000
3000
4000
Ion (uA/um)
bulk
FinFET
SiNWFET
ITRS(Planer)
ITRS(SOI)
ITRS(DG)
DG
ITRS
(Bulk)
ITRS (SOI)
ITRS (DG)
dia~10nm
Bulk
Si Nanowire
dia~3nm

Nanowire FET

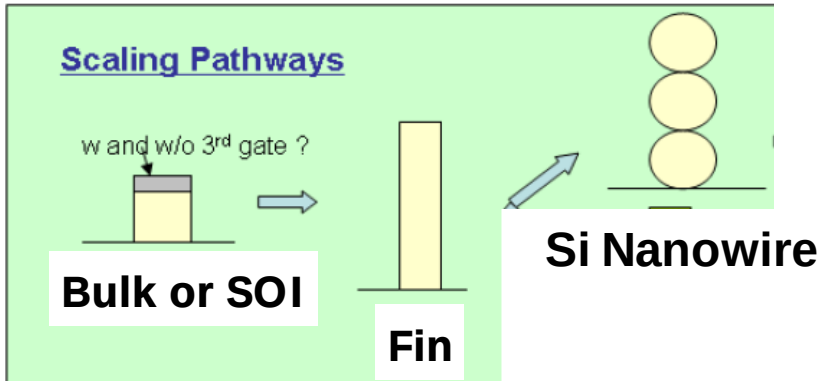
First Year of IC Production	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024
Device Structures																
Planar bulk	←							→								
FDSOI					←								→			
Multiple Gate							←									→

Nanowire FET

Multiple Gate (Fin)FET

ITRS 2009

Bulk → Fin → Nanowire

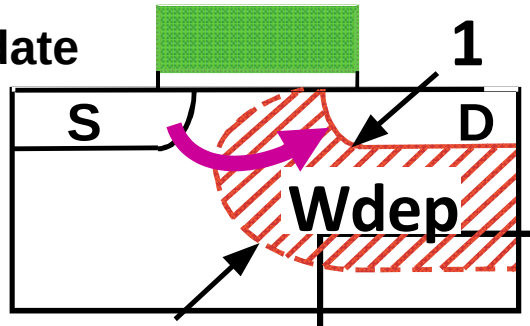


Si nanowire FET as a strong candidate

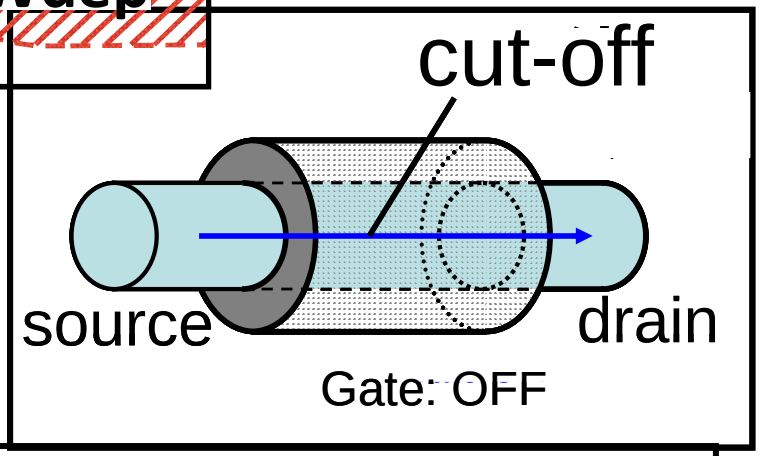
1. Compatibility with
   current CMOS process

2. Good controllability of I_{OFF}

3. High drive current

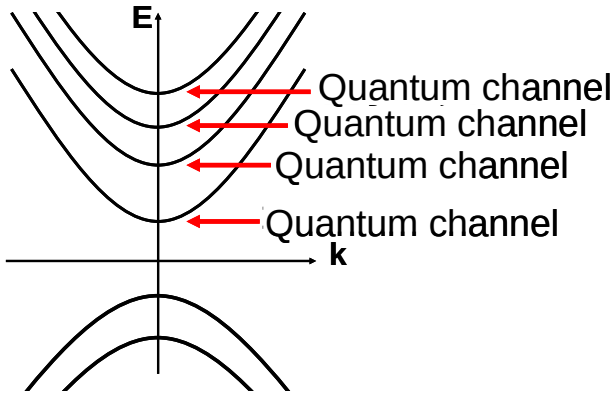


Leakage current

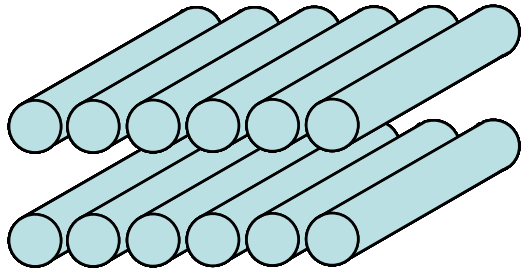


1D ballistic conduction

Multi quantum Channel

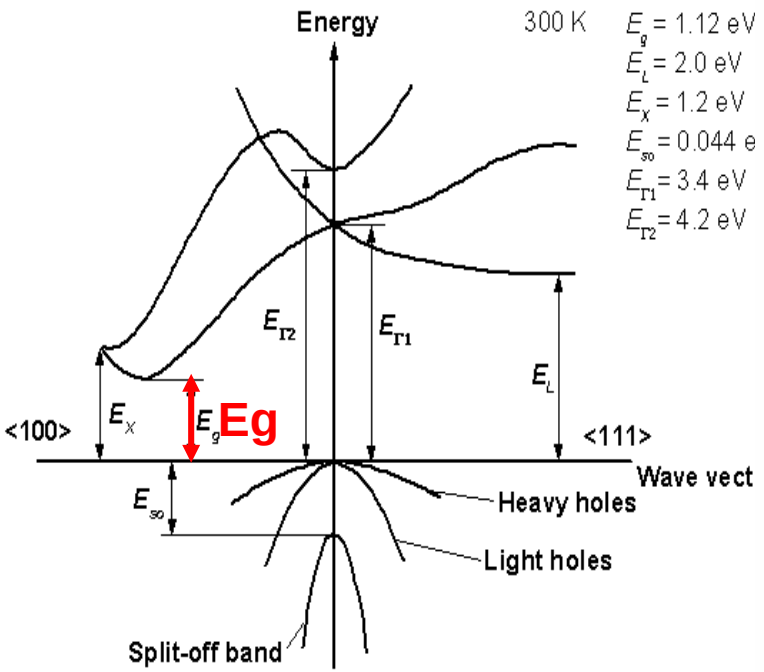


High integration of wires

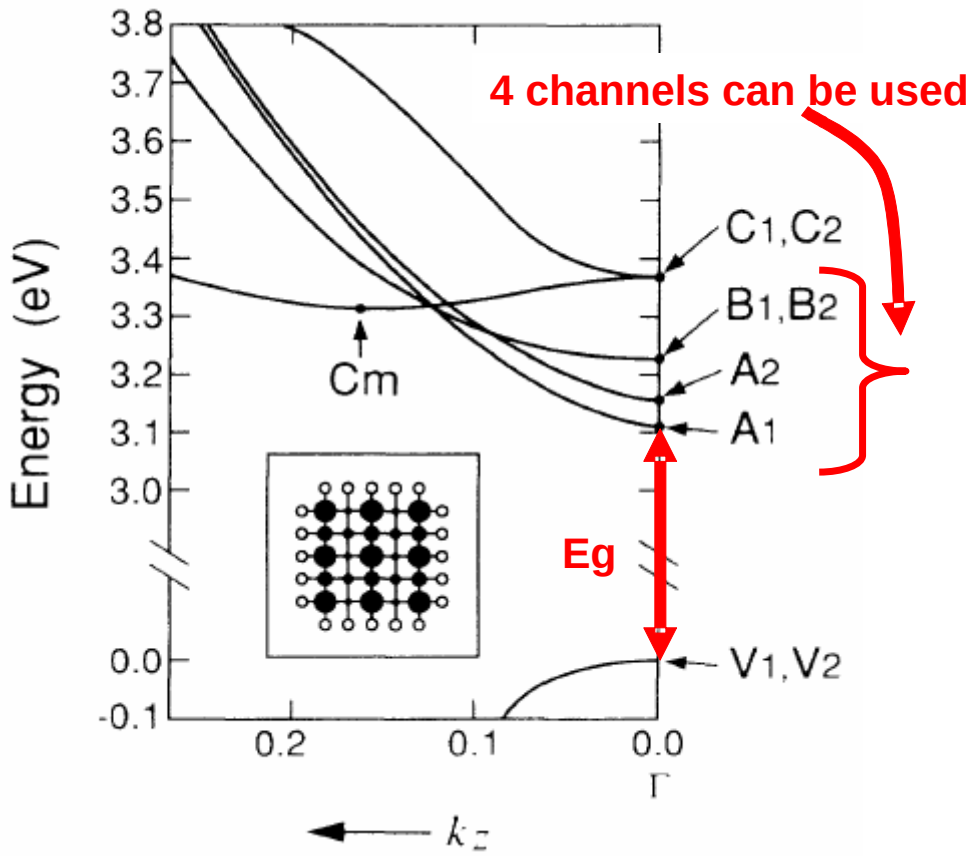


Increase the Number of quantum channels

By Prof. Shiraishi of Tsukuba univ.



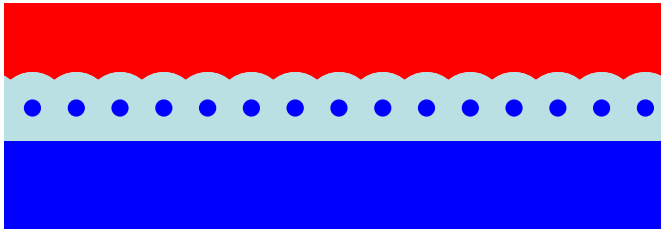
Energy band of Bulk Si



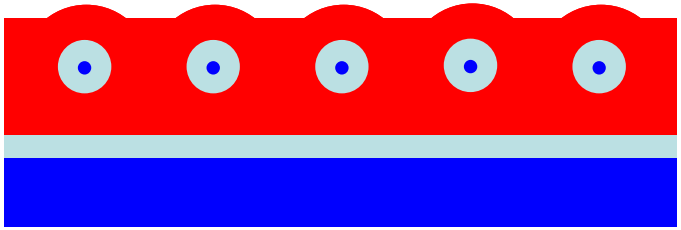
Energy band of 3 x 3 Si wire

Maximum number of wires per 1 μm

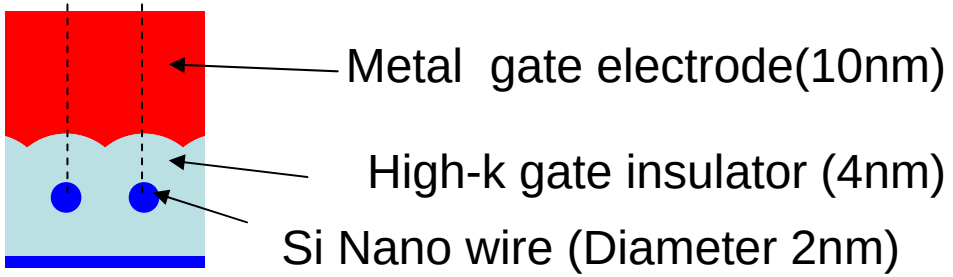
Front gate type MOS 165 wires /μm

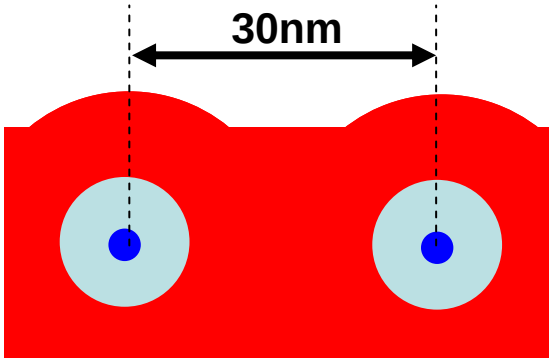


Surrounded gate type MOS 33 wires/μm

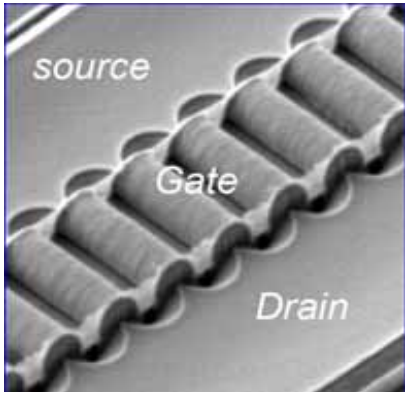


6nm pitch
By nano-imprint method





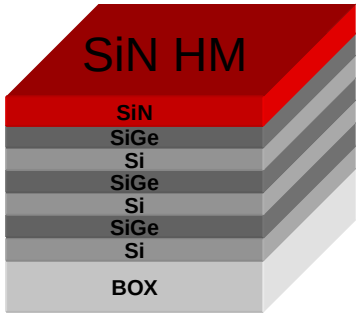
30nm pitch:
EUV lithograpy



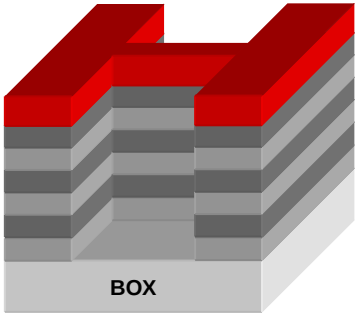
Surrounded gate MOS

Device fabrication

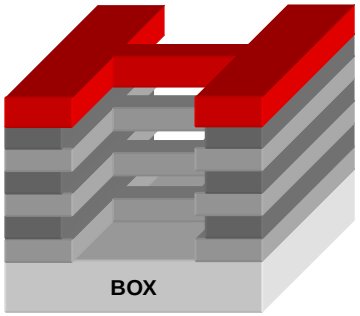
$Si/Si_{0.8}Ge_{0.2}$ superlattice epitaxy on SOI



Anisotropic etching of these layers



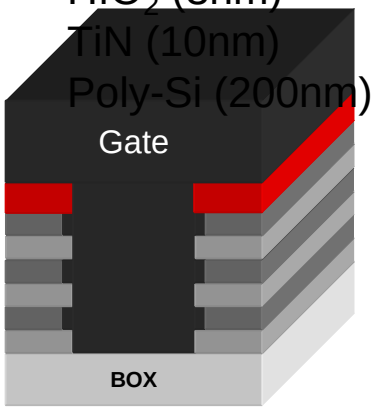
Isotropic etching of SiGe



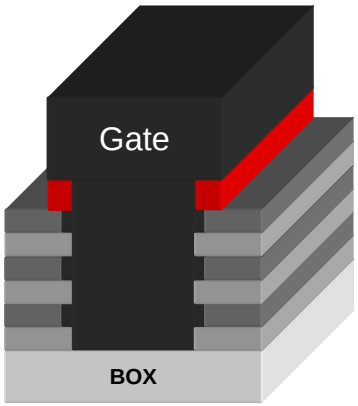
The NW diameter is controllable down to 5 nm by self limited oxidation.

Gate depositions

HfO_2 (3nm)
TiN (10nm)
Poly-Si (200nm)



Gate etching



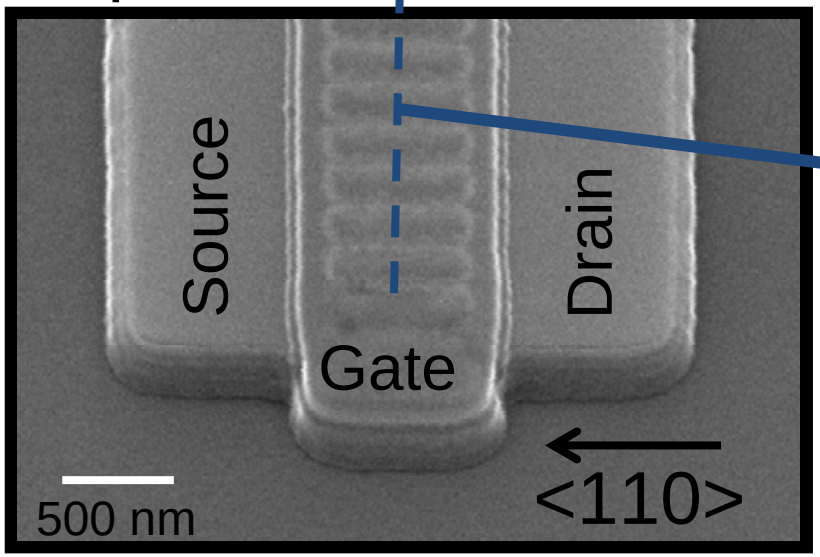
S/D implantation
Spacer formation
Activation anneal
Salicidation

Standard Back-End of-Line Process

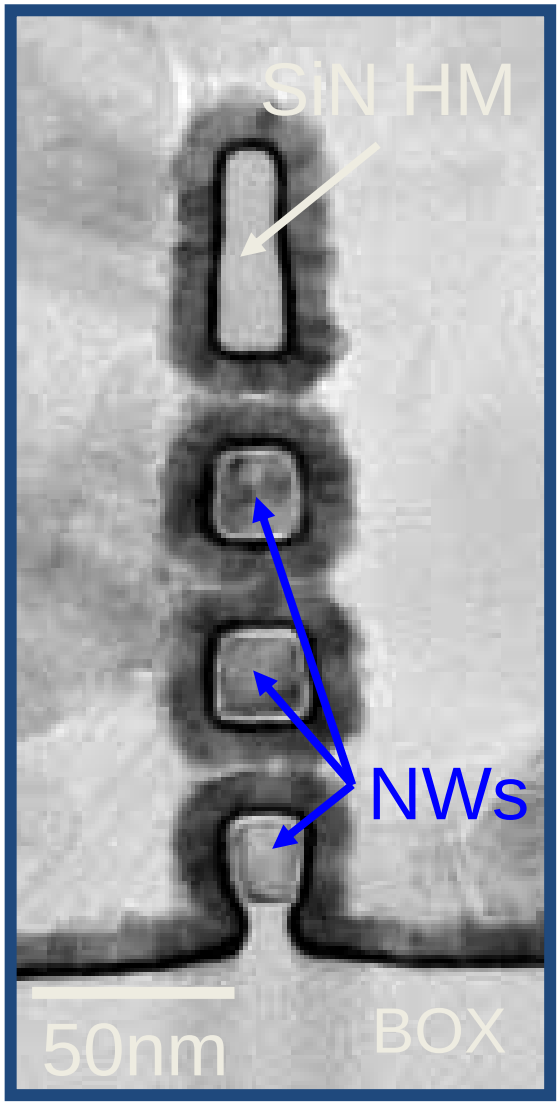
Process Details :
C. Dupre *et al.*,
IEDM Tech. Dig., p.749, 2008

3D-stacked Si NWs with Hi-*k*/MG

Top view



Cross-section

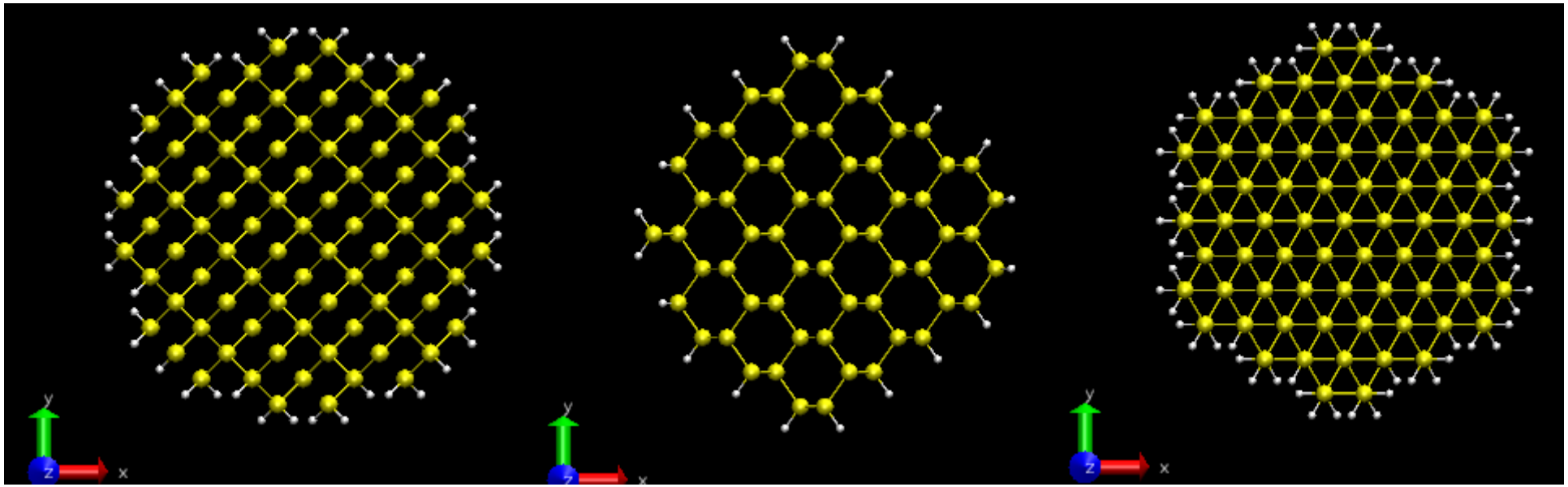


Wire direction : <110>
50 NWs in parallel
3 levels vertically-stacked
Total array of 150 wires
EOT ~2.6 nm

SiNW Band structure calculation

Cross section of Si NW

First principal calculation,

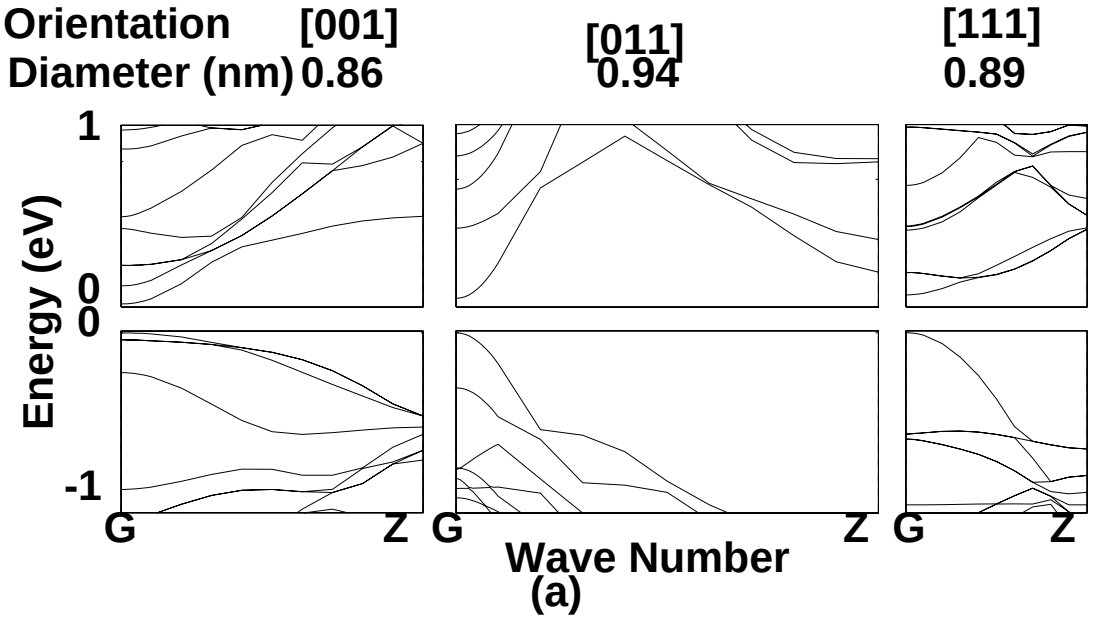


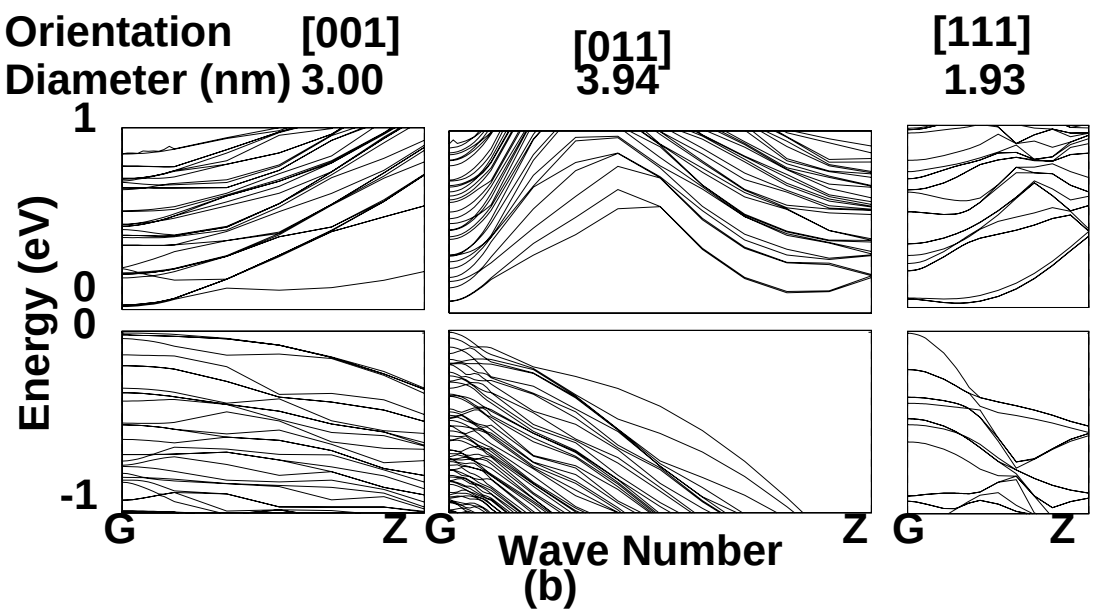
D=1.96nm
[001]

D=1.94nm
[011]

D=1.93nm
[111]

Si nanowire FET with 1D Transport

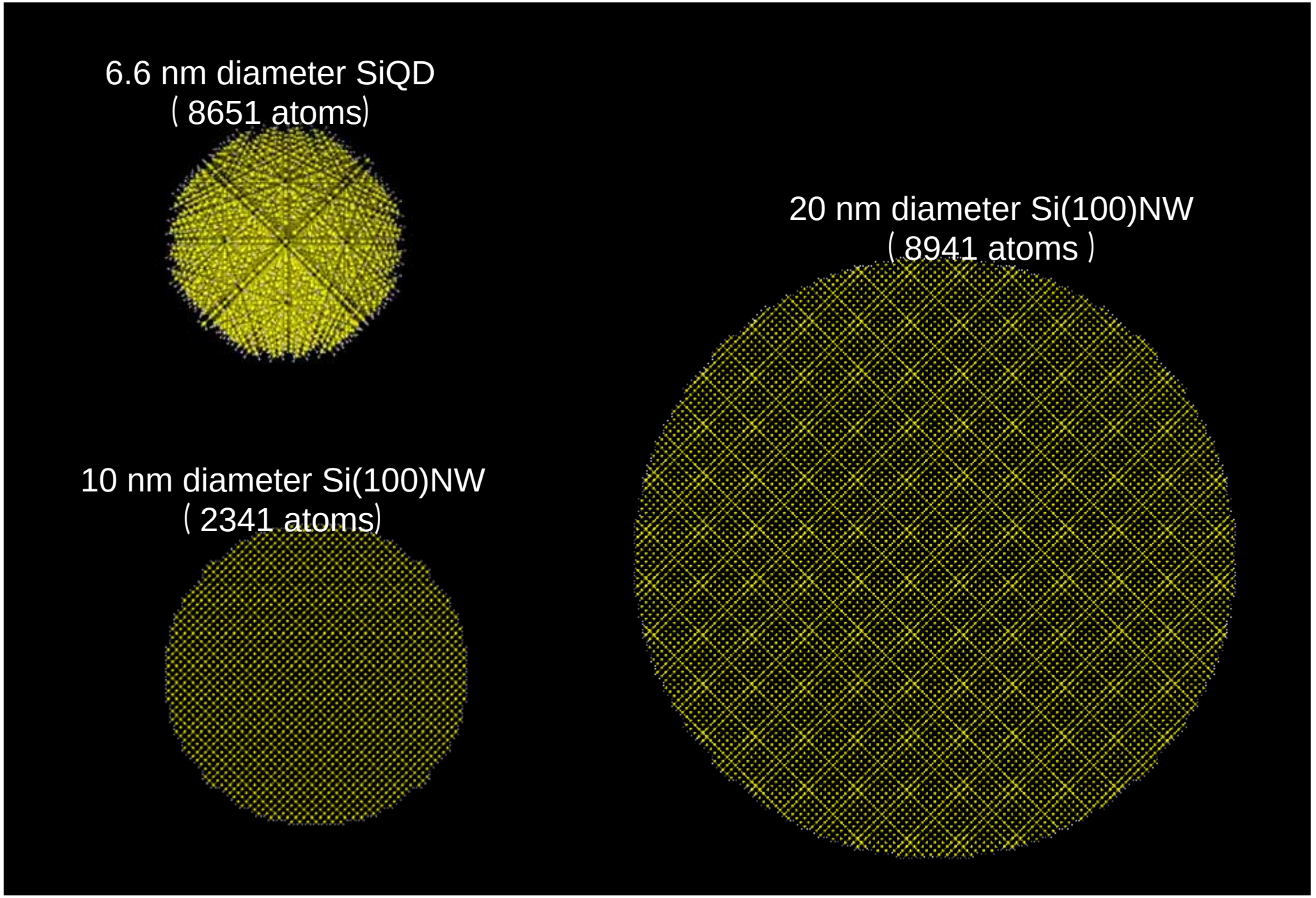




Small mass with [011]

Large number of quantum channels with [001]

Atomic models of a Si quantum dot and Si nanowires



RSDFT – suitable for parallel first-principles calculation -

- ✓Real-Space Finite-Difference
- ✓Sparse Matrix
- ✓FFT free (FFT is inevitable in the conventional plane-wave code)
- ✓MPI (Message Passing Interface) library

Higher-order finite difference pseudopotential method
J. R. Chelikowsky et al., Phys. Rev. B, (1994)

3D grid is divided by several regions for parallel computation.

Kohn-Sham eq. (finite-difference)

$$\left(-\frac{1}{2}\nabla^2 + v_s[\rho](\mathbf{r}) + \hat{v}_{nloc}^{PP}(\mathbf{r})\right)\phi_n(\mathbf{r}) = \varepsilon_n\phi_n(\mathbf{r})$$

Higher-order finite difference

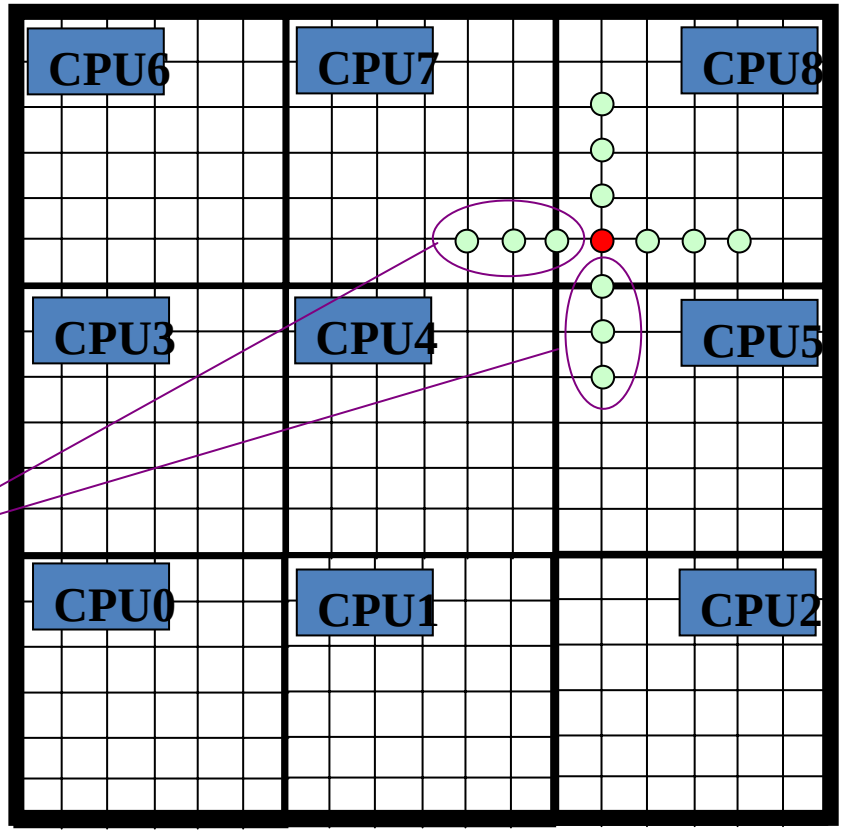
$$\frac{\partial^2}{\partial x^2}\psi_n(x,y,z) \approx \sum_{m=-6}^{6} C_m\psi_n(x+m\Delta x, y, z)$$

MPI_ISEND, MPI_IRECV

Integration

$$\int \psi_m(\mathbf{r})\psi_n(\mathbf{r})d\mathbf{r} \approx \sum_{i=1}^{Mesh} \psi_m(\mathbf{r}_i)\psi_n(\mathbf{r}_i)\Delta x\Delta y\Delta z$$

MPI_ALLREDUCE



Massively Parallel Computing

with our recently developed code “RSDFT”

Iwata et al, J. Comp. Phys., to be published

Real-Space Density-Functional Theory code (RSDFT)

Based on the finite-difference pseudopotential method (J. R. Chelikowsky et al., PRB1994)

Highly tuned for massively parallel computers

Computations are done on a massively-parallel cluster **PACS-CS** at University of Tsukuba.

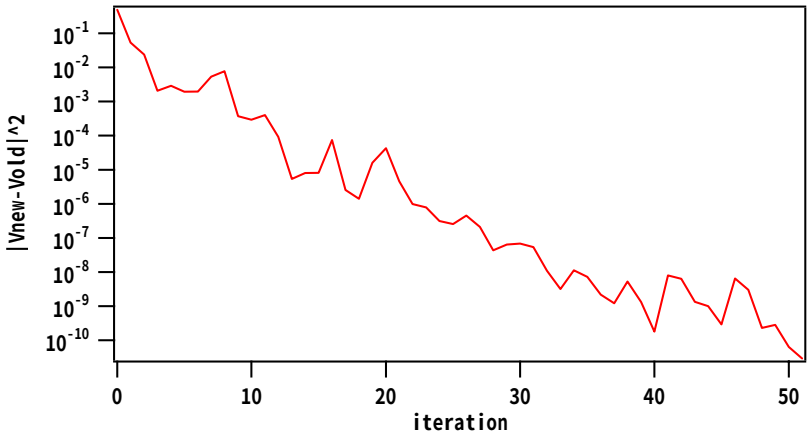
(Theoretical Peak Performance = 5.6GFLOPS/node)

e.g.) The system over 10,000 atoms → $Si_{10701}H_{1996}$

(7.6 nm diameter Si dot)

Convergence behavior for $Si_{10701}H_{1996}$

Grid points = 3,402,059
Bands = 22,432

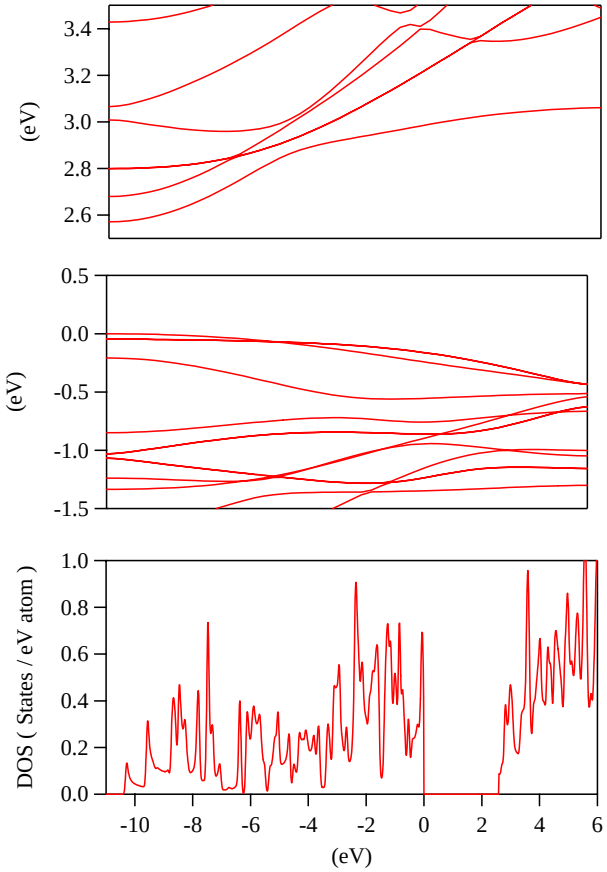


Computational Time (with 1024 nodes of PACS-CS)

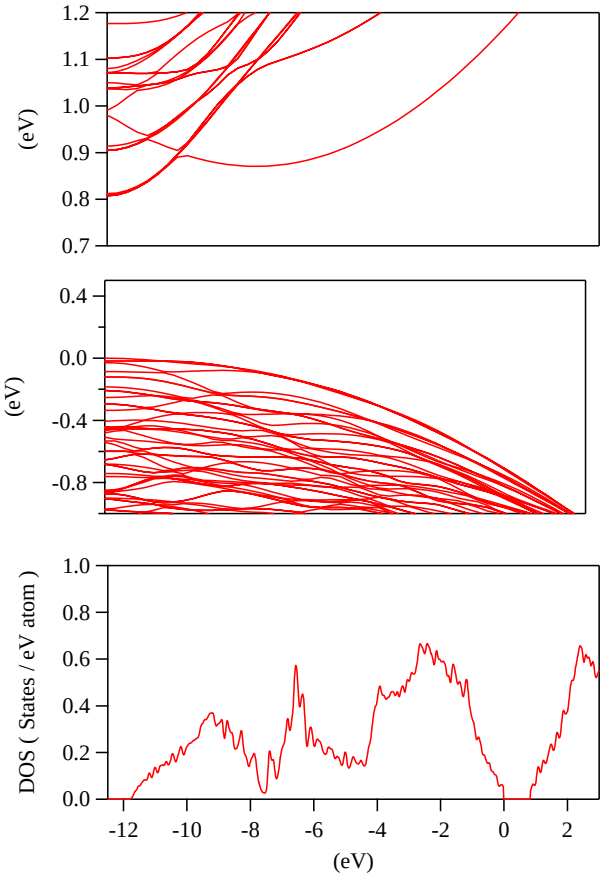
6781 sec. × 60 iteration step = 113 hour

Band Structure and DOS of Si(100)NWs (D=1nm, 4nm, and 8nm)

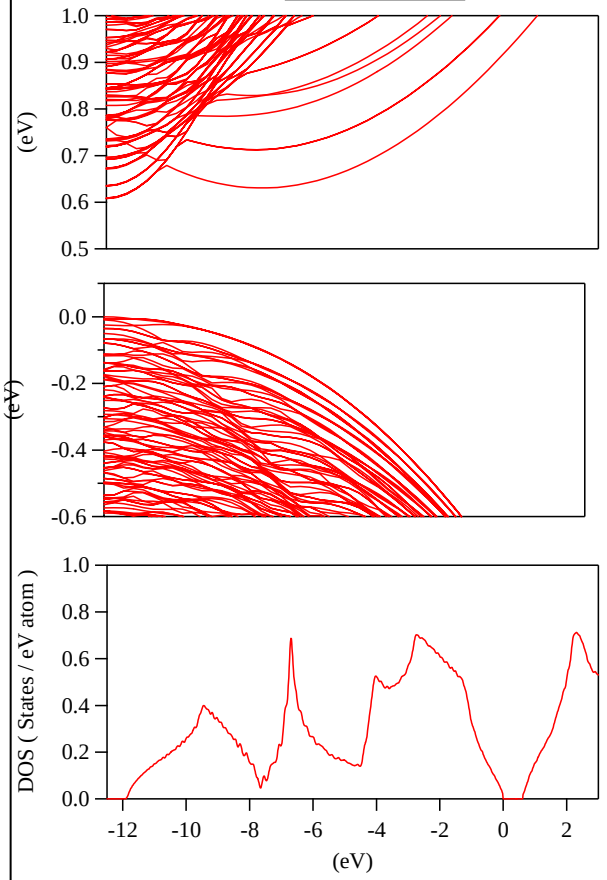
D=1nm



D=4nm



D=8nm



D=1 nm
Si21H20 (41 atoms)
KS band gap=2.60eV

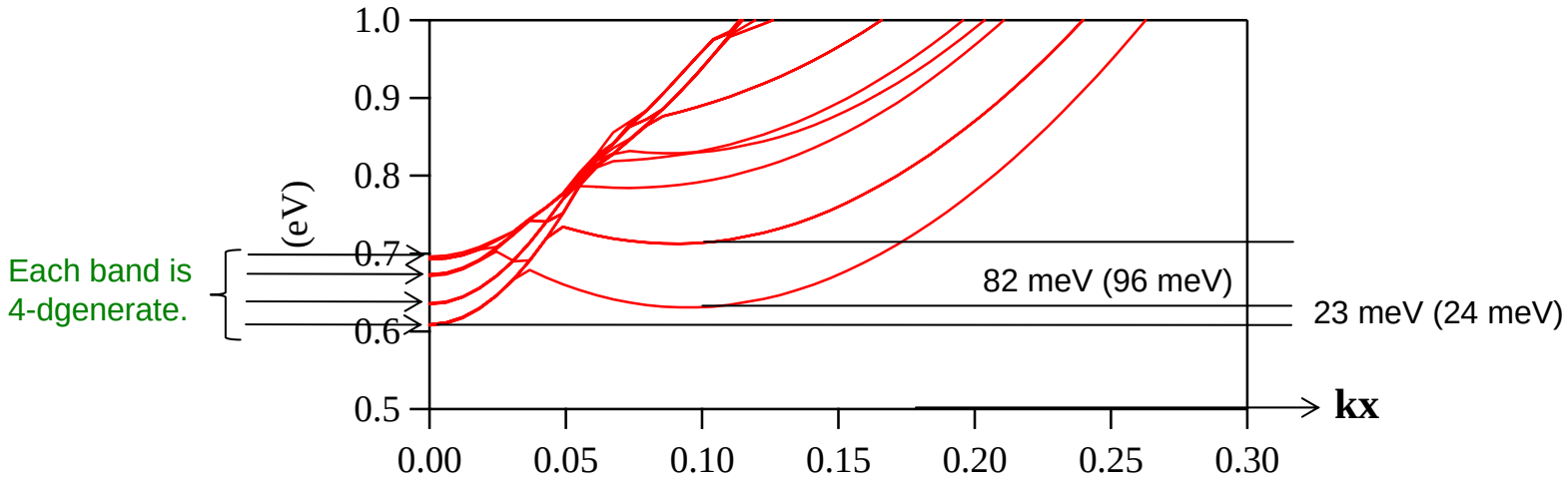
D = 4 nm
Si341H84 (425 atoms)
KS band gap = 0.81eV

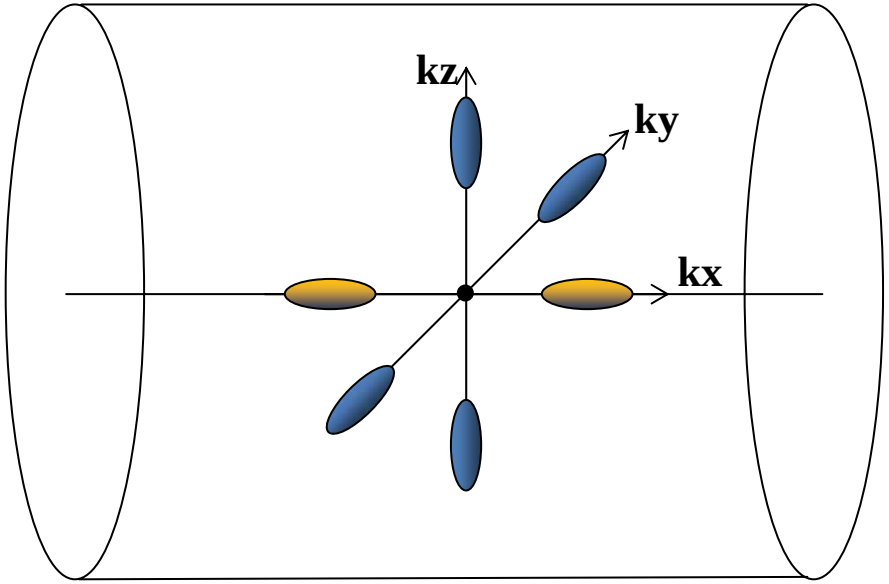
D=8 nm
Si1361H164 (1525 atoms)
KS band gap=0.61eV

KS band gap of bulk (LDA) = 0.53eV

Band structure of 8-nm-diameter Si nanowire near the CBM

- KS band gap = 0.608 eV (@Γ)



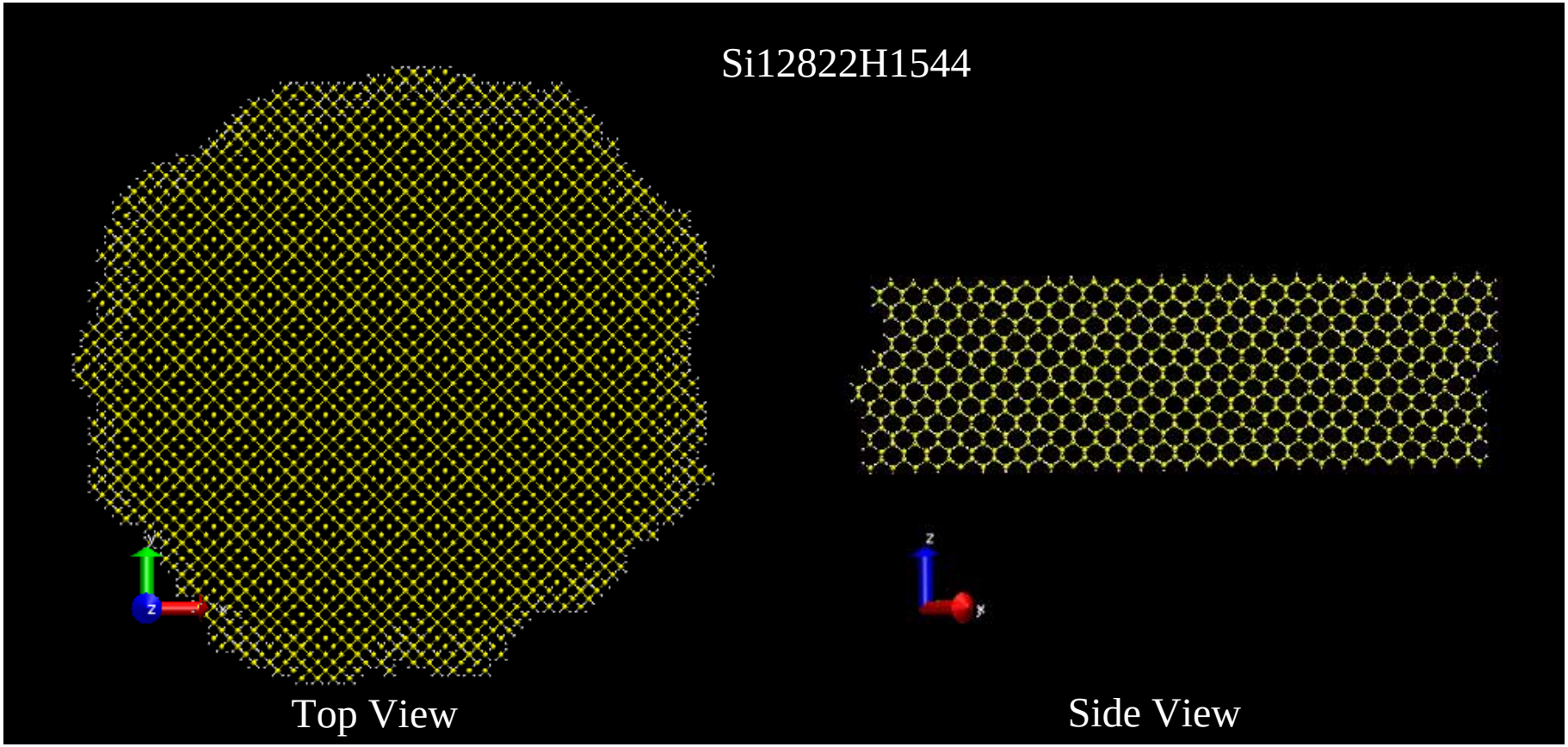


Effective mass equation

$$\left[-\frac{\hbar^2}{2m_t^*}\left(\frac{\partial^2}{\partial x^2}+\frac{\partial^2}{\partial y^2}\right)-\frac{\hbar^2}{2m_l^*}\frac{\partial^2}{\partial z^2}\right]\Phi(\mathbf{r})=(\varepsilon-\varepsilon_{CBM})\Phi(\mathbf{r})$$

The band structure can be understood that electrons near the CBM in the bulk Si are Confined within a cylindrical geometry.

Si nano wire with surface roughness

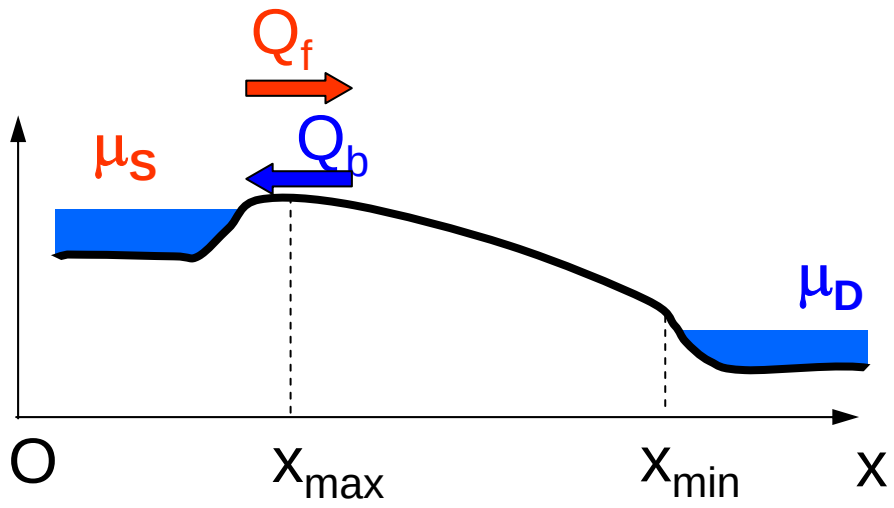


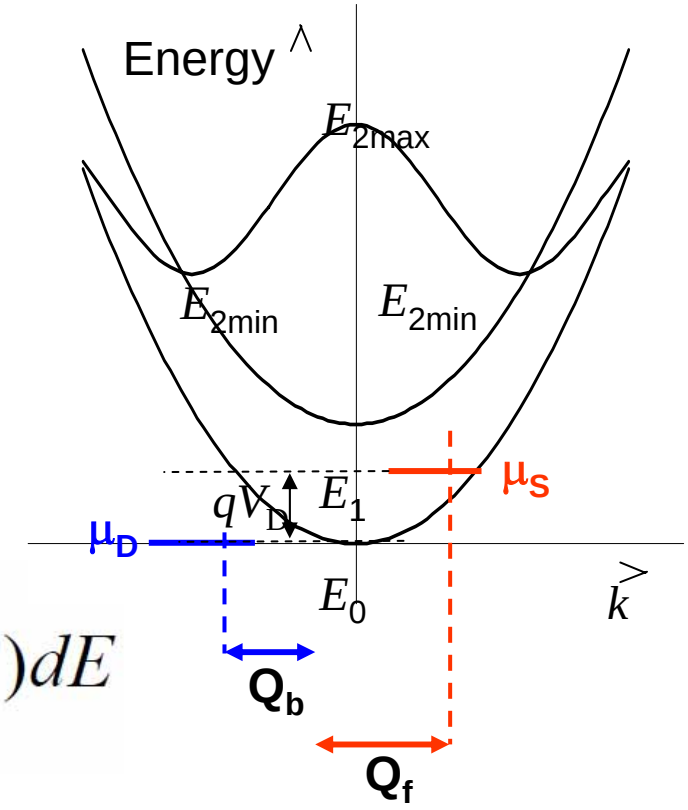
Si12822H1544 (14,366 atoms)

- 10nm diameter、3.3nm height、(100)
- Grid spacing：0.45Å (~14Ry)
- # of grid points：4,718,592
- # of bands：29,024
- Memory：1,022GB～2,044GB

SiNW Band compact model

Landauer Formalism for Ballistic FET



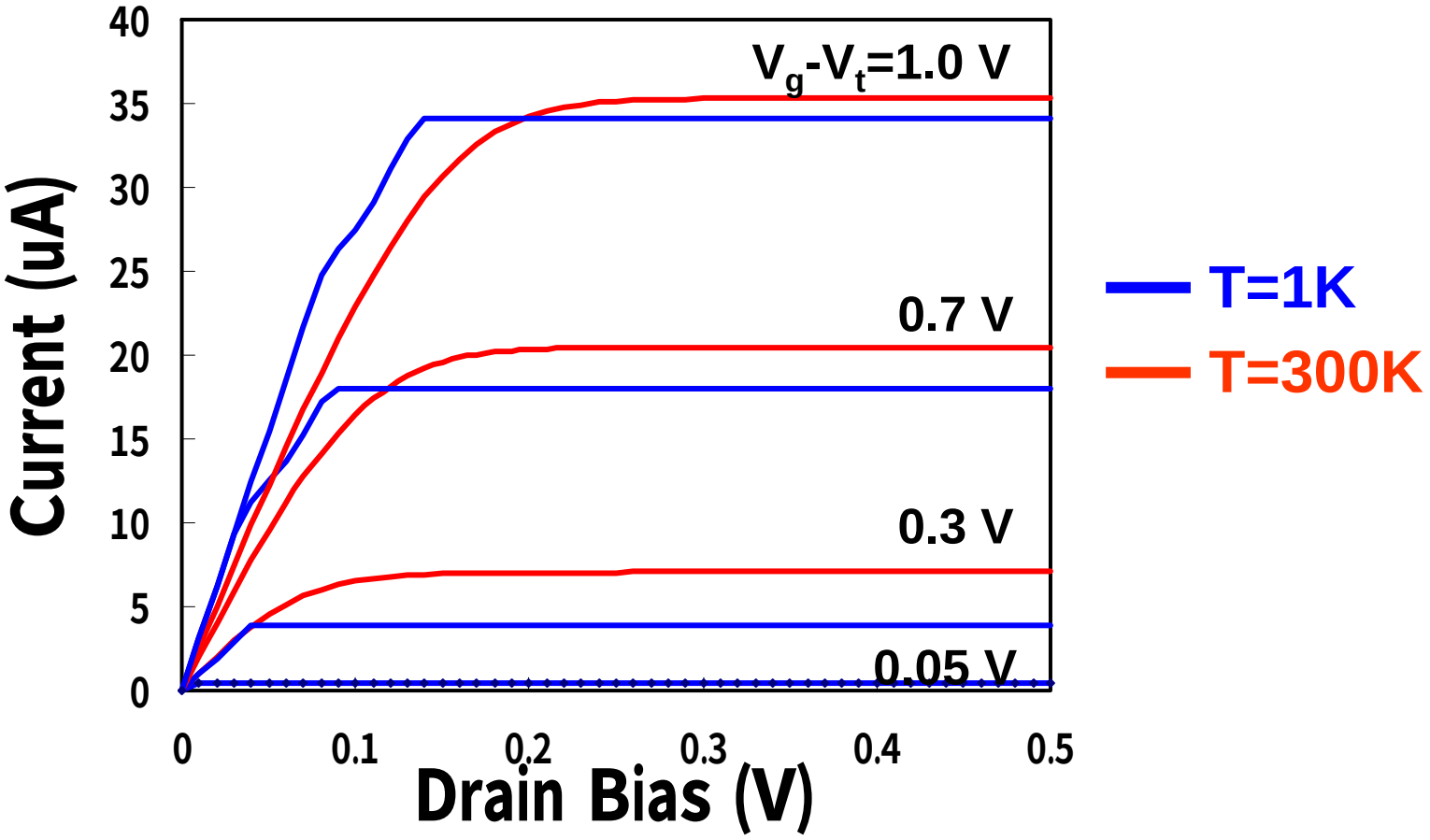


$$I_D = \frac{q}{\pi\hbar}\sum_i \int \left[f(E,\mu_S) - f(E,\mu_D) \right] T_i(E)\, dE$$

From x_{max} to x_{min} $\quad T_i(E) \approx 1$

$$I_D = G_0 \left(\frac{k_B T}{q} \right) \sum_i g_i \ln \left\{ \frac{1+\exp\left[(\mu_S - E_{i0}) / k_B T \right]}{1+\exp\left[(\mu_D - E_{i0}) / k_B T \right]} \right\}$$

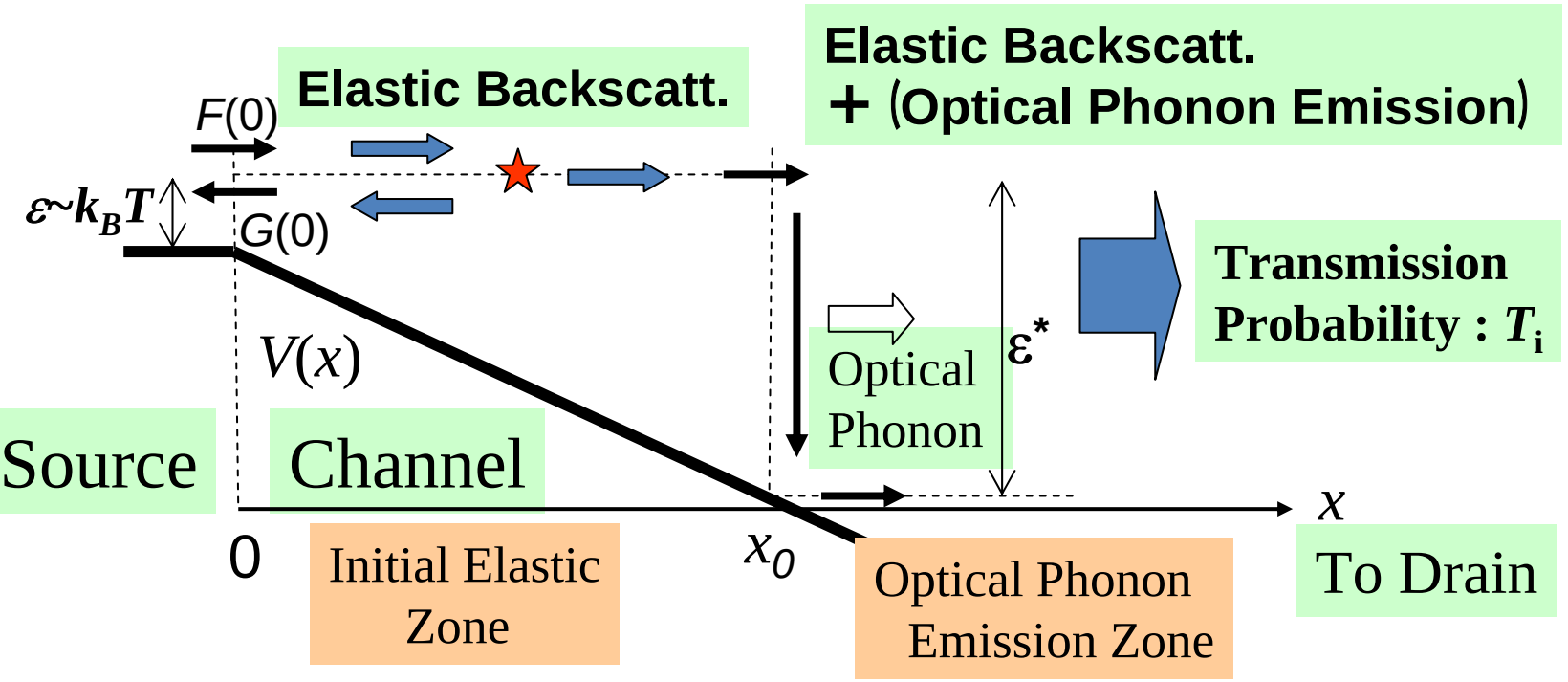
IV Characteristics of Ballistic SiNW FET



Small temperature dependency
35μA/wire for 4 quantum channels

Model of Carrier Scattering

Linear Potential Approx. ; Electric Field E



Transmission Probability to Drain

$$T(\varepsilon) = \left.\frac{F(0) - G(0)}{F(0)}\right)_{\text{Injection from Drain}=0}$$

Résumé of the Compact Model

$$I = \frac{q}{\pi \hbar} \sum_i g_i \int \left[f(\varepsilon, \mu_s) - f(\varepsilon, \mu_D) \right] T_i \, d\varepsilon$$

$$C_G = \frac{2\pi \varepsilon_{ox}}{\ln\left\{ \dfrac{\sqrt{2r + t_{ox}} + \sqrt{t_{ox}}}{\sqrt{2r + t_{ox}} - \sqrt{t_{ox}}} \right\}}.$$

Planar Gate

$$(V_G - V_t) - \alpha \frac{\mu_S - \mu_0}{q} = \frac{\left| Q_f + Q_b \right|}{C_G}.$$

(Electrostatics requirement)

$$\mu_S - \mu_D = qV_D$$

$$C_G = \frac{2\pi \varepsilon_{ox}}{\ln\left(\dfrac{r + t_{ox}}{r} \right)}.$$

GAA

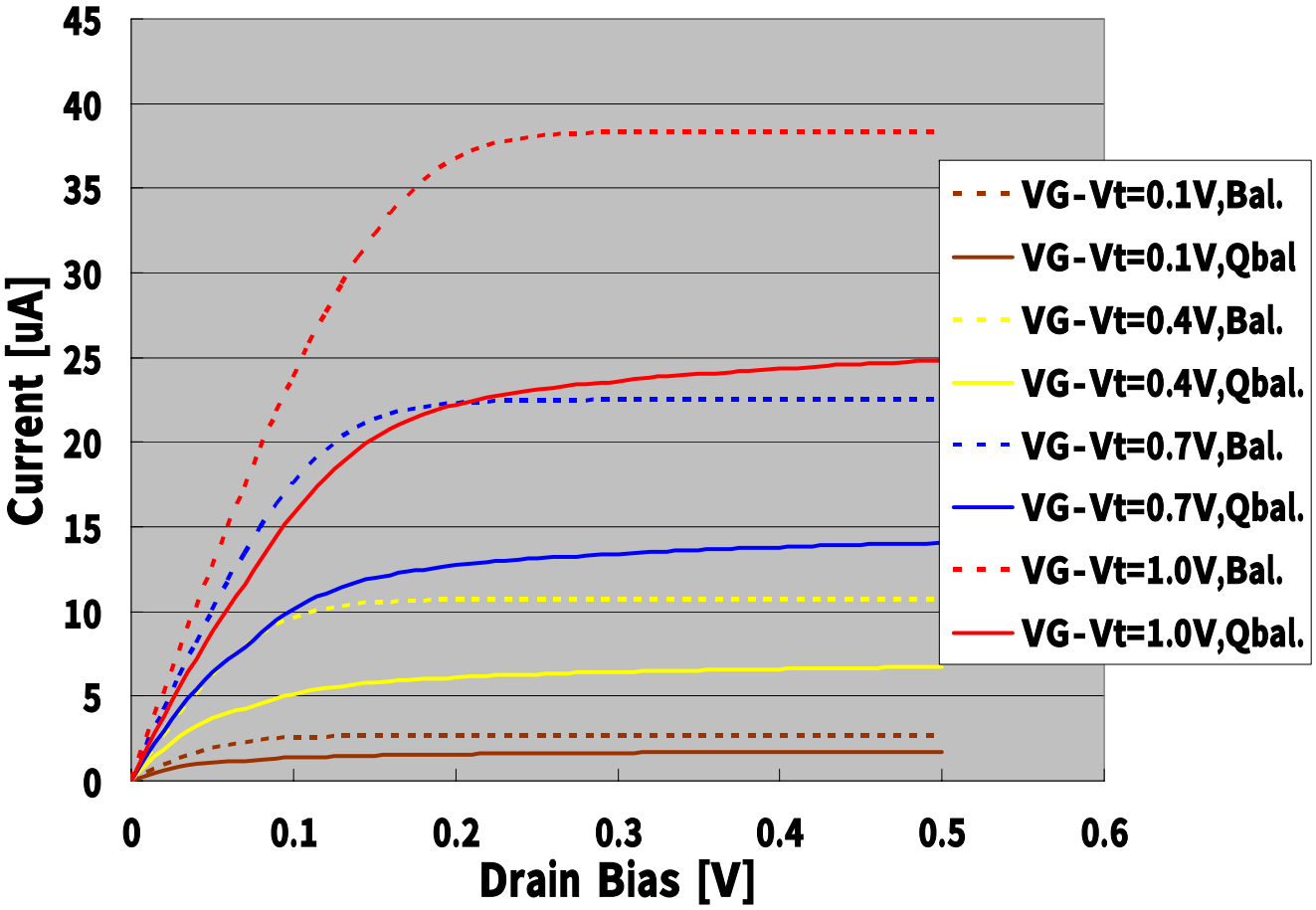
$$\left| Q_f + Q_b \right| = \frac{q}{\pi} \sum_i g_i \left[\int_{-\infty}^{\infty} \frac{dk}{1 + \exp\left\{ \dfrac{\varepsilon_i(k) - \mu_S}{k_B T} \right\}} - \int_{-\infty}^{0} \left\{ \frac{1}{1 + \exp\left\{ \dfrac{\varepsilon_i(k) - \mu_S}{k_B T} \right\}} - \frac{1}{1 + \exp\left\{ \dfrac{\varepsilon_i(k) - \mu_D}{k_B T} \right\}} \right\} T_i(\varepsilon_i(k)) dk \right]$$

$$T(\varepsilon) = \frac{\sqrt{2D_0} qE}{\left(\sqrt{B_0 + D_0} + \sqrt{D_0} \right) qE + \sqrt{2mD_0} B_0 \ln\left(\dfrac{qEx_0 + \varepsilon}{\varepsilon} \right)}$$

(Carrier distribution in Subbands)

Unknowns are I_D, $(\mu_S - \mu_0)$, $(\mu_D - \mu_0)$, $(Q_f + Q_b)$

I-V_D Characteritics (RT)

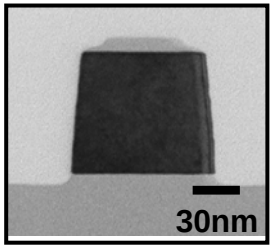


- Electric current 20～25 μA
- No satruration at Large V_D

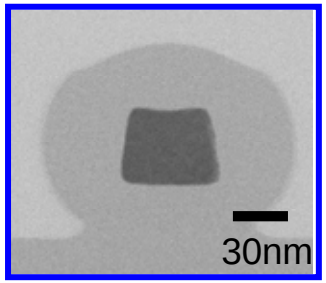
SiNW FET Fabrication

SiNW FET Fabrication

S/D & Fin Patterning

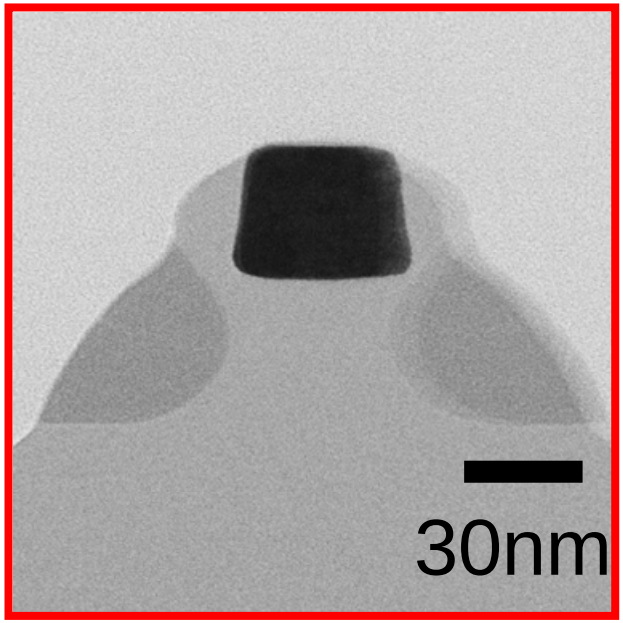


Sacrificial Oxidation



Oixde etch back

SiN sidewall support formation



Gate Oxidation & Poly-Si Deposition

Gate Lithography & RIE Etching

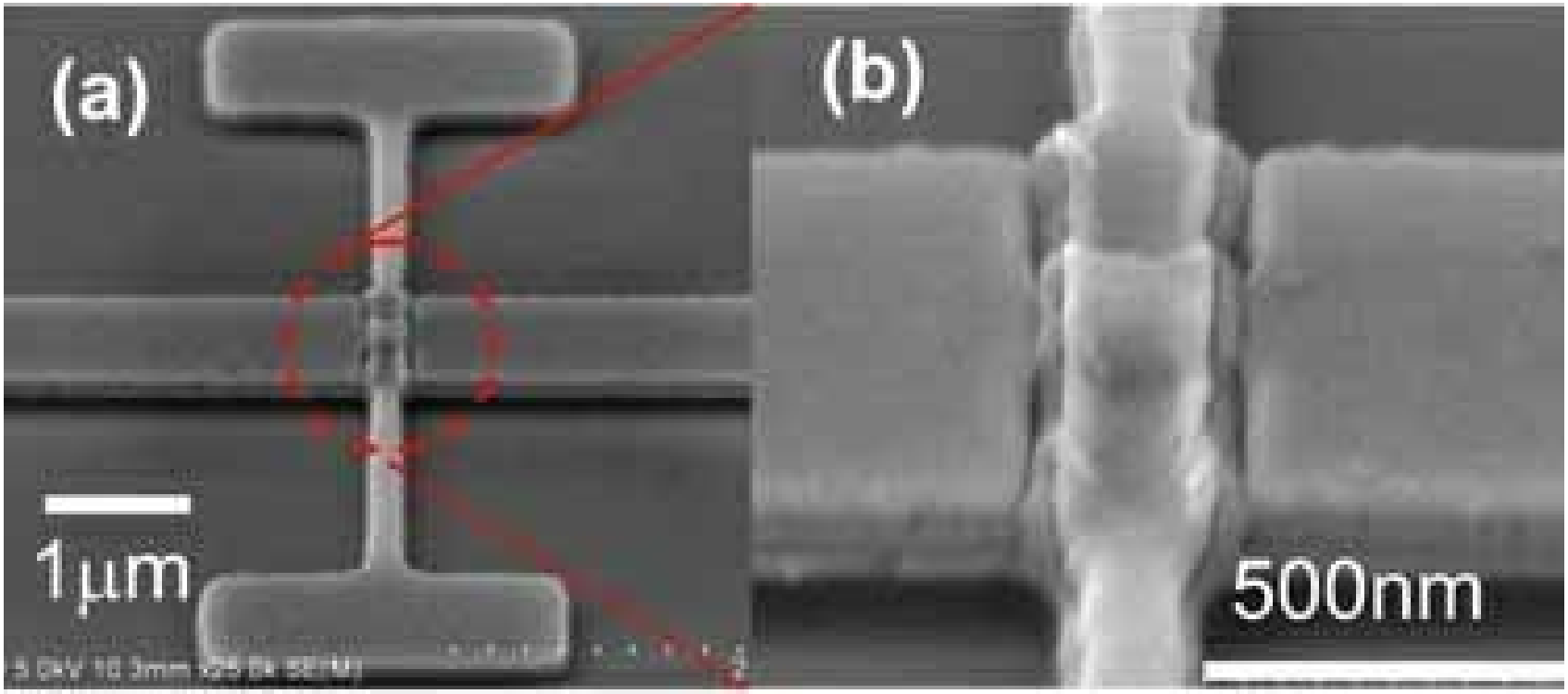
Gate Sidewall Formation

Ni SALISIDE Process (Ni 9nm / TiN 10nm)

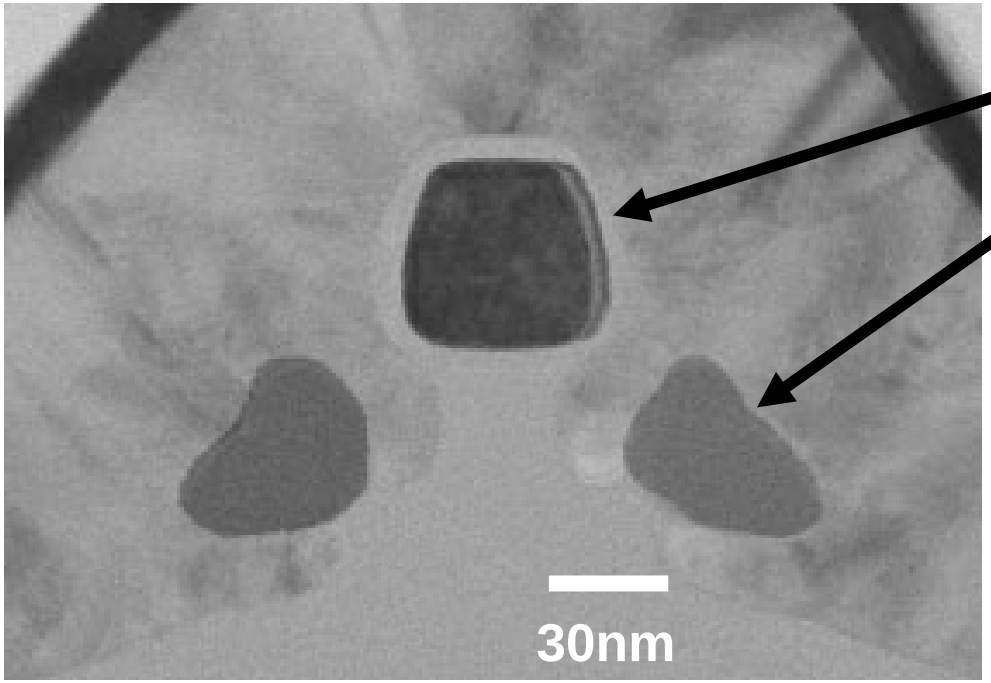
Backend

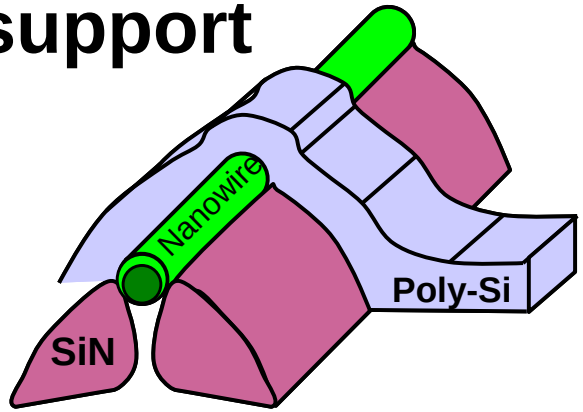
Standard recipe for gate stack formation

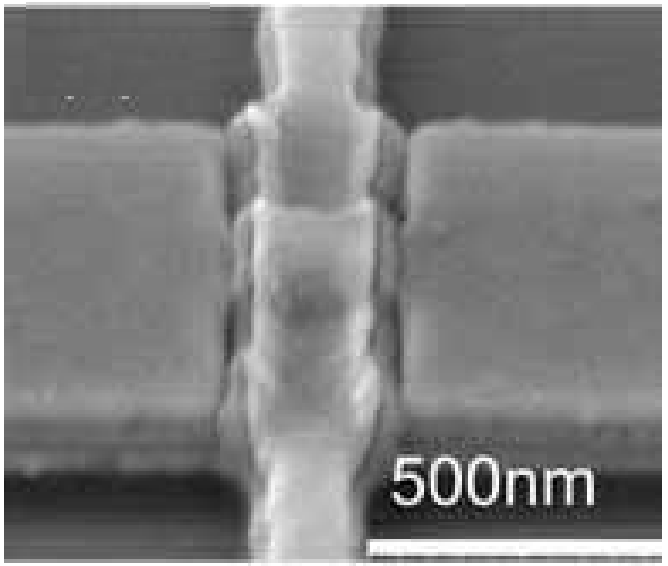
(a) SEM image of Si NW FET (Lg = 200nm)
(b) high magnification observation of gate and its sidewall.



Fabricated SiNW FET

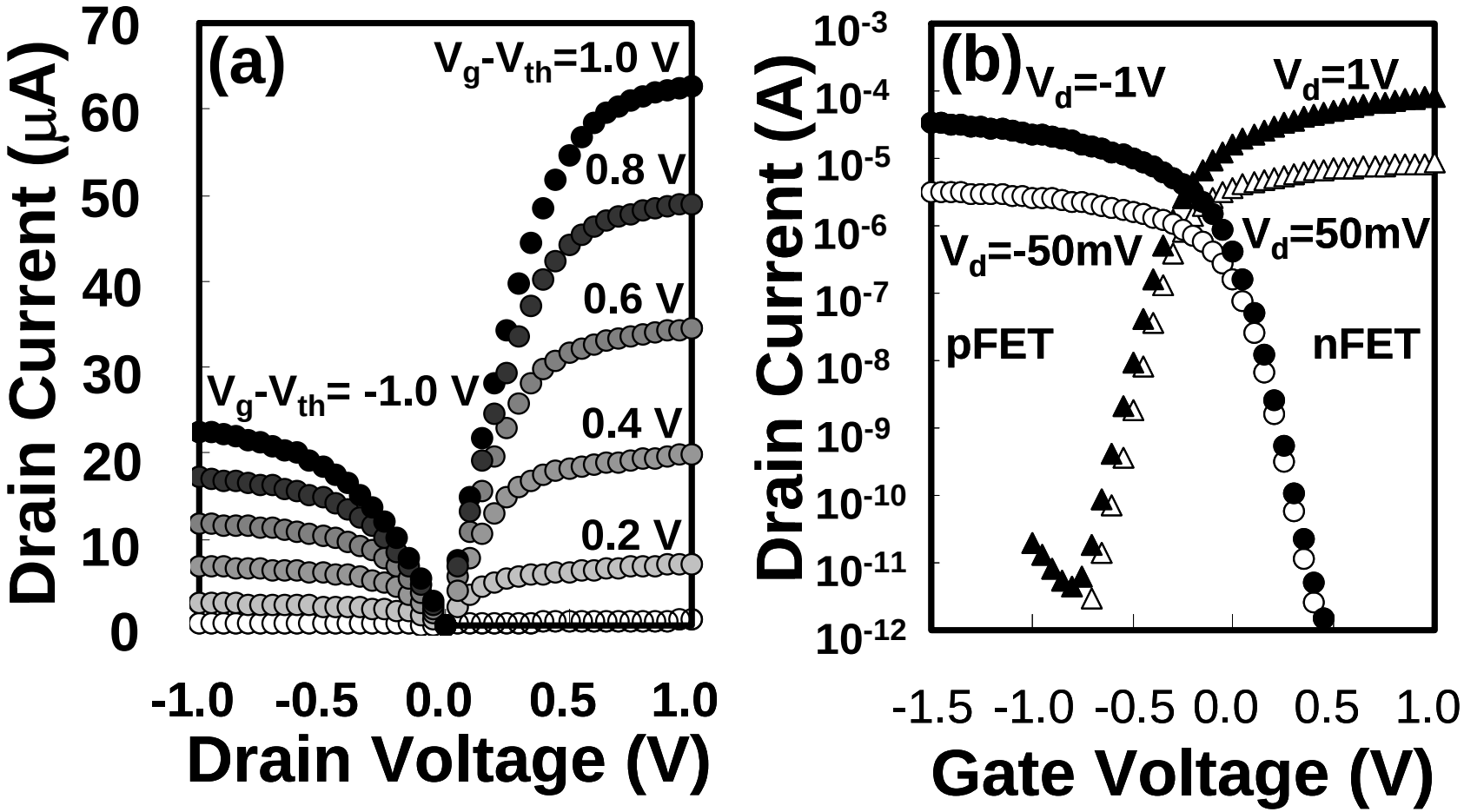






Recent results to be presented by ESSDERC 2010 next week in Sevile

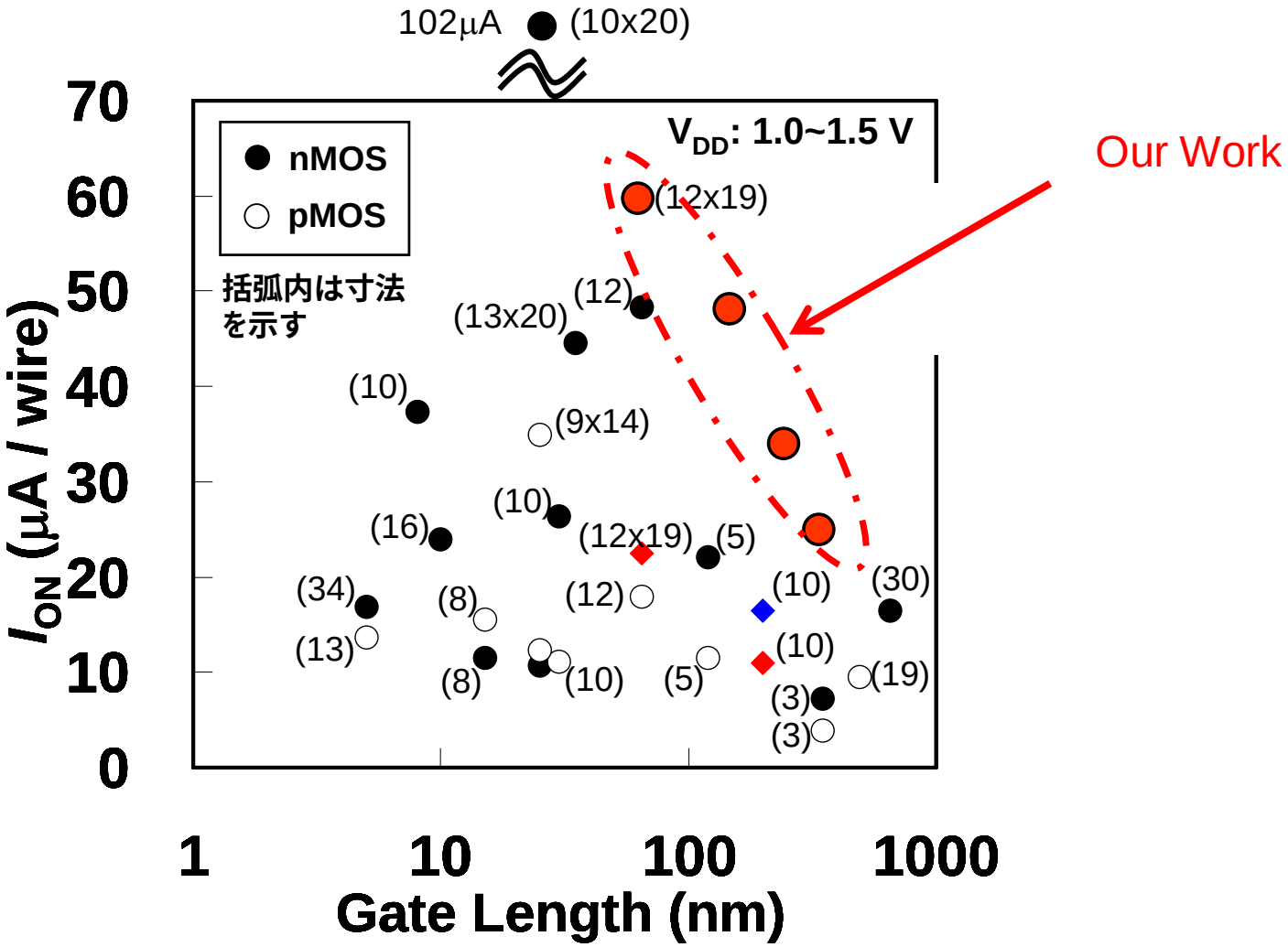
Wire cross-section: 20 nm X 10 nm



On/Off>10^6、 60uA/wire

L_g=65nm, T_{ox}=3nm

Bench Mark


102μA
(10x20)
70
60
50
40
30
20
10
0
I_{ON} (μA / wire)
nMOS
pMOS
括弧内は寸法を示す
V_{DD}: 1.0~1.5 V
Our Work
(12x19)
(12)
(13x20)
(10)
(9x14)
(10)
(16)
(12x19)
(5)
(34)
(8)
(12)
(10)
(30)
(13)
(10)
(8)
(10)
(5)
(19)
(3)
(3)
1
10
100
1000
Gate Length (nm)

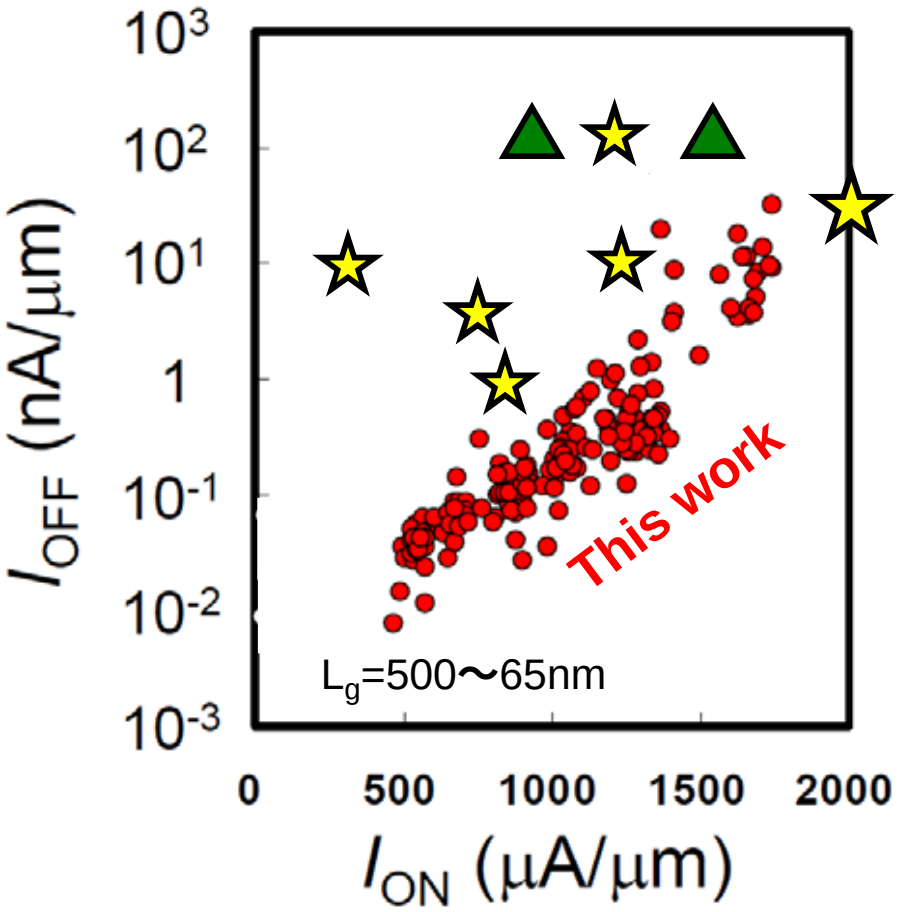
Bench Mark

	This work	Ref[11]	Ref[12]	Ref[13]	Ref[14]	Ref[15]	Ref[4]
NW Cross-section (nm)	Rect.	Rect.	Rect.	Cir.	Cir.	Elliptical	Elliptical
NW Size (nm)	10x20	10x20	14	10	10	12	13x20
Lg (nm)	65	25	100	30	8	65	35
EOT or Tox (nm)	3	1.8	1.8	2	4	3	1.5
Vdd (V)	1.0	1.1	1.2	1.0	1.2	1.2	1.0
Ion(uA) per wire	60.1	102	30.3	26.4	37.4	48.4	43.8
Ion(uA/um) by dia.	3117	5010	2170	2640	3740	4030	2592
Ion(uA/um) by cir.	1609	2054	430	841	1191	1283	825
SS (mV/dec.)	70	79	68	71	75	~75	85
DIBL (mV/V)	62	56	15	13	22	40-82	65
Ion/Ioff	~1E6	>1E6	>1E5	~1E6	>1E7	>1E7	~2E5

Ref[11] by Stmicro Lg=25nm,Tox=1.8nm

This work Lg=65nm,Tox=3nm

I_{ON}/I_{OFF} Bench mark

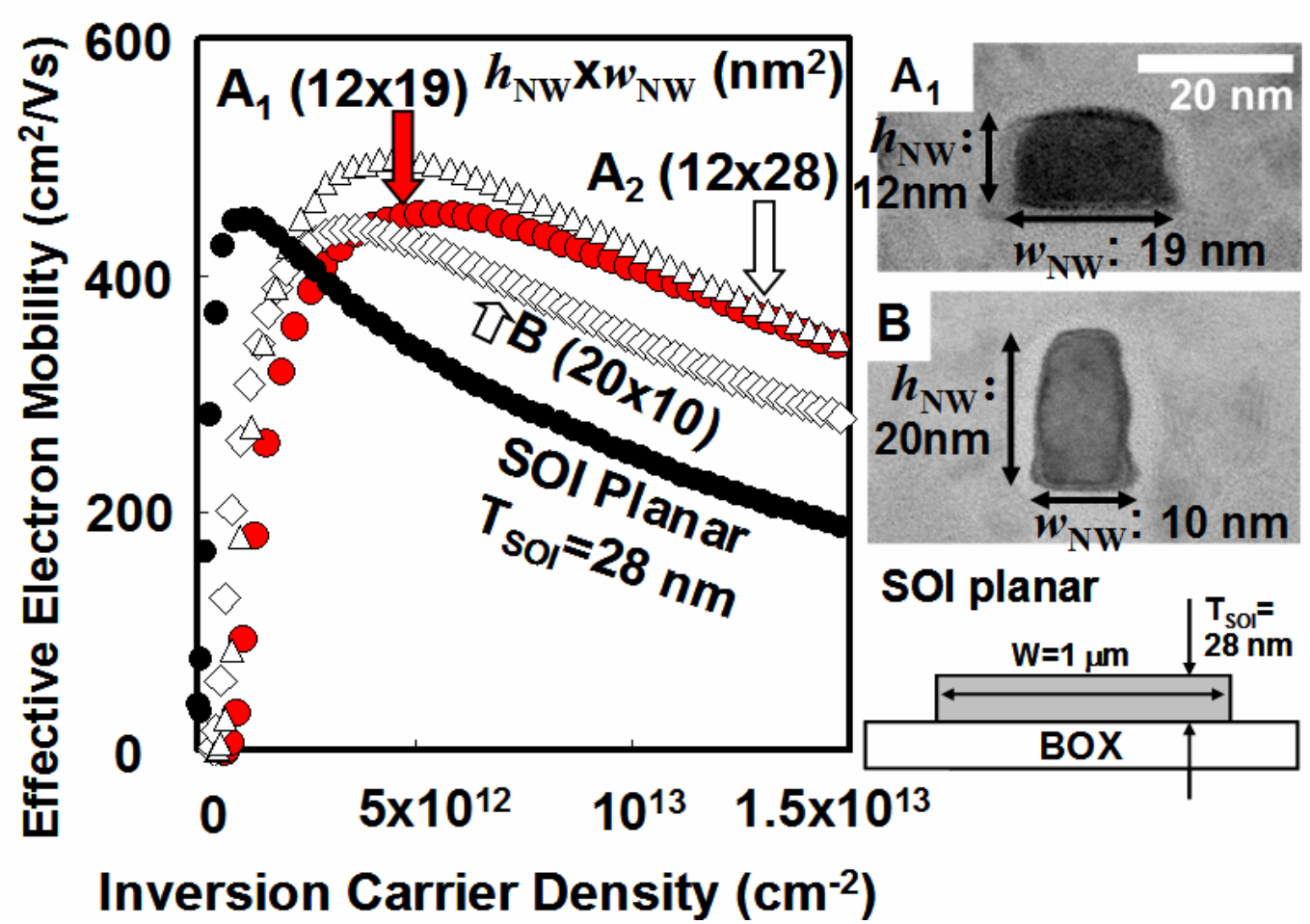


Planer FET ▲ 1.0〜1.1V

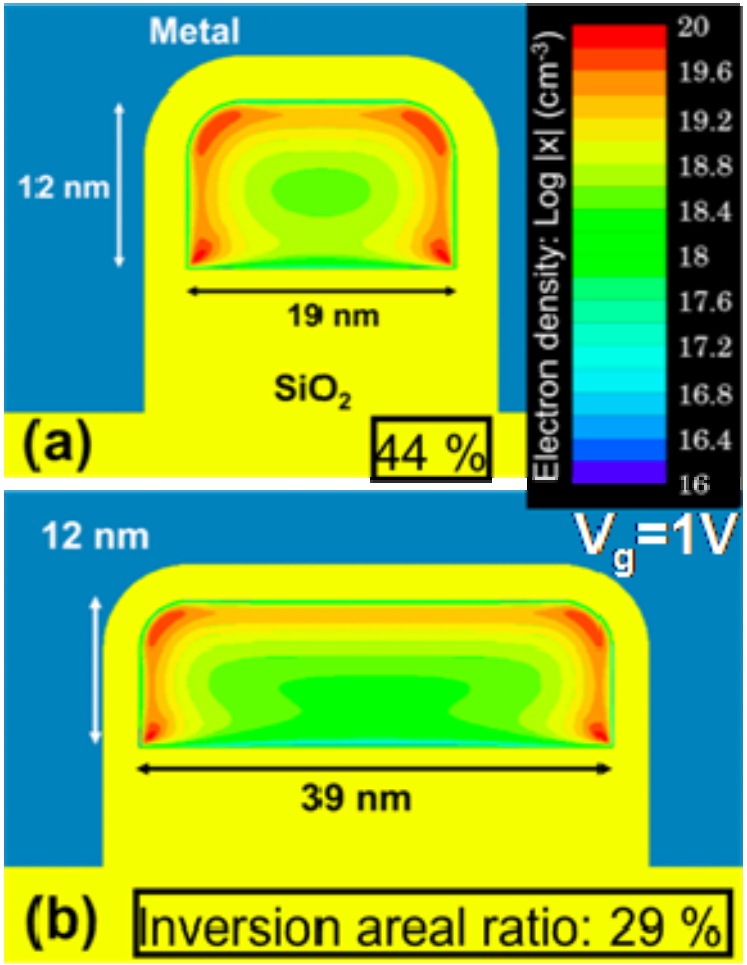
S. Kamiyama, IEDM 2009, p. 431
P. Packan, IEDM 2009, p.659

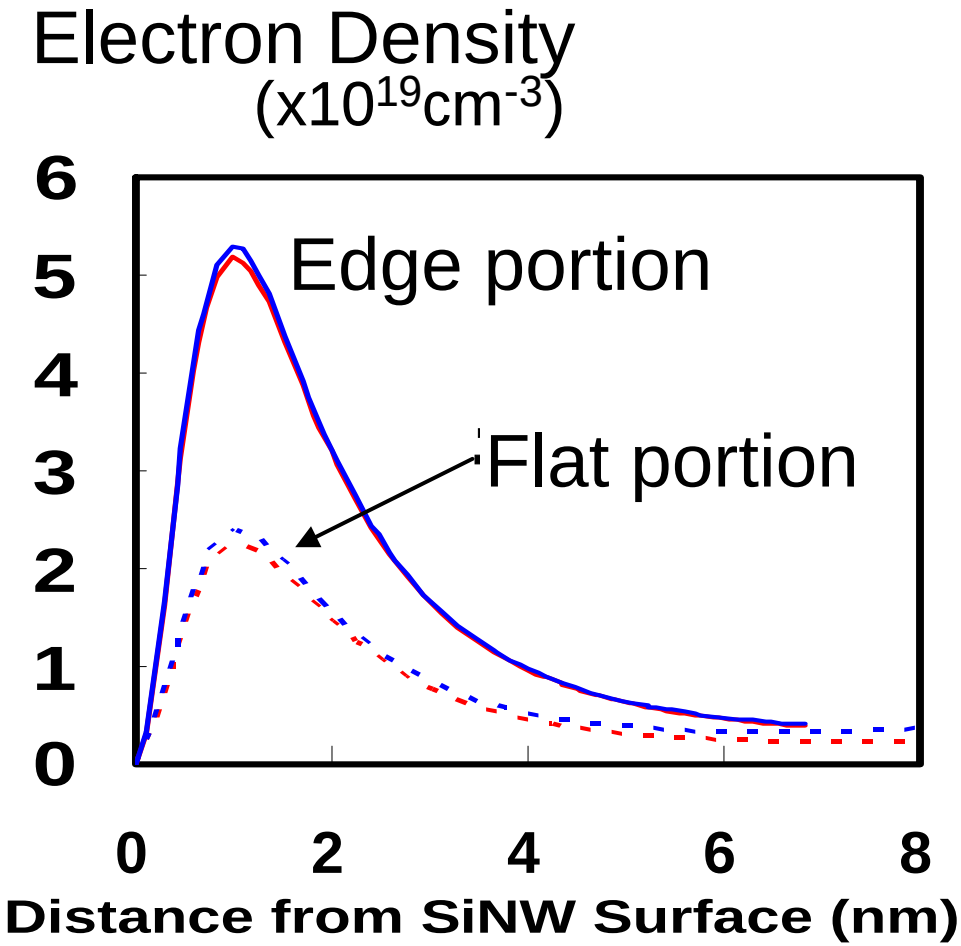
Siナノワイヤ FET ★ 1.2〜1.3V

Y. Jiang, VLSI 2008, p.34
H.-S. Wong, VLSI 2009, p.92
S. Bangsaruntip, IEDM 2009, p.297
C. Dupre, IEDM 2008, p. 749
S.D.Suk, IEDM 2005, p.735
G.Bidel, VLSI 2009, p.240

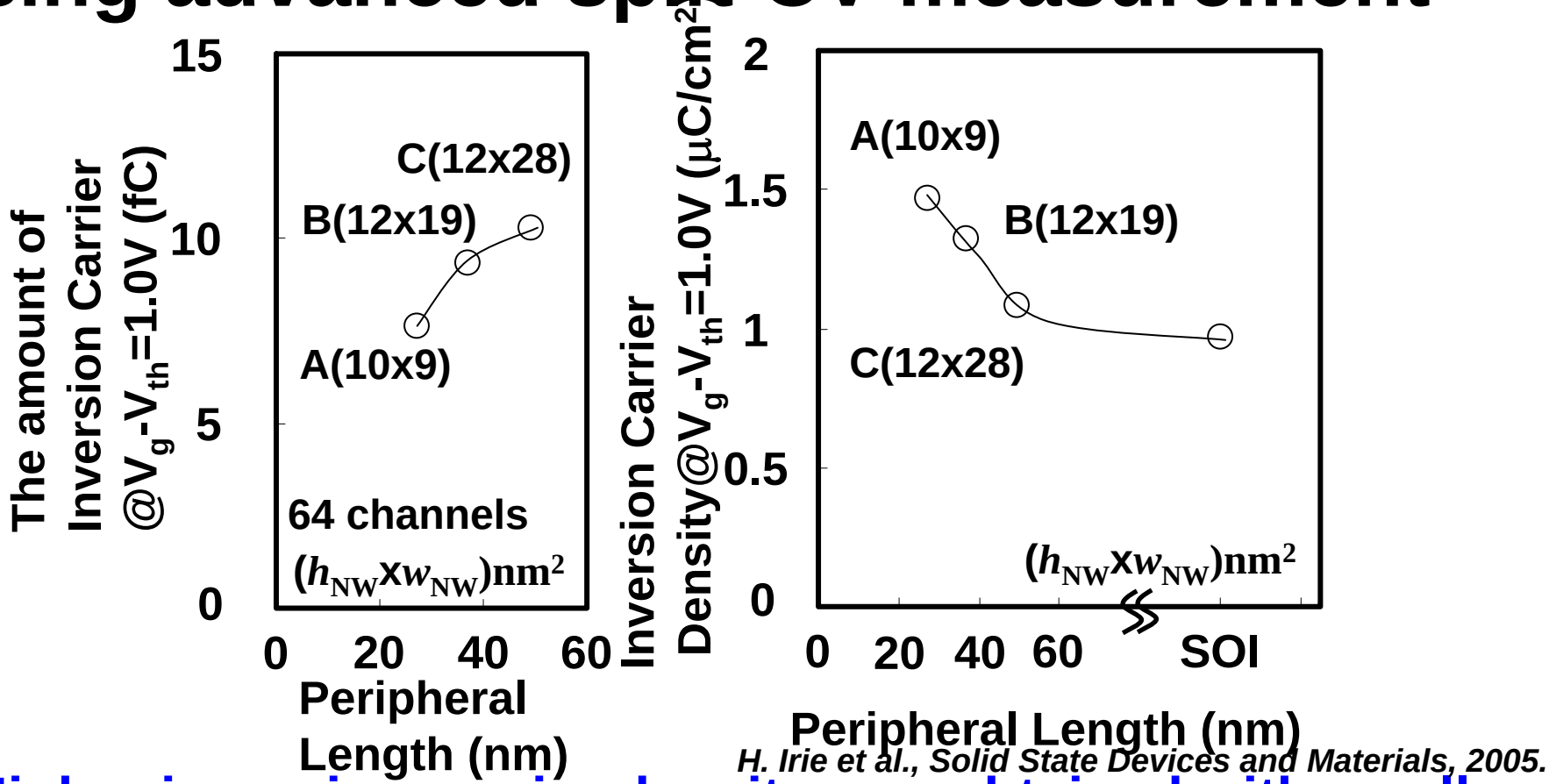

Effective Electron Mobility (cm²/Vs)
600
400
200
0
0
5x10¹²
10¹³
1.5x10¹³
Inversion Carrier Density (cm⁻²)
A₁ (12x19) h_NW x w_NW (nm²)
A₂ (12x28)
B (20x10)
SOI Planar
T_SOI=28 nm
A₁
20 nm
h_NW: 12nm
w_NW: 19 nm
B
h_NW: 20nm
w_NW: 10 nm
SOI planar
T_SOI= 28 nm
W=1 μm
BOX

1. Increase of Inversion Carrier Density


Metal
12 nm
19 nm
SiO2
(a)
44 %
Electron density: Log |x| (cm-3)
20
19.6
19.2
18.8
18.4
18
17.6
17.2
16.8
16.4
16
12 nm
Vg=1V
39 nm
(b)
Inversion areal ratio: 29 %


Electron Density
(x10^19cm^-3)
6
5
4
3
2
1
0
Edge portion
Flat portion
0
2
4
6
8
Distance from SiNW Surface (nm)

Evaluation of Inversion carrier extracted using advanced split-CV measurement



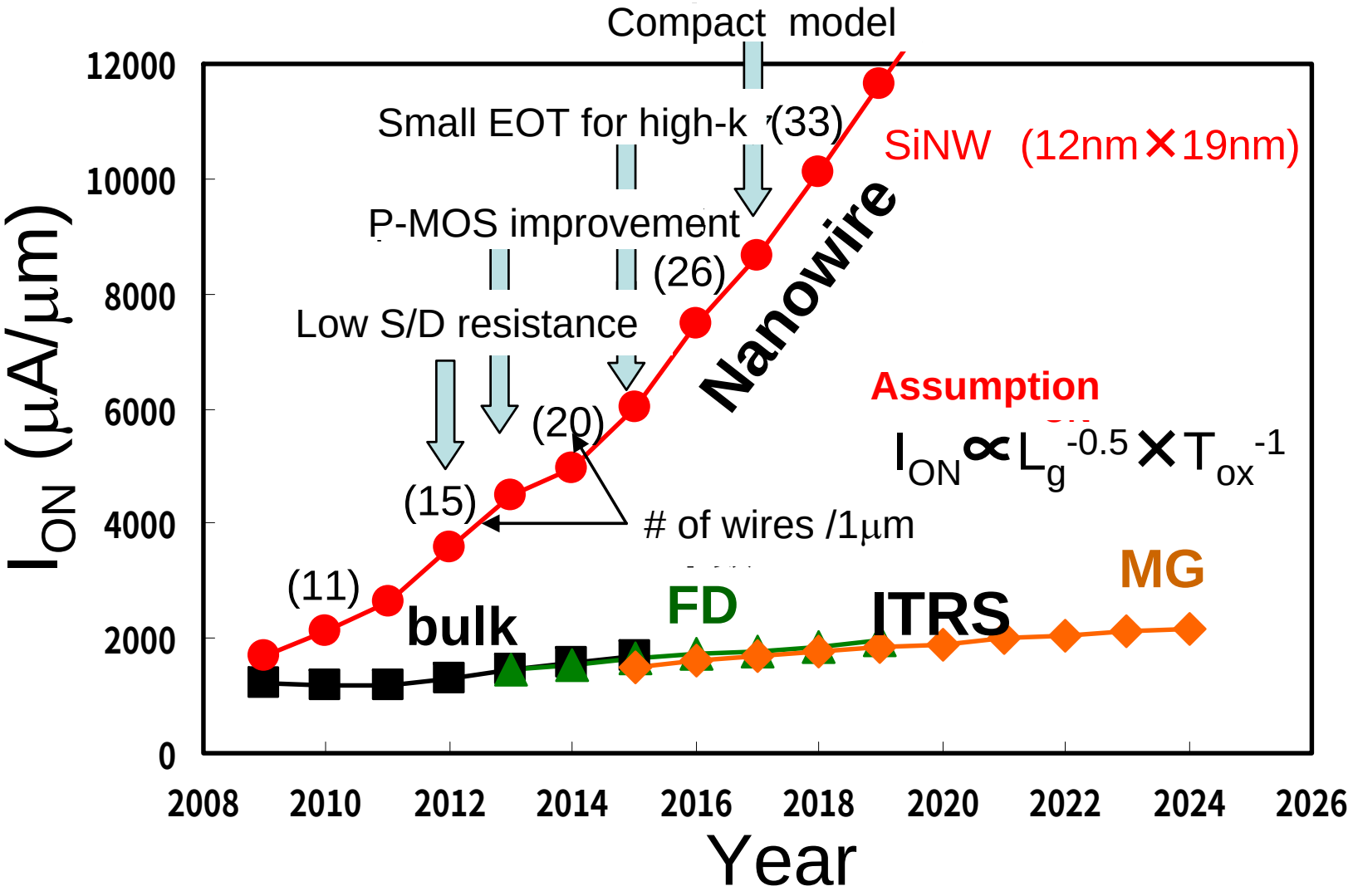
H. Irie et al., Solid State Devices and Materials, 2005.

✓**Higher inversion carrier density was obtained with smaller dimensions.**

✓**The result of two-dimensional simulation in the previous slide supports these experimental results.**

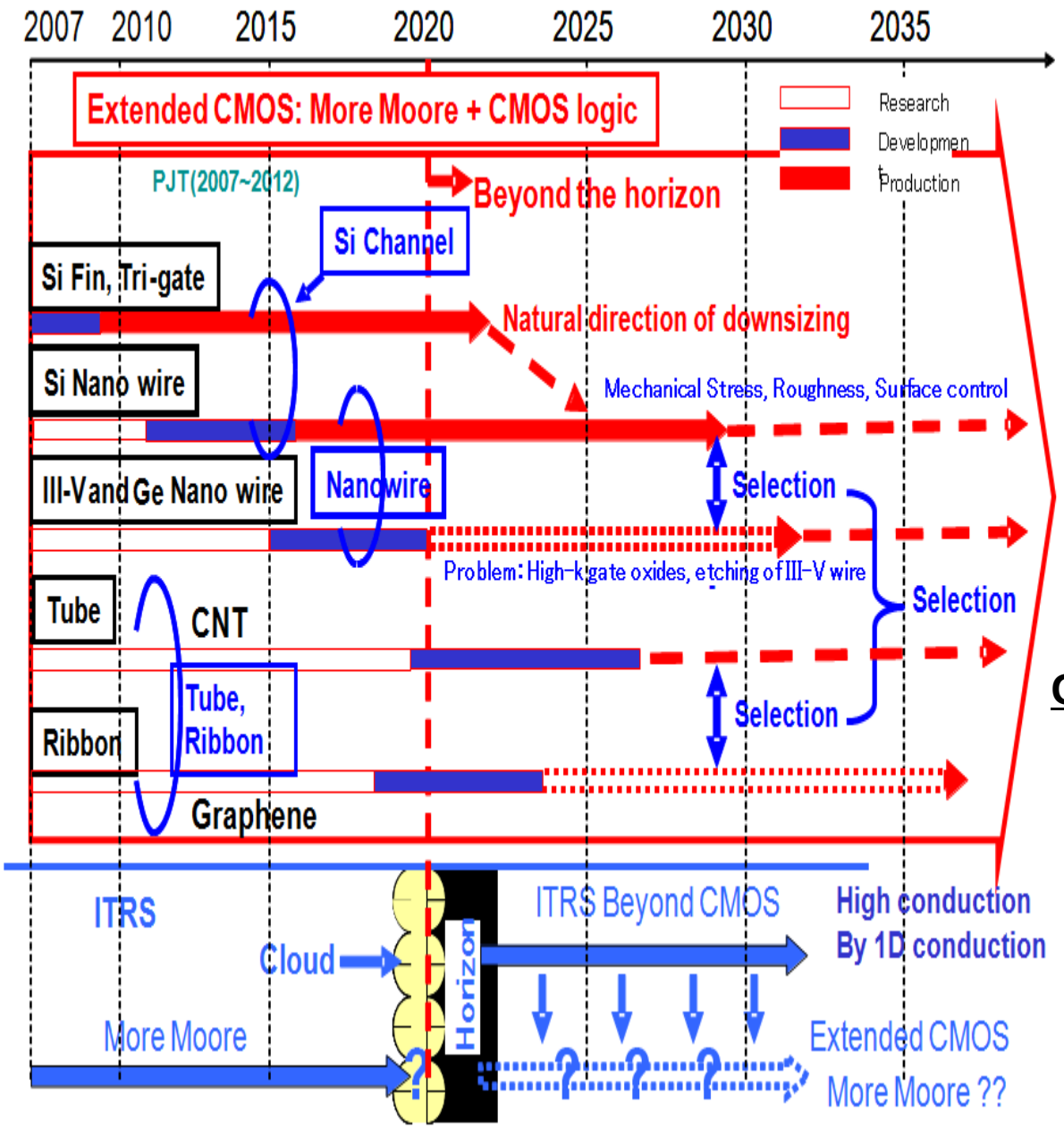
2. Enhancement of Effective Carrier Mobility

Primitive estimation !



Our roadmap for R &D

Source: H. Iwai, IWJT 2008



Current Issues

Si Nanowire

Control of wire surface property

Source Drain contact

Optimization of wire diameter

Compact I-V model

III-V & Ge Nanowire

High-k gate insulator

Wire formation technique

CNT:

Growth and integration of CNT

Width and Chirality control

Chirality determines conduction types: metal or semiconductor

Graphene:

Graphene formation technique

Suppression of off-current

Very small bandgap or no bandgap (semi-metal)

Control of ribbon edge structure which affects bandgap

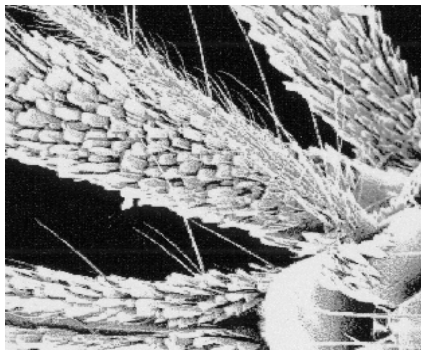
Brain

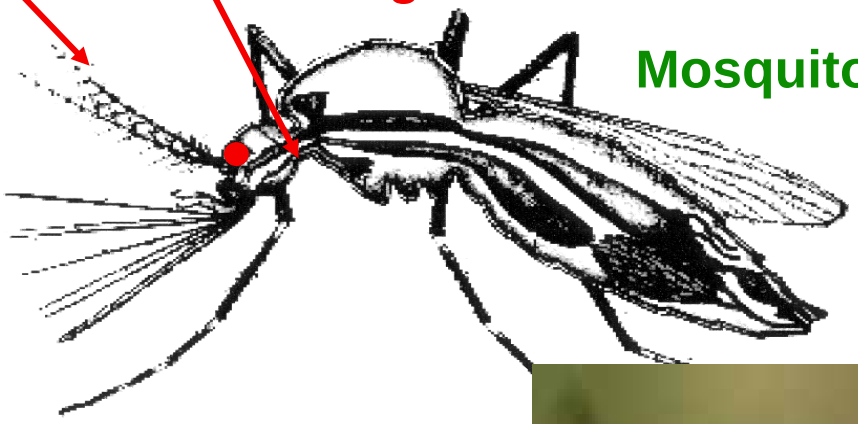
Sensor

Ultra small volume
Small number of neuron cells
Extremely low power

Infrared
Humidity
CO_2

Real time image processing
(Artificial) Intelligence
3D flight control





Mosquito

System and Algorism becomes more important !

But do not know how?

Dragonfly is further high performance